

# LIFE CYCLE ASSESSMENT OF THE FAIRPHONE 3

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Berlin, July 2020

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## Abbreviations

ADP	Abiotic resource depletion
AUO	AU Optonics Corporation, Taiwanese display manufacturer
BOD	Biological oxygen demand
BoM	Bill of materials
CO <sub>2</sub> e	Carbon dioxide equivalents
COD	Chemical oxygen demand
DRAM	Dynamic random access memory
ecoinvent	Life cycle inventory data base
EoL	End of life
FP2	Fairphone 2
FP3	Fairphone 3
GaBi	LCA software by thinkstep
GWP	Global warming potential
IC	Integrated circuit
LCA	Life cycle assessment
LCD	Liquid crystal display
LCI	Life cycle inventory
LCIA	Life cycle impact assessment
LCO	Lithium cobalt oxide
LED	Light emitting diode
LPG	Liquefied petroleum gas
NO <sub>x</sub>	Generic term for the mono-nitrogen oxides nitric oxide (NO) and nitrogen dioxide (NO <sub>2</sub> )
PC	Polycarbonate
PCB	Printed circuit board
PFC	Perfluorocarbons
SB-e	Antimony equivalents
SO <sub>x</sub>	Sulfur oxide
TPU	Thermoplastic polyurethane
TSS	Total suspended solids
VOCs	Volatile organic compounds

# 1 Executive Summary

Fairphone 3 is the new iteration of Fairphone’s modular smartphone. The present LCA study aims to assess the environmental impact of the Fairphone 3 and identifies main drivers and hotspots in the life cycle. A special focus is put in the modular design of the device, which allows for easier repair. For that matter, a scenario-based approach is used, accounting for different lengths of the use phase and involving various repair strategies. The functional unit is set to be three years of intensive use of the Fairphone 3 as it is delivered to the customer.

The following impact categories are analysed in the study:

- Climate change (GWP)
- Abiotic resource depletion – elements (ADP elements)
- Abiotic resource depletion – fossil resources (ADP fossil)
- Human toxicity (Human tox)
- Ecotoxicity (Eco tox)

The data for this study is based on the bill of materials provided by Fairphone B.V., as well as on the material declarations provided by its suppliers. Those have been cross-checked with a teardown of a Fairphone 3 performed by Fraunhofer IZM.

## Results

The total GWP for the Fairphone 3 is estimated to be 39.5 kg CO<sub>2</sub>e. The relative values for five impact categories are shown in Figure 1-1.

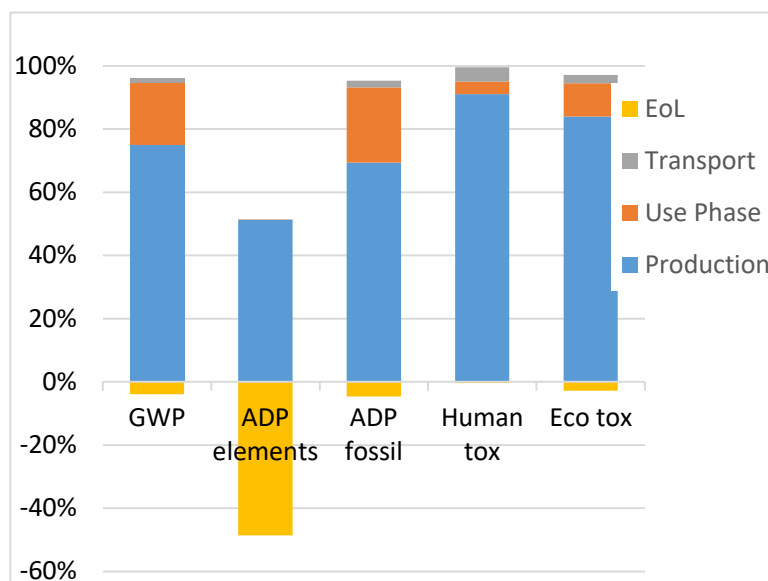
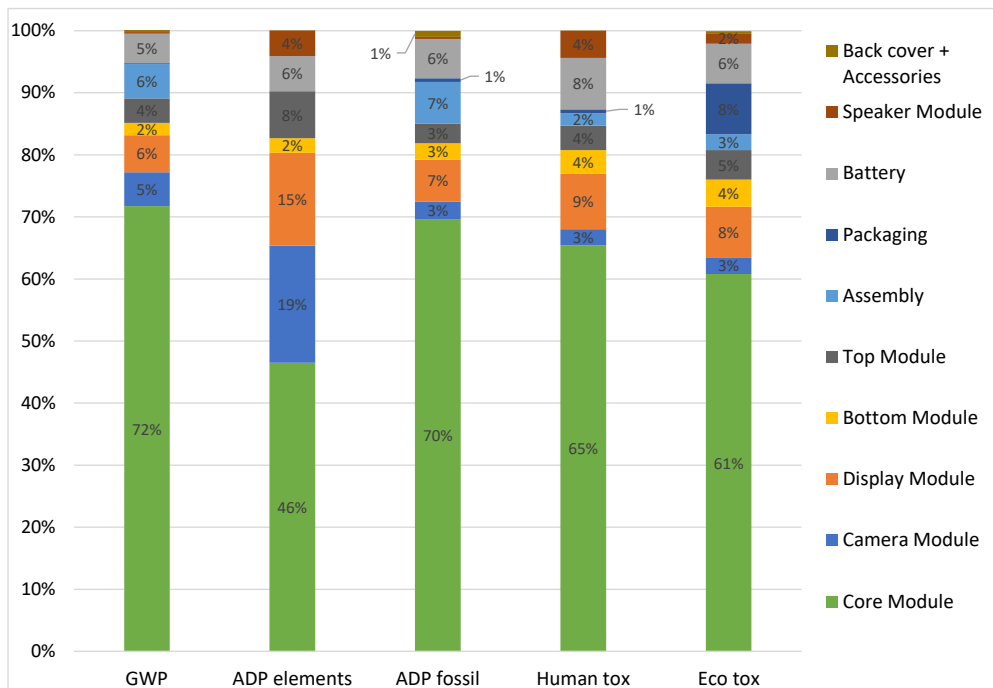


Figure 1-1: Relative impact per life cycle phase

Production is the main driver for all impact categories. A breakdown of the contributions of the different parts is shown in Figure 1-2 below. The second main contribution to the impact categories is the use phase while the role of transport is rather minor. The end-of-life (EoL) phase shows negative impacts, which means environmental benefits, most distinctly in the impact category ADP elements due to the recovery of gold.

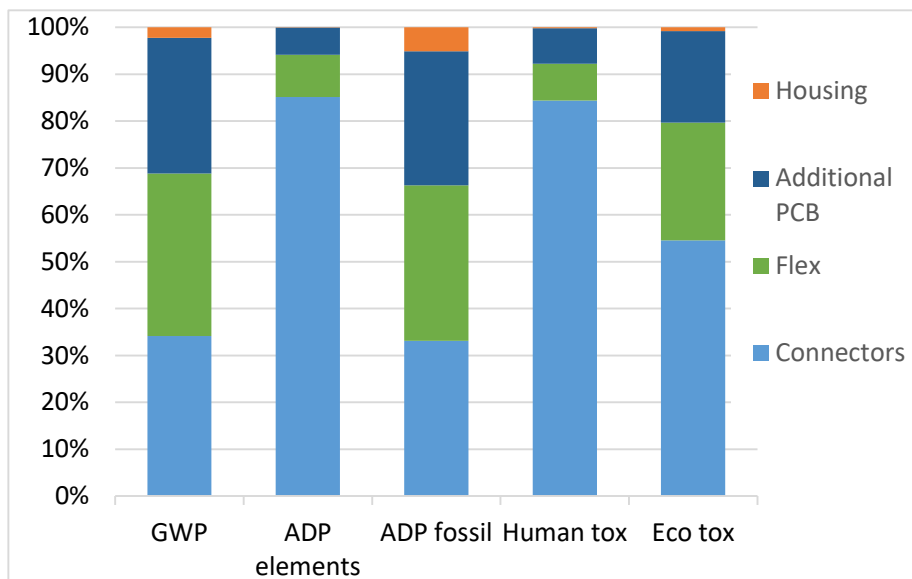


**Figure 1-2: Relative impacts of the production phase per impact category**

Within production, the core module is associated with the greatest contribution across all impact categories as it includes most of the PCB area, the main ICs and electronics.

### Modularity and repair

Modularity has been modelled as being mainly related to extra housing and module connections. Those are made through flex cables and press-fit connectors. For GWP the modularity overhead is calculated to be 0.744 kg CO<sub>2</sub>e, which represents 2.3 % of all production impacts. For ADP elements the share is bigger at around 17.2 %, due to the gold plating of the connector contacts. Figure 1-3 expands on that.



**Figure 1-3: Relative impacts connected to modularity**

As for repair, two main repair scenarios have been assumed. In repair scenario A, faulty modules are assumed to be replaced by new ones, taking advantage of Fairphone's

modular design. In repair scenario B, it is assumed that part of the faulty modules are actually repaired at board-level, allowing for replacement of specific components. A per-year comparison of the results are shown in Figure 1-4. It is clear that the benefits from both repair scenarios are highly dependent on the related use phase extension.

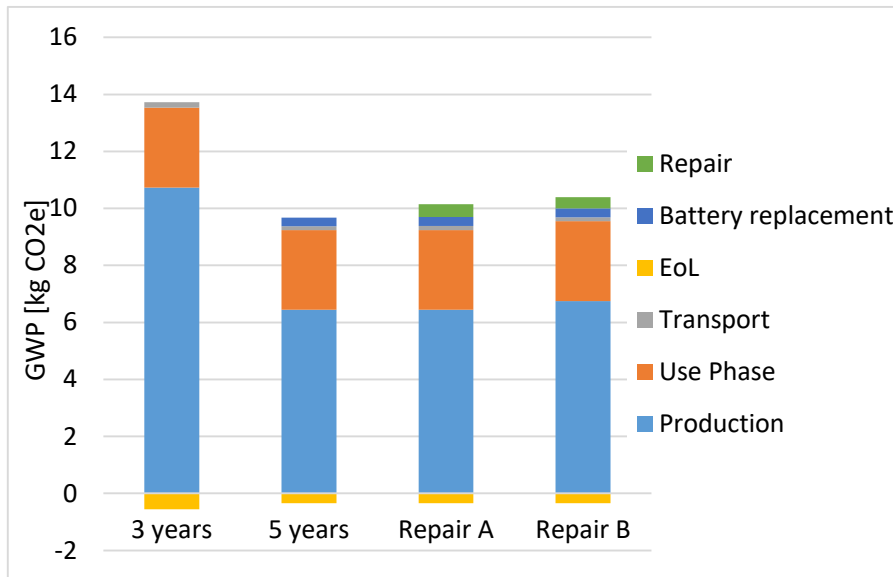


Figure 1-4: Relative impact per year use for the impact category GWP

Figure 1-5 provides a more detailed look at the differences between both repair scenarios which are too small to be seen in the per-year results. The benefits of on-board repair are tightly connected to the burden that transport poses and the components that can be effectively replaced. The study considered a conservative scenario in which only 37 % of modules are effectively repaired (75 % used modules are collected and only 50 % of those can be repaired).

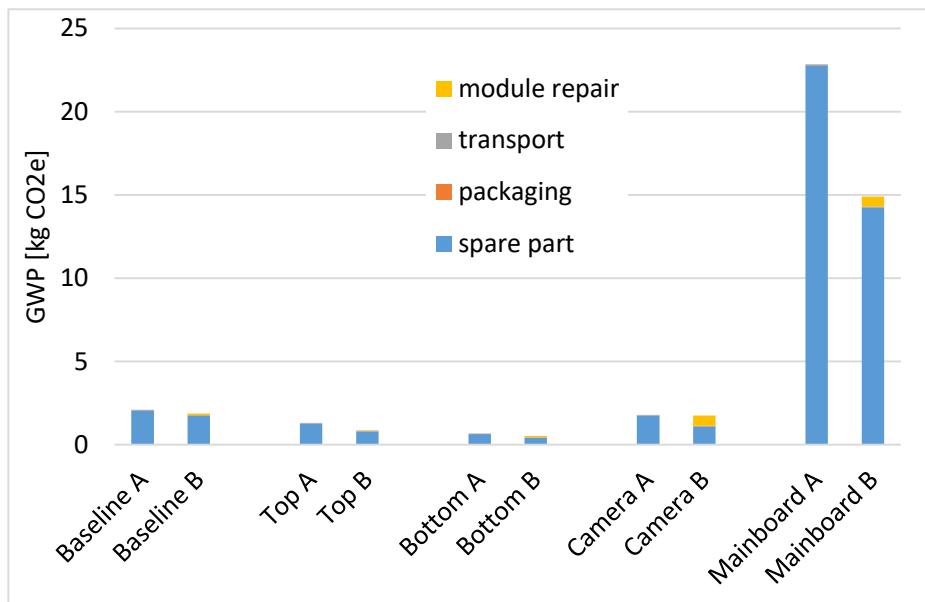


Figure 1-5: Variation between different repairs

## Conclusions

The results of the Fairphone 3 LCA show that environmental impacts are largely production driven, with the electronic components causing the main impact. Housing and structural parts play a minor role in the overall impact. Design aspects, such as form factor, indirectly influence the entire LCA of the device, mainly through the display and battery size, but not through the impact of housing material itself.

As the main impact is caused by production, prolonging the use phase is still a strong measure to influence the overall environmental impact for all impact categories except ADP elements, which can be reduced through efficient precious metal recycling. The comparison of 3, 5 and 7 years of use shows that the impact per year of use drops significantly with longer lifetime (up to 42 % GWP drop per year for a 7 years use phase). This is still the case if repair is needed, as shown in the repair scenarios. This is, however, dependent on the effective lifetime extension that is achieved in reality.

The impact of the additional hardware required to enable modularity has been reduced in comparison with Fairphone 2. This is due to the new connectors which, unlike the previous pogo pin connectors, use less gold in their contacts. Furthermore, the small press-fit connectors are not a unique feature of the Fairphone, as they can also be found in more conventionally designed smartphones. Therefore, the “modularity overhead” is now much smaller when compared to the previous model.

The change in transport to the distribution hub, which now takes place by train rather than by air, is translated into a notable reduction on transport-related impacts of around 87 % reduction in GWP. The use phase, on the contrary, results in an increased environmental impact in all categories when compared to the Fairphone 2, mainly due to the bigger battery of the Fairphone 3 and the assumption of one full charge/discharge cycle per day.

## 2 Goal and Scope Definition

### 2.1 Goal

The goal of this life cycle assessment is threefold:

- Assess the environmental impact of the Fairphone 3 and identify main drivers and hotspots in its life cycle.
- Compare different use phase assumptions, especially regarding repair.
- Assess the potential impact of using more recycled material for 8 focus materials (section 5).

To assess the environmental impact of the phone, a baseline scenario is assessed based on the product as sold to the users.

For the impact of repair and different use-times, additional scenarios with varying use-time (active years of use) and replacements of parts are being calculated.

The potential impact of a possible use of secondary materials for eight focus materials is assessed separately in section 5. Those are a selection of materials in which Fairphone is focusing efforts to tackle some environmental and social hotspots.

The intended applications of the study are:

- Use lessons-learned for possible future product designs,
- evaluate the effect of using more recycled materials in the production of the phone, and
- stakeholder communication

### 2.2 Scope

The scope of this study covers the entire life cycle of the Fairphone 3: raw material acquisition, manufacturing, transport, use and end-of-life.

The functional unit for the baseline scenario is an intensive smartphone use over three years. The corresponding reference flow is the Fairphone 3 as delivered to the customer including sales packaging, manual, screwdriver and protection bumper, but without charger, which is not part of the standard delivery. No parts' failures are assumed for the baseline scenario. The additional scenarios cover:

- Varying years of use:
  - 5 years of use with one additional replacement battery
  - 7 years of use with two additional replacement batteries
- Different repair scenarios:
  - Repair scenario A: 5 years use with replacement of several modules (see section 3.5.1)
  - Repair scenario B: similar to repair scenario A, but with additional repair of module (see section 3.5.2)

The data inventory is based on the bill-of-materials (BoM), a product tear-down, and material declarations for subparts from suppliers. The final assembly process is based on primary data from Arima comms in China (see section 3.1.13).

The following impact categories are covered for the life cycle assessment:

- Climate change (GWP)
- Abiotic resource depletion – elements (ADP elements)

- Abiotic resource depletion – fossil resources (ADP fossil)
- Human toxicity (Human tox)
- Ecotoxicity (Eco tox)

However, not all processes used in the assessment could cover all the listed impact categories. The effect will be described in the sensitivity analysis and interpretation of results (section 4.5). Additionally, the analysis of recycled materials covers mainly GWP and only partially other impact categories due to limited data availability (see section 5).

Transport processes cover the transport of parts to the final assembly, transport of the final product from final assembly in China to the distribution hub in Europe, and product delivery to the final customer within Europe.

Use phase impacts are related to electricity consumption of the phone and the charger, which is not delivered with the product. Impact of the mobile network (availability and data transfer) are not within the scope of this study. Consumables are considered for the scenarios with longer use (replacement batteries) and spare parts for the repair scenarios.

Processes are modelled with the LCA software GaBi and the corresponding data base, including the "Electronics" extension data base. This is supplemented with theecoinvent data base v3.6 for processes where no suitable GaBi data set is available.

# 3 Life Cycle Inventory

The life cycle inventory covers the following sections:

- Raw material acquisition and manufacturing
- Use phase
- Transport
- End-of-life (EoL)

The raw material acquisition is indirectly covered using cradle-to-gate data sets for the manufacturing.

For the assessment, the life cycle assessment software GaBi with its own data base, the electronics extension as well as the ecoinvent 3.6 data base was used. If data is used from additional sources, this is specifically mentioned in the description. In many aspects, the modelling follows the same assumptions as the Fairphone 2 LCA [Proske et. al. 2016], which was also carried out by Fraunhofer IZM.

## 3.1 Raw material acquisition and manufacturing

The manufacturing phase was modelled according to the bill of materials (BoM) of the Fairphone 3 and the material compositions of several components provided by the suppliers. The analysis was supplemented with a teardown of the phone at Fraunhofer IZM.

Life cycle data sets were allocated to all parts based on weight (mechanical parts), number of pieces (electronic components) or size/area (e.g. printed circuit boards). The individual approach for each module and component group is described in the following. The modules of the phone with its main parts are shown in Table 3-1.

**Table 3-1: Main parts per module**

Module	Main parts	Weight [g]
Fairphone 3		190.4
Core module		
	Mainboard with	18.5
	• Main electronic components	
	• Connectors to modules	
	• Connectors to battery and display assembly	
	Button assembly	
	Flex boards to module connectors	
	Fingerprint sensor	
	Frame and mid frame	
Top module		5.1
	Top module board	
	Front camera	
	Receiver (speaker)	
	Earphone jack	
Camera module		2.9
	Camera	
	Camera board	
Bottom module		4.3
	Bottom module board	
	Vibration motor	
	USB-C connector	



Module	Main parts	Weight [g]
Speaker module	Speaker, microphone	3.1
Display module	Display frame	63.4
	LCD display	
	Display board	
	Cover glass	
Battery module	Battery	50.4
Back cover		12.6

### 3.1.1

#### Core Module

The core module consists of the following parts:

- Mainboard with the majority of integrated circuits (ICs) of the phone, including the CPU, memory and storage, and other electronic components
- Metallic shielding on the board
- Connectors to the different modules, based on flexible printed circuit boards (flex boards)
- SIM card and MicroSD card connectors
- Mid-frame and screws
- Fingerprint sensor
- Buttons and printed circuit boards

The detailed modelling of the PCBs, ICs, passive components and connectors is described in subsection 3.1.9. The detailed BoM with the assigned weight and life cycle inventory data set for the core module can be found in the annex in Table 8-5.

### 3.1.2

#### Battery

The battery in the Fairphone 3 contains a lithium-ion cell with the following specifications:

- Capacity: 11.55 Wh / 3040 mAh
- Mass: 52 g

The following Table 3-2 lists the material composition ranges provided by the manufacturer. The median values are used for modelling, which results in the mass of individual materials provided in the last column. A range of additional materials is included in the category "other".

**Table 3-2: Material composition of the battery**

Material	Mass percentage range	Mass percentage median	Mass per cell [g]
Cobalt Oxide	25 - 30 %	27.5 %	14.3
Graphite	23 - 35 %	29 %	15.1
LiPF <sub>6</sub>	12 - 15 %	13.5 %	7
Aluminium foil	7 - 10 %	8.5 %	4.4
Copper	5 - 10 %	7.5 %	3.9
Nickel	2 - 3 %	2.5 %	1.3

Material	Mass percentage range	Mass percentage median	Mass per cell [g]
Polyvinylidene fluoride (PVDF)	0.5 – 2 %	1.25 %	0.7
Polypropylene	2 – 5 %	3.5 %	1.82
Polyethylene	0.5 – 1 %	0.75 %	0.39
PVC	0.2 – 0.5 %	0.35 %	0.18
Other		5.65	2.94

The battery management system PCB and the cell packaging are assumed to be the same as in the FP2.

For replacement batteries (depending on the years of use, see section 3.2) additional packaging and transport is assumed.

### 3.1.3

#### Top module

The top module consists of the following parts:

- Module housing
- Module board with electronic components
- Front camera
- Receiver
- Connectors
- Earphone jack

The detailed modelling of the PCBs, ICs, passive components and connectors is described in subsection 3.1.9. The detailed BoM with the assigned weight and life cycle inventory data set for the top module can be found in the annex in Table 8-7.

### 3.1.4

#### Bottom module

The bottom module consists of the following parts.

- Module housing
- Module board with electronic components
- Connectors
- USB-C connector
- Vibration motor

The vibration motor is modelled based on the material composition. For the tungsten, no data set was available in GaBi or ecoinvent. Therefore, a data set from the German life cycle data base Probas was used [Probas 2020].

The detailed modelling of the PCBs, ICs, passive components and connectors is described in subsection 3.1.9. The detailed BoM with the assigned weight and life cycle inventory data set for the bottom module can be found in the annex in Table 8-7.

### 3.1.5

#### Speaker module

The speaker module consists of the following parts:

- Module housing
- Speaker
- Connectors

The detailed modelling of the connectors is described in subsection 3.1.9. The detailed BoM with the assigned weight and life cycle inventory data set for the speaker module can be found in the annex in Table 8-8.

### 3.1.6 Display Module

GaBi does not contain an LCD data set. The data set from Ecoinvent for a display is from 2001 and therefore out-dated and has only limited applicability for a smartphone display. Therefore, the display is modelled according to the CSR report from the Taiwanese display manufacturer AUO [AUO 2019]. The same approach was used for the Fairphone 2 LCA, but with older data from 2015.

The data is scaled by panel size, which in the case of Fairphone 3 is of 81.9 cm<sup>2</sup>.

AUO data covers scope 1 (direct emissions) and scope 2 (purchased energy). Scope 3 covers product use, business travel, and commuting but not the impact of upstream suppliers and is therefore not taken into account. Production of input materials is not covered. The data covers the panel manufacturing without backlight and electronics (display board).

The following data presented in Table 3-3 is given by the AUO CSR report and the data marked in blue is transferred to the LCA model.

The given values from AUO for scope 2 greenhouse gas (GHG) emissions (from purchased energy) are not directly transferred, but the energy consumption is included via the corresponding processes (electricity production, gas, diesel) to also address other impact categories. Purchased electricity for the production process is included as electricity from Taiwan.

**Table 3-3: Panel production data by AUO [2019]**

<b>Input</b>	<b>Total</b>	<b>per m<sup>2</sup></b>
<b>Material</b>		
Glass substrate	97,865.90 tonnes	1.42E+00 kg/m <sup>2</sup>
liquid crystal	90.00 tonnes	1.31E-03 kg/m <sup>2</sup>
Photoresist	31,290.00 kiloliters	4.55E-01 l/m <sup>2</sup>
Array stripper Usage	80,862.30 tonnes	1.18E+00 kg/m <sup>2</sup>
CF Thinner	1,774.00 tonnes	2.58E-02 kg/m <sup>2</sup>
Developer	49,188.00 tonnes	7.15E-01 kg/m <sup>2</sup>
Aluminium Etchant	10,493.00 kiloliters	1.53E-01 l/m <sup>2</sup>
PFC Usage	900.40 tonnes	1.31E-02 kg/m <sup>2</sup>
<b>Energy</b>		
total consumed	19,746,407.09 GJ	2.87E-01 GJ/m <sup>2</sup>
Purchased Electricity	18,921,349.28 GJ	2.75E-01 GJ/m <sup>2</sup>
Natural Gas	716,182.93 GJ	1.04E-02 GJ/m <sup>2</sup>
LPG	12,511.37 GJ	1.82E-04 GJ/m <sup>2</sup>
Diesel	96,363.50 GJ	1.40E-03 GJ/m <sup>2</sup>
self-generated solar power	299.87 GJ	4.36E-06 GJ/m <sup>2</sup>
Wind power	0.00 GJ	0.00E+00 GJ/m <sup>2</sup>
<b>Water</b>		
total	33,735.21 megaliters	4.90E+02 l/m <sup>2</sup>
<b>Emissions</b>		
scope 1	320,000.00 tonnes CO <sub>2</sub>	4.65E+00 kg CO <sub>2</sub> /m <sup>2</sup>
scope 2	3,250,000.00 tonnes CO <sub>2</sub>	4.73E+01 kg CO <sub>2</sub> /m <sup>2</sup>
scope 3	8,250,000.00 tonnes CO <sub>2</sub>	1.20E+02 kg CO <sub>2</sub> /m <sup>2</sup>
ODS emissions	0.08 tonnes	1.16E-06 kg/m <sup>2</sup>

Input	Total	per m <sup>2</sup>
SO <sub>x</sub>	53.80 tonnes	7.82E-04 kg/m <sup>2</sup>
NO <sub>x</sub>	75.00 tonnes	1.09E-03 kg/m <sup>2</sup>
Fluorides	3.60 tonnes	5.23E-05 kg/m <sup>2</sup>
HCl <sub>4</sub>	2.20 tonnes	3.20E-05 kg/m <sup>2</sup>
Volatile organic compounds (VOC)	144.90 tonnes	2.11E-03 kg/m <sup>2</sup>
Wastewater	25,995.10 megaliters	3.78E+02 l/m <sup>2</sup>
COD	874.80 tonnes	1.27E-02 kg/m <sup>2</sup>
Biochemical oxygen demand (BOD)	121.70 tonnes	1.77E-03 kg/m <sup>2</sup>
total suspended solids	179.40 tonnes	2.61E-03 kg/m <sup>2</sup>
hazardous waste	30,623.40 tonnes	4.45E-01 kg/m <sup>2</sup>
non-hazardous waste	79,349.50 tonnes	1.15E+00 kg/m <sup>2</sup>
<b>Panel output</b>		
large size	114.80 Mio pieces	
small/medium size (<10inch)	166.60 Mio pieces	
Total produced display area	68.78 Mio. m <sup>2</sup>	

Life Cycle Inventory

### Backlight assembly:

Die size of LEDs per screen area is modelled (as for the FP2 LCA) based on Deubzer [2012] for a comparable tablet display (see Table 3-4). This results in a die area of 0.0077 cm<sup>2</sup> for the Fairphone 3 display. The LEDs are modelled per die area as CMOS logic according to Boyd [2012] as it is also described by Zgola [2011].

**Table 3-4: Die area per display area [Deubzer 2012]**

Backlight design (typical product)	Display diagonal	Brightness [cd/m <sup>2</sup> ]	Total die area per display area [mm <sup>2</sup> /cm <sup>2</sup> ]
Edge lit (tablet)	7"	350	0.0094

### 3.1.7

#### Camera Module

The camera module consists of

- Camera with camera sensor Sony IMX363
- Camera board
- Connector.

The sensor ICs are modelled according to the die size as described in section 3.1.9.3 and was determined via CT images.

The detailed modelling of the connectors is described in subsection 3.1.9. The detailed BoM with the assigned weight and life cycle inventory data set for the camera module can be found in the annex in Table 8-10.

### 3.1.8

#### Back cover

The back cover consists of 12.5 g polycarbonate.

### 3.1.9

#### Cross-module approaches

##### 3.1.9.1 Connectors

Connectors are modelled according to their material composition provided by the manufacturers. The impacts of possible production overheads are analysed in the sensitivity analysis (see section 4.5.2).

The board-to-board connectors changed from pogo pin connectors in the Fairphone 2 to press-fit connectors in the FP3 and they mainly consist of the following materials:

- Copper, nickel and gold for the contacts
- Steel or bronze for metal fittings
- Glass fibre-supported plastic for the housing

A flex cable is used per module to connect it to the core, with a pair of male/female press-fit connectors on each end. The connectors are modelled based on the material composition from the manufacturer, while the flex cables are modelled as one-layer PCBs.

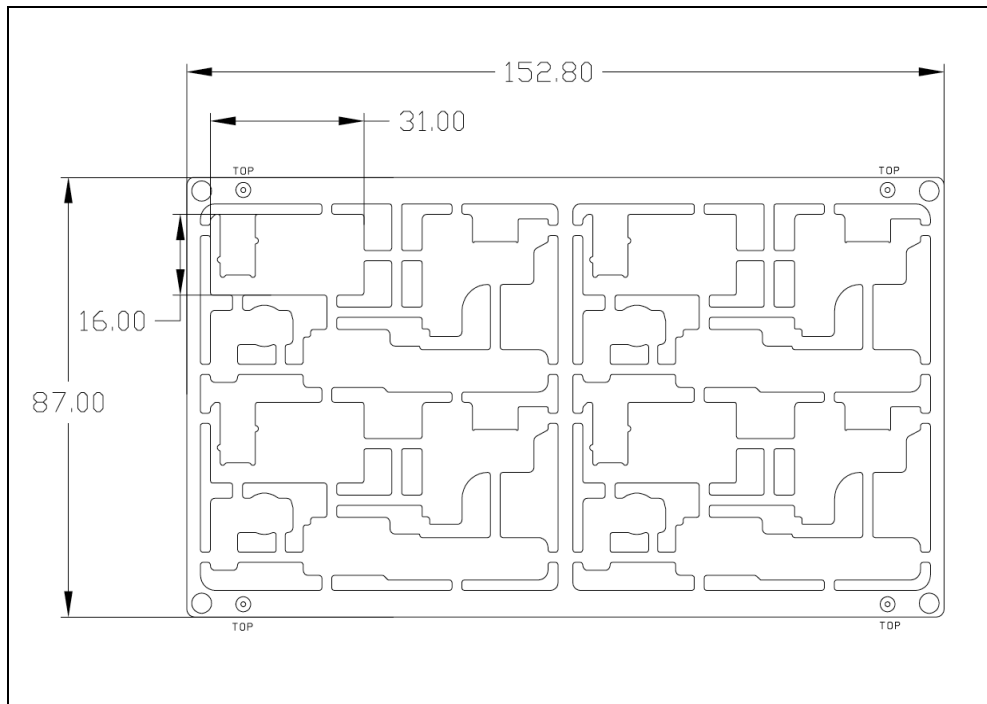
The detailed material breakdown can be found in the corresponding module table in the annex.

The connector between mainboard (core module) and display board is the only pogo pin connector with 32 pins on the mainboard and has contact areas on the PCB on the display side. The pogo pins are modelled as the press-fit connectors based on the material composition given by the supplier.

The contact area is modelled similarly to the Fairphone 2 LCA based on the additional amount of nickel and gold on the PCB. The amount of gold deposited on all module boards together is 2 mg (see also Figure 3-1). 80% of that gold is assumed to be connected to the contact area, resulting in 1.6 mg.

##### 3.1.9.2 PCBs:

The conventional method to model printed circuit boards is according to the number of layers and outer dimension (smallest rectangular). This might over- or underestimate offcuts, depending on the specific form and production layout. For the Fairphone 3, the production layouts were available and therefore directly used for the modelling of the rigid PCBs.



**Figure 3-1: Module board production layout**

The module PCBs are produced all on the same panel (Figure 3-1), with four module boards arranged in each. The mainboard is modelled with two mainboards per panel. Table 3-5 shows the allocated area for the boards and the area based on the outer dimensions. The results show that the offcuts would have been underestimated for the module boards (in total by 13.5 cm<sup>2</sup>) and overestimated for the mainboard (in total by 17.8 cm<sup>2</sup>).

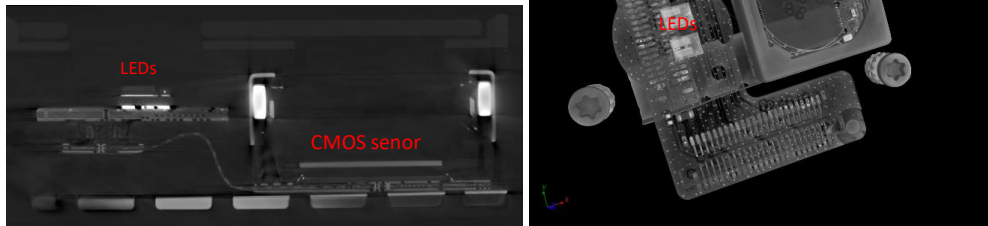
**Table 3-5: Printed circuit board area modelled**

Module	Boards per panel	Length	Width	Area	Allocated area
		mm	mm	cm <sup>2</sup>	cm <sup>2</sup>
Module panel	4 per module	152.8	87	132.94	
Bottom		25	24	6.00	10.11
Camera		15	16	2.40	4.04
Display		49	13	6.37	10.73
Top		31	16	4.96	8.35
Mainboard panel	2	166.0	86.0	142.76	71.38
Mainboard		136.1	65.51	89.16	

Flexible printed circuit boards are modelled as one-layer PCBs according to the outer dimensions as no data set for flex boards was available.

### 3.1.9.3 Integrated circuits

The environmental impact of ICs is determined mainly by the processed die area. For the Fairphone 3, die area was determined using CT images of the individual boards (Figure 3-2) and grinding of the ICs.



**Figure 3-2: Exemplary pictures of CT images – camera module**

For the main board, CT images were not enough to determine the die size. Therefore, additional x-rays from various dimensions and vertical grinding of the ICs was used.

Table 3-6 shows the identified and modelled die sizes per module. Additional ICs from the mainboard are modelled with existing data sets from GaBi.

**Table 3-6: Die sizes**

Module	IC description	Die area [mm <sup>2</sup> ]
Bottom module	I.C analogue switch	0.847
Camera module	LED Flash	1.208
Camera module	LED Flash	1.222
Camera module	CMOS image sensor	35.714
Top module	Light sensor	0.8933
Top module	Light sensor	0.0814
Top module	LED Full Colour	0.2556
Top module	CMOS image sensor	18.009
		3
Mainboard (WLAN)	I.C WLAN	11.6
Mainboard (WLAN)	I.C WLAN	1.44
Mainboard	I.C audio power amplifier	12.96
Mainboard	I.C analogue switch	1.61
Mainboard (power management)	I.C power amplifier modules	6.28
Mainboard (power management)	I.C PMU	26.88
Mainboard (power management)	I.C PMU	0.77
Mainboard (power management)	I.C PMU	11.36
Mainboard	Sensor	7.2
Mainboard	NFC Microcontroller	8.69
Mainboard	I.C transceiver	11.44
Mainboard	I.C audio power amplifier	9.58

Module	IC description	Die area [mm <sup>2</sup> ]
Mainboard (CPU)	Baseband processor	46.4
Mainboard (Flash/RAM)	Stacked memory	507.74

The integrated circuits with greater die size are the power management ICs, CPU and Flash/RAM stacked package. The latter having a higher die size than all other ICs together. Flash storage and RAM are contained within one stacked memory with 9 stacked dies. It was not possible to assign all of them to either RAM or Flash, so die area and results are presented for the whole package.

The impact of the ICs is modelled according to figures from Boyd [2012] and Prakash et al. [2013]. Boyd [2012] refers to CMOS logic, the numbers from Prakash et al. [2013] are based on a DRAM chip by Samsung. Therefore, the DRAM and storage of the Fairphone 3 are modelled according to Prakash et al. [2013] (see Table 3-9), all other ICs listed in Table 3-4: Die area per display area [Deubzer 2012] and Table 3-6 are based on the figures for logic chips (see Table 3-8). As the wafer manufacturing is similar for all ICs, the more detailed wafer data set from Prakash et al. [2013] was used also for the wafer manufacturing of the CMOS logic ICs.

The impact category ADP elements is not covered by the data by Boyd [2012]. This impact category is driven by material use, specifically gold and other precious metals have a high impact. To reflect this, the ADP elements impact of gold, silver and palladium in the package is added to the individual ICs which are modelled with the CMOS logic based on the material composition given by the supplier (see Table 3-7).

**Table 3-7: Gold, silver and palladium in IC packages per module board**

	Gold [g]	Silver [g]	Palladium [g]
Mainboard	2,45E-04	1,83E-03	6,95E-06
Top module	8,55E-04	5,99E-05	3,10E-06
Camera module	0,00E+00	2,00E-07	0,00E+00
Bottom module	0,00E+00	1,70E-05	0,00E+00

The DRAM figures already include gold as an individual flow in the model. The material composition of the Samsung storage chip used by Prakash et al. [2013] therefore fits the amount of gold stated by the material composition of the Fairphone 3 storage IC very well when scaled by die size.



**Table 3-8: Environmental impacts according to Boyd [2012] per cm<sup>2</sup> die for the technology 32 nm logic chips**

Process	Energy	GWP	Photo-chemical smog	Acidification	Eco-toxicity	Human Health Cancer	Human Health non cancer
	[MJ]	[kg CO <sub>2</sub> e]	[kg NO <sub>x</sub> ]	[mol H <sup>+</sup> ]	[kg 2,4-D]	[kg C <sub>6</sub> H <sub>6</sub> ]	[kg C <sub>6</sub> H <sub>6</sub> ]
Fab	33.6	0.9	0.006	0.356	0.030		2.444
Infrastructure (fab construction and equipment)	17.9	1.5	7.43E-03	3.86E-01	4.96E-05	7.36E-05	3.07E+00
Silicon	5.9	0.5	5.25E-03	3.03E-01	2.60E-02		2.08E+00
Chemicals	2.9	0.4					
Fab direct emissions and EoL			2.51E-04	2.00E-01	4.70E-04	1.89E-05	1.00E+00

**Table 3-9: Environmental impacts according to Prakash et al. [2013] of storage chips**

Process	Wafer	Good die out	Packaged die	GaBi process
Reference	cm <sup>2</sup>	1	1	1
Inputs		process	incl. upstream	process
				incl. upstream
Wafer		1,38		
good die			1	
Electricity	kWh	3,85E-01	1,27	1,80E+00
Natural gas	kWh		1,60E-01	1,60E-01
Silicon dioxide	kg	4,87E-03		6,72E-03
Wood pallets (as energy material)	kg	1,83E-03		2,53E-03
Lignite	kg	3,98E-03		5,49E-03
Petroleum coke	kg	5,97E-04		8,24E-04
Electrode material	kg	1,63E-04		2,25E-04
HCl	kg	6,75E-03		9,32E-03
				2,37E+00
				5,72E-01
				7,09E-02
				1,10E-04
				6,83E-03
				2,53E-03
				5,49E-03
				8,24E-04
				2,25E-04
				9,32E-03
				CN: Electricity grid mix ts
				US: Natural gas mix ts
				GLO: Silicon mix (99%) ts
				EU-28: Wood pellets (6.2% moisture; 5.8% H2O content) (EN15804 B6) ts
				EU-28: Lignite mix ts
				EU-28: Petroleum coke at refinery ts
				RER: Hydrogen chloride ELCD/PlasticsEurope <t-agg>

Process	Wafer	Good die out	Packaged die	GaBi process
Water	kg	7,88E+00	7,88E+00	7,88E+00 EU-28: Water (deionised) ts
N2 (high purity) <sup>1</sup>	kg	6,06E-01	6,06E-01	6,06E-01 EU-28: Nitrogen (gaseous) ts
O2 (high purity)	kg	4,13E-03	4,13E-03	4,13E-03 EU-28: Oxygen (gaseous) ts
Ar (high purity)	kg	2,34E-03	2,34E-03	2,34E-03 DE: Argon (gaseous) ts
H2 (high purity)	kg	6,34E-05	6,34E-05	6,34E-05 RER: Hydrogen (electrolysis) PlasticsEurope
Sulphuric acid (high purity)	kg	7,33E-03	7,33E-03	7,33E-03 EU-28: Sulphuric acid (96%) ts
Hydrogen peroxide (high purity)	kg	2,04E-03	2,04E-03	2,04E-03 DE: Hydrogen peroxide (100%; H2O2) (Hydrogen from steam cracker) ts
hydrofluoric acid (high purity)	kg	5,53E-04	5,53E-04	5,53E-04
Phosphoric acid (high purity)	kg	3,32E-03	3,32E-03	3,32E-03 EU-28: Phosphoric acid (H3PO4, 54% P2O5) Fertilizers Europe
2-Propanol (C3H8O)/ isopropyl alcohol (IPA) (high purity)	kg	2,78E-03	2,78E-03	2,78E-03 DE: Isopropanol ts
Ammonium hydroxide (high purity)	kg	1,09E-03	1,09E-03	1,09E-03
CF4	kg	5,94E-05	5,94E-05	5,94E-05
CHF3	kg	5,66E-06	5,66E-06	5,66E-06 GLO: trifluoromethane production ecoinvent 3.5
NF3	kg	3,02E-04	3,02E-04	3,02E-04
C2F6	kg	6,89E-05	6,89E-05	6,89E-05 GLO: hexafluoroethane production, from fluorination of tetrafluoroethane ecoinvent 3.5
SF6	kg	8,96E-06	8,96E-06	8,96E-06 RER: sulphur hexafluoride production, liquid ecoinvent 3.5

<sup>1</sup> For high-purity materials, adjustments factors according to Prakash et al. [2013] were applied.

Process	Wafer	Good die out	Packaged die	GaBi process	
NaOH (for wastewater treatment)	kg	2,04E-03	2,04E-03	2,04E-03	EU-28: Sodium hydroxyde (caustic soda) mix (100%) ts
Polymer	kg		2,47E-05	2,47E-05	
Au	kg		4,65E-07	4,65E-07	GLO: Gold (primary) ts
Carbon Black	kg		4,65E-07	4,65E-07	DE: Carbon black (furnace black; general purpose) ts
Ag	kg		1,62E-06	1,62E-06	GLO: Silver mix ts
Cu	kg		2,33E-07	2,33E-07	GLO: Copper mix (99,999% from electrolysis) ts
Sn	kg		5,49E-05	5,49E-05	GLO: Tin ts
BT-Core (Bismaleimidetriazine)+ Cu+Au+Ni	kg		1,22E-04	1,22E-04	
<b>Emissions</b>					
CO2	kg	8,33E-03	1,15E-02	1,15E-02	
CO	kg	1,67E-04	2,30E-04	2,30E-04	
Nox	kg	1,38E-05	1,90E-05	1,90E-05	
Methanol	kg	8,51E-05	1,17E-04	1,17E-04	
Methane	kg	8,50E-05	1,17E-04	1,17E-04	
Ethan	kg	2,90E-05	4,00E-05	4,00E-05	
Particles	kg	2,01E-04	2,77E-04	2,77E-04	
H2O	kg	1,88E-03	2,59E-03	2,59E-03	
SO2	kg	3,44E-05	4,75E-05	4,75E-05	
Hydrogen	kg	1,25E-04	1,73E-04	1,73E-04	
HFC-23 (Trifluormethane)	kg		2,26E-06	2,26E-06	modelled directly as CO2-emissions
Perfluorethane (C2F6)	kg		3,84E-06	3,84E-06	
Tetrafluormethane (CF4)	kg		3,25E-06	3,25E-06	
Perfluoropropane (C3F8)	kg		2,26E-06	2,26E-06	
SF6	kg		2,26E-06	2,26E-06	
NF3	kg		1,56E-05	1,56E-05	

### 3.1.9.4 Passive components

Passive components were modelled with corresponding data sets from the GaBi electronics extension, scaled by number of pieces. If no corresponding data set was available in GaBi, an ecoinvent data set for unspecific passive components was used and scaled by weight.

### 3.1.10 Protection bumper

The Fairphone 3 is delivered with a protection bumper, therefore it is included in the reference flow. It consists of 13.7 g TPU from bio-based oil. As no life cycle data is available for this specific material it is modelled as conventional TPU.

### 3.1.11

#### Screwdriver

The screwdriver consists of a metal (~1.1 g stainless steel) and a plastic part (2.9 g polyamide) and was modelled by weight.

### 3.1.12

#### Packaging

The packaging consists of a sales and a distribution packaging. The distribution packaging is proportionality reflected in the modelling. The detailed parts and assigned GaBi data sets are listed in the annex in Table 8-11.

### 3.1.13

#### Final assembly

For the final assembly, electricity consumption of the final assembly process was considered using the Chinese energy grid mix. Additionally, the consumption of ethyl alcohol and cloths from cleaning processes in the packaging process and nitrogen gas used in the reflow oven are considered. This is based on primary data from the manufacturer Arima comms in China as shown in Table 3-10.

**Table 3-10: Final assembly**

Energy use		GaBi dataset
Electricity, from grid	2.186 kWh	CN: Electricity grid mix ts
<b>Process material</b>		
Ethyl alcohol (95% purity)	0.39 g	RoW: benzyl alcohol production ecoinvent 3.5
Nitrogen (gas, >95% purity)	0,50 g	EU 28 Nitrogen (gaseous)
Cloth (lint free)	0.15 g	GLO: Cotton fibre (bales after ginning) CottonInc

## 3.2

### Use Phase

The following use pattern is assumed for the Fairphone 3 baseline scenario:

- Daily charging
- One charging cycle consumes 19.21 Wh, which results in 7.01 kWh/a

The energy per charging cycle is based on measurements carried out at Fraunhofer IZM with new and aged (state of health: 80 % capacity) batteries. As expected, aged batteries showed a lower efficiency. The average energy consumption was used to calculate the use phase consumption.

No repairs except battery replacements were assumed for the baseline scenario, but three different use-times were calculated:

- 3 years with one replacement battery
- 5 years with 2 replacement batteries

- 7 years with 3 replacement batteries

For the number of replacement batteries considered, laboratory cycle life testing of the battery was carried out. This resulted in the following insights: charging with the provided Quick Charge 3.0 enabled charger resulted in a charging rate of 0.67C (2A). The charging efficiency (power drawn from the grid relative to the battery capacity) with the above-mentioned charger was 60 %.

Battery cycle life testing at 0.67C in accordance with IEC 61960 showed that the batteries could, on average, withstand more than 850 cycles while retaining a capacity (SOH) of 80 %, and two out of three tested cells could even endure up to 1000 cycles.

Previous LCA studies of smartphones have worked with the conservative assumption that the battery is fully charged and discharged once every day, resulting in 365 charge/discharge cycles per year. Empirical data suggests that the actual number may be closer to 230 cycles on average annually [Clemm et al. 2016]. This study therefore works with the following assumptions: The battery durability is enough to last for 3 years of use, after which it needs to be replaced with a new battery. To calculate the use phase energy consumption, the study adopts the conservative assumption that the battery is fully charged once every day as explained above.

The electricity is assigned according to the distribution of sales within Europe (see Table 8-1 in the annex) assigning national electricity grid mixes.

### 3.3

#### Transport

The transport is separated in three main parts:

- Transport of parts from tier 2 suppliers to final assembly in China
- Transport of the final product to the distribution hub in Europe
- Transport to customer from distribution hub within Europe

The transportation is modelled as so-called tonne kilometres (tkm), considering transported weight and distance.

##### 3.3.1

##### **Transport to final assembly**

For the transport to final assembly, the following modes of transportation are assumed:

- Truck delivery within China
- Air freight for international transportation

The transportation is scaled by distance and weight. For the components, a weight overhead is calculated to represent packaging. Therefore, the following factors are used (as for the Fairphone 2 LCA):

- 0.1 for components > 0.5 g
- 0.94 for components < 0.5 g

This results in the following distances:

- Air freight: 0.199 tkm
- Truck: 0.253 tkm

##### 3.3.2

##### **Transport to distribution hub**

The phone is transported from the final assembly in China to the distribution hub in the Netherlands by train freight for regular orders, for which a distance of 1.632 tkm was modelled.

### 3.3.3

#### Transport to consumer

The phone is transported by truck within Europe. An average distance from the distribution hub to the different countries is assumed for this (Table 8-2 in the annex). These transport distances are weighted according to the distribution of sales.

## 3.4

### End-of-Life

For the reference case scenario, a conservative approach has been taken i.e. that the Fairphone 3 device is assumed to be discarded as a regular phone and join the wider WEEE recycling stream. This approach relies on the assumption that this is the most usual route for smartphones to follow in their end of life. Additionally, this was also the modelling approach for the Fairphone 2 LCA and using alternative modelling options could therefore hinder comparability.

Due to a lack of specific data on smartphone recycling, several assumptions needed to be made, which will be explained in this section. To begin with, the device is assumed to be disposed of in its entirety, meaning that no mass losses take place between the disposal and the recycling plant. On the lines of the EoL scenario of Fairphone 2 [Proske et al. 2016], no specific point of disposal was assumed and instead a general transport to the plant was modelled as follows, in accordance with [Hischier, 2007].

- Total transportation distance from user to recycling plant: 1500 km
- Mode of transportation is by lorry (75 % of distance) and by train (25 % of distance).

Following the Umicore recycling process [Hagelüken 2006], the device is set to have the battery removed first (depollution) and then the rest is sent to the material recovery streamline as scrap. The main processes included in the model are:

- Copper smelting
- Electrowinning
- Precious metal recovery

In the depollution step, 95% of the batteries are assumed to be separated correctly [Sommer 2013] and a recovery rate of 95% for the copper and cobalt contained is estimated. In the electrowinning step copper is recovered with a rate of 95%. Finally, in the precious metal recovery step, three elements are yielded: gold, silver and palladium, all with a rate of 95%. All recovery rates are based on Chancerel et al. [2016]. The absolute amounts recovered are in turn based on the cross comparison of the bill of materials provided by Fairphone and the material declarations of the suppliers themselves. Additionally, a disassembly of a Fairphone 3 device carried out at Fraunhofer IZM has been used as backup for completing weights and material data. Table 3-11 below shows a summary of the materials considered in the EOL modelling, their recovery rates and the mass in the device.

**Table 3-11: Recycling relevant material content in the device and recovery rate**

Material	Recovery rate	Mass in device
Copper	95%	10,28 g
Cobalt	95%	11,25 g
Gold	95%	28,17 mg
Silver	95%	44,19 mg
Palladium	95%	7,5 mg

All burdens as well as credits of the material recovery have been allocated to the Fairphone 3 under study. This has been decided in order not to hinder comparability with the Fairphone 2 LCA study. For the credits' estimation, direct correspondence has

been assumed between recovered secondary material and avoided primary material production.

## 3.5 Scenarios

In addition to the baseline scenario with different years of use, two repair scenarios are calculated, which are described in the following.

### 3.5.1 Repair scenario A

Repair scenario A addresses the repair through module replacement:

- 5 years use
- 1 replacement battery
- And the repair of one module per phone based on repair and insurance statistics:
  - 63% display
  - 16% connectors resulting in
    - 9% top module (earphone jack)
    - 7% bottom module (USB-C connector)
  - 10% camera module
  - 5% speaker
  - 3% back cover and protection bumper
  - 3% mainboard

It is assumed that over the course of 5 years each phone is repaired once. The numbers are roughly based on numbers published by Clickrepair<sup>1</sup> with the following figures:

- 67.4% Display
  - 50.0% housings
  - 33.9% battery
  - 16.1% connectors
  - 7.9% camera

An older study from Clickrepair [click repair 2016] states a share of water damages of 5%. It is assumed that roughly half of these water damages lead to defects on the mainboard.

The battery is not included in the assumption of damages and replacement is based on degradation assumptions (see section 3.2). Additionally, it is assumed that broken housings are more frequent for phones with more fragile (glass) housings. Therefore, the number of replacement back covers is reduced compared to the statistics. The protection bumper is assumed to be replaced together with the back cover.

For the replacement batteries and spare part modules, additional transport and packaging is assumed. The changes in end-of-life are not assessed for the repair scenarios.

### 3.5.2 Repair scenario B

The repair scenario considers the same use phase and replacement rates of modules as repair scenario A. However, repair scenario B considers additional repair of the modules itself on board-level:

- Top module: earphone jack replaced
- Bottom module: new microphone

<sup>1</sup> <https://www.clickrepair.de/images/presse/downloads/pdf/clickrepair-smartphone-repair-study-2019-en.pdf>

- Camera module: new camera
- Mainboard: new power supply unit

For transport distances, a board-level repair in France is assumed. For the repair services, it is assumed that only the broken module and not the whole phone is transported.

It is assumed that 75% of broken modules (with the potential of repair, so no re-transport of e.g. displays) are sent back to Fairphone B.V. and 50% of these could be repaired. This results in 63% new modules still needed for top, bottom, camera module and mainboard plus individual components.

For the board-level repairs, energy consumption of de-soldering and re-soldering processes were measured at a rework station at Fraunhofer IZM to approximate board-level repair in professional environment.

## Materials and methods

Standard activities involved in rework are as follows:

- [1]Desoldering: Application of heat to the PCB and BGA up until the melting point of the solder balls, then picking up the component, commonly with a vacuum nozzle
- [2]Residual solder removal: Application of heat to melt the residual solder on the PCB, and removal with a vacuum nozzle
- [3]Soldering in: The new or repaired (and re-balled) component is placed on the PCB and soldered in using heat (application of heat to the PCB and the BGA component)

Professional board-level repair in practice may be performed using industrial rework stations offering precise pre-programmable temperature and air flow profiles, high placement accuracy and bottom heating of the PCB. This process is approximated in this project using a manual rework station. The power consumption of the rework station in different operational modes was measured using a laboratory power meter.

- Weller Multi-Digital Rework Station WMD 3 (with In-Built Pump)
  - Power Input: 310W
  - Temperature control soldering/desoldering 50-450°C; hot air pencil 50-550°C
  - Pump: max. low pressure 0.7 bar; max. conveyance 20 l/min; hot air max. 10 l/min
- Hameg Programmable Power Meter HM8115-2

Generic profiles were derived from rework training material and referring to standard IPC/JEDEC J-STD-020E. The air flow on the rework station can be set between 10 % and 100 %. The temperature indicates the settings of the machine, not the temperature of the PCB or sample component. The power consumption of each operational mode was measured for at least 30 seconds to obtain average values.

## Results

The energy consumptions shown in Table 3-12 were measured, leading to simplified profile shown in Table 3-13.

**Table 3-12: Desoldering/reflow (hot air flow from nozzle) – measurements from Fraunhofer IZM**

Phase/device status	Air flow [%]	Temperature [°C]	Measured average power consumption [W]
Standby	n/a	n/a	3,38
Heating up	n/a	300	19,46
Operation	50	300	49,04
	50	350	49,39



Phase/device status	Air flow [%]	Temperature [°C]	Measured average power consumption [W]
	75	300	70,39
	75	350	70,39
	100	300	99,17
	100	350	109,43

Table 3-13: Simplified profile for desoldering/reflow energy consumption

Phase / device status	Time [s]	Power consumption [W]	Energy consumption [Ws]
Standby	180	3,4	612
Heating up / 300°C	30	19,5	585
Pre-heat / 300°C; 50%	60	49,0	2.940
Soak / 300°C; 75%	120	70,4	8.448
Reflow / 350°C; 100%	45	109,4	4.923
<b>Total [Ws]</b>			<b>17.508</b>
<b>Total [Wh]</b>			<b>4,86</b>

In a simplified scenario, the above process flow is assumed for both desoldering and soldering in, in addition to residual solder removal described below in Table 3-14.

Table 3-14: Residual solder removal

Phase / device status	Air flow [%]	Temperature [°C]	Measured average power consumption [W]
Standby	n/a	n/a	3,40
Heat up	n/a	300	89,12
Operation	10	300	56,86
	50	300	102,33
	75	300	143,95

The following simplified profile for residual solder removal energy consumption is considered, assuming this process takes place right after desoldering, therefore no standby or heating up is accounted for.

Table 3-15: Simplified profile for residual solder removal

Phase / device status	Time [s]	Power consumption [W]	Energy consumption [Ws]
Operation / 300°C; 75%	30	145	4.350
<b>Total [Wh]</b>			<b>1,21</b>

The energy consumption of the entire process is therefore:

$$4,86 \text{ Wh} + 1,21 \text{ Wh} + 4,86 \text{ Wh} = 10,93 \text{ Wh}$$

## 4 Impact Assessment

Based on material flows defined in the LCI, the life cycle impact assessment (LCIA) will be carried out according to the recognized CML methodology [CML 2001] using LCA software GaBi. For the following impact categories, the results will be displayed and discussed in detail:

- Climate change:
  - Global Warming Potential (GWP) 100 years in kg CO<sub>2</sub> equivalents
- Resource depletion:
  - Abiotic resource depletion (ADP) elements in kg Sb equivalents
  - ADP fossil in MJ
- Human toxicity:
  - Human Toxicity Potential in kg DCB equivalents
- Ecotoxicity:
  - Terrestrial Ecotoxicity Potential in kg DCB equivalents

Normalization, grouping, and weighting of the results (optional steps in the impact assessment of an LCA) will not be applied.

### 4.1 Definition of impact categories

For the impact categories covered in this LCA study, the following definitions from CML are used:

- Global Warming Potential (GWP) 100 years: "Global warming is considered as a global effect. Global warming - or the "greenhouse effect" - is the effect of increasing temperature in the lower atmosphere. The lower atmosphere is normally heated by incoming radiation from the outer atmosphere (from the sun). A part of the radiation is normally reflected from the surface of the earth (land or oceans). The content of carbon dioxide (CO<sub>2</sub>) and other "greenhouse" gasses (e.g. methane (CH<sub>4</sub>), nitrogen dioxide (NO<sub>2</sub>), chlorofluorocarbons etc.) in the atmosphere reflect the infrared (IR)-radiation, resulting in the greenhouse effect i.e. an increase of temperature in the lower atmosphere to a level above normal. [...] The GWP for greenhouse gases is expressed as CO<sub>2</sub>-equivalents, i.e. the effects are expressed relatively to the effect of CO<sub>2</sub>." [Stranddorf 2005]
- Resource depletion: "The model of abiotic resource depletion [...] is a function of the annual extraction rate and geological reserve of a resource. In the model as presently defined, the ultimate reserve is considered the best estimate of the ultimately extractable reserve and also the most stable parameter for the reserve parameter. However, data for this parameter will by definition never be available. As a proxy, we suggest the ultimate reserve (crustal content)." [Oers 2016]
- Abiotic resource depletion (ADP) elements: "The impact category for elements is a heterogeneous group, consisting of elements and compounds with a variety of functions (all functions being considered of equal importance)." [Oers 2016]
- ADP fossil: "The resources in the impact category of fossil fuels are fuels like oil, natural gas, and coal, which are all energy carriers and assumed to be mutually substitutable. As a consequence, the stock of the fossil fuels is formed by the total amount of fossil fuels, expressed in Megajoules (MJ)." [Oers 2016]

- Human Toxicity Potential: “The normalisation references for human toxicity via the environment should reflect the total human toxic load in the reference area caused by human activity, i.e. the potential risk connected to exposure from the environment (via air, soil, provisions and drinking water) as a result of emissions to the environment from industrial production, traffic, power plants etc. Ideally, all emissions of substances potentially affecting human health should be quantified and assessed. However, the multitude of known substances (>100.000) and an even larger number of emission sources logically makes that approach unfeasible. The inventory used for calculating the normalisation references is therefore based on available emission registrations for substances, which are believed to contribute significantly to the overall load.” [Stranddorf 2005]
- Terrestrial Ecotoxicity Potential: “The impact category ecotoxicity covers the possible effects of toxic substances released during the life cycle of a product to the environment. The sources of toxicants are quite different depending on the type of environment as well as the methods used in the assessment of the impact. Consequently, the impact on aquatic and terrestrial systems are usually considered separately. In principle, the normalisation reference for ecotoxicology includes all toxic substances emitted to the environment due to human activities, and it requires extensive data on all types of emissions. In general, however, only few data on environmental releases of toxic substances are available, and the normalisation there-fore relies on extrapolations from a relatively limited set of data. The normalisation reference includes the following emission types: [...] Terrestrial environment: Pesticide use, Agricultural use of sewage sludge, Atmospheric deposition of metals and dioxins” [Stranddorf 2005]

## 4.2

### Results

The assessment results in a GWP of 39.5 kg CO<sub>2</sub>e (see Table 4-1). The main impact for all impact categories is caused by the production phase. Transport and use phase have a smaller impact. EoL has a negative impact value, meaning a positive potential for the environment. This is especially relevant for the impact category ADP elements. Most of this impact could potentially be recovered through recycling (see Figure 4-1.)

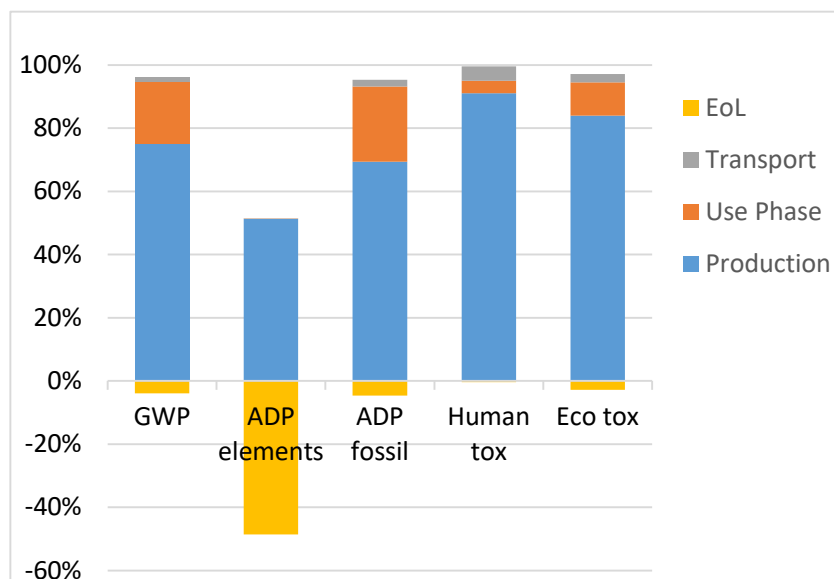


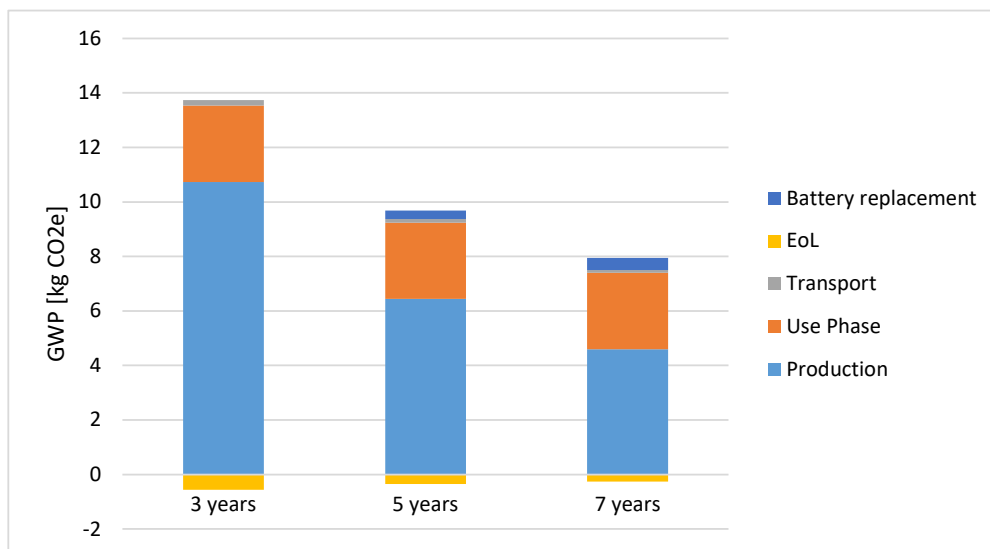
Figure 4-1: Relative impact per life cycle phase (3-year scenario)

**Table 4-1: Absolute impacts of the whole life cycle (3-year scenario)**

	<b>GWP</b>	<b>ADP elements</b>	<b>ADP fossil</b>	<b>Human tox</b>	<b>Eco tox</b>
	kg CO2e	kg Sb eq.	MJ	kg DCB eq.	kg DCB eq.
Totals	3,95E+01	8,40E-05	3,44E+02	8,63E+00	7,60E-02
Production	3,22E+01	1,51E-03	2,63E+02	7,92E+00	6,76E-02
Use Phase	8,40E+00	3,39E-06	9,03E+01	3,42E-01	8,49E-03
Transport	5,94E-01	5,79E-07	8,36E+00	3,98E-01	2,16E-03
EoL	-1,67E+00	-1,43E-03	-1,76E+01	-3,46E-02	-2,29E-03

The difference between the three baseline scenarios is the varying length of the phone’s use-time. The use phase impacts therefore scale directly with number of years in use. Within the production phase, only the impact of the battery changes and, connected to it, a small increase of package and transport impact is caused by the additional transport of the replacement battery to the customer (see Table 8-3 in the annex).

The absolute impact increases with the length of the use phase. However, the impact per year of use decreases with longer use as the main product impact is distributed across a longer useful life (see Figure 4-2). The figure shows a decrease of 29% for the yearly GWP impact category when extending lifetime to 5 years and one of 42% when extended to 7 years.



**Figure 4-2: Impact per year of use (baseline scenarios)**

### 4.3 Contribution Analysis

The following contribution analysis is focussed on the baseline scenario with 3 years of use. Additional numbers for packaging, transport and production of the replacement battery can be found in the annex in Table 8-3.

#### 4.3.1 Production

Within the production phase, the production of the core module and therein specifically the mainboard causes the highest impact for all impact categories (see Figure 4-3 and Table 4-2). For the 5 and 7 years scenario, the impact of 1, respectively 2, batteries needs to be added accordingly, changing the relative impact of the modules only slightly.

The final assembly has an impact between 0.01 % (ADP elements) and 6.8% (GWP) of the total production impact, the display module between 7% (GWP) and 15% (ADP elements). Back cover, protection bumper and screwdriver cause a combined impact of less than 1%. Packaging is only relevant for the impact category eco toxicity (8.2%) due to paper and cardboard production.

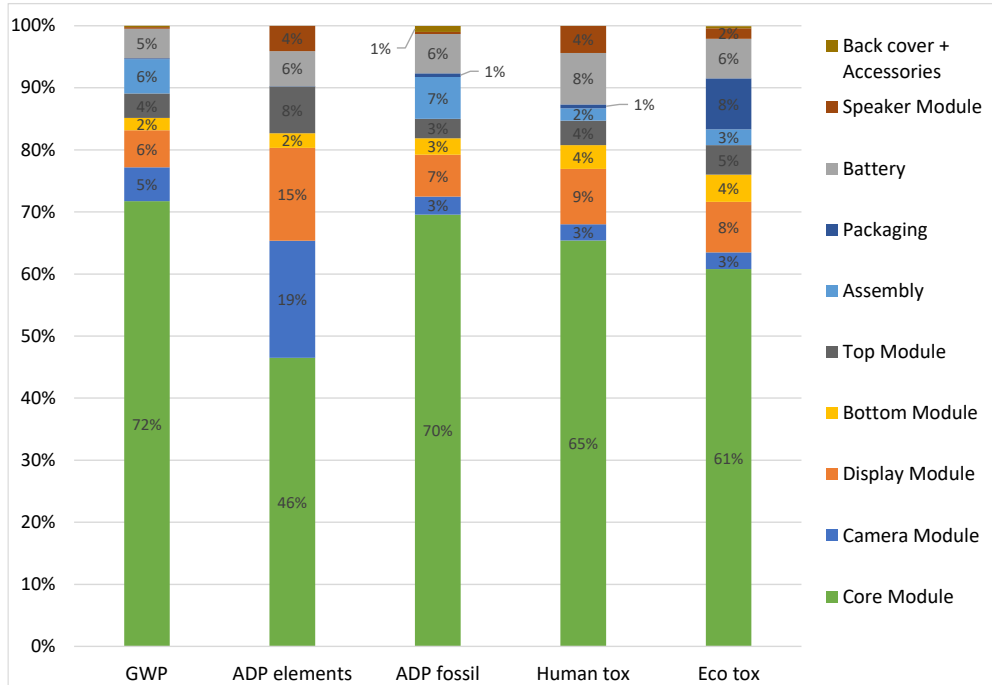


Figure 4-3: Relative impacts of the production phase per impact category (3-year scenario)

Table 4-2: Absolute impacts of the production phase (3-year scenario)

	GWP	ADP elements	ADP fossil	Human tox	Eco tox
	kg CO <sub>2</sub> e	kg Sb-e	MJ	kg DCB-e	kg DCB-e
Production	3,22E+01	1,51E-03	2,63E+02	7,92E+00	6,76E-02
Assembly	1,78E+00	1,48E-07	1,78E+01	1,59E-01	1,70E-03
Back cover	4,24E-02	1,12E-07	1,08E+00	2,36E-03	7,39E-05
Battery	1,54E+00	8,55E-05	1,66E+01	6,57E-01	4,32E-03
Bottom Module	6,35E-01	3,55E-05	7,03E+00	3,06E-01	2,95E-03
Camera Module	1,76E+00	2,85E-04	7,61E+00	2,06E-01	1,83E-03
Core Module	2,31E+01	7,02E-04	1,83E+02	5,18E+00	4,11E-02
Display Module	1,92E+00	2,26E-04	1,77E+01	7,06E-01	5,50E-03
Packaging	4,55E-02	1,07E-07	1,56E+00	4,91E-02	5,55E-03
Speaker Module	7,84E-02	6,23E-05	8,58E-01	3,45E-01	1,14E-03
Top Module	1,27E+00	1,14E-04	8,19E+00	3,10E-01	3,23E-03
Screwdriver	1,26E-02	2,73E-08	2,81E-01	9,25E-04	1,89E-05
Protection bumper	5,58E-02	1,70E-07	1,23E+00	1,76E-03	1,48E-04

Broken down per type of component, the major share is caused by the production impact of the ICs, followed by the PCBs. Connectors have the highest relative impact in the category ADP elements (14.7%) due to the amount of gold used (see Figure 4-4 and Table 4-3).

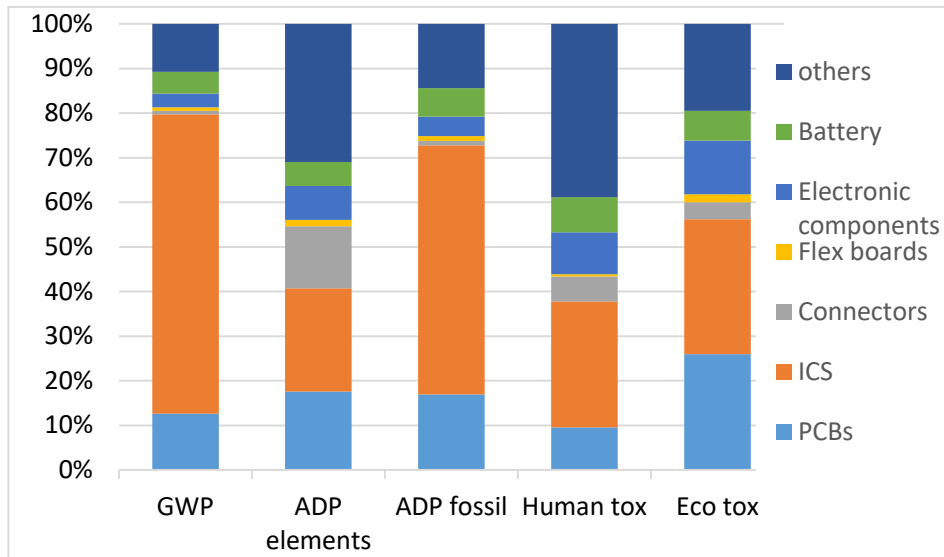


Figure 4-4: Relative impact per component type of the phone (without packaging, assembly, accessories)

Table 4-3: Absolute impact of components

	GWP	ADP elements	ADP fossil	Human tox	Eco tox
	kg CO <sub>2</sub> e	kg Sb e	MJ	kg DCB e	kg DCB e
ICS	2,14E+01	3,70E-04	1,44E+02	2,37E+00	1,95E-02
Connectors	2,54E-01	2,21E-04	2,71E+00	4,68E-01	2,47E-03
Flex boards	2,58E-01	2,34E-05	2,72E+00	4,35E-02	1,14E-03
PCBs	4,03E+00	2,81E-04	4,38E+01	7,98E-01	1,67E-02
Electronic components	9,88E-01	1,21E-04	1,13E+01	7,86E-01	7,75E-03
others	3,43E+00	4,94E-04	3,71E+01	3,25E+00	1,25E-02

The core module causes more than half of the total production impact and is therefore analysed in detail in the following. The mainboard's ICs cause more than 80% of the related GWP impact. Within them, the combined RAM/Flash package causes the major share. The 8-layer rigid PCB has a share between 12% and 31%, whereas the flex boards of the connectors only have a share of 0.3% to 1.1% (see Figure 4-5).

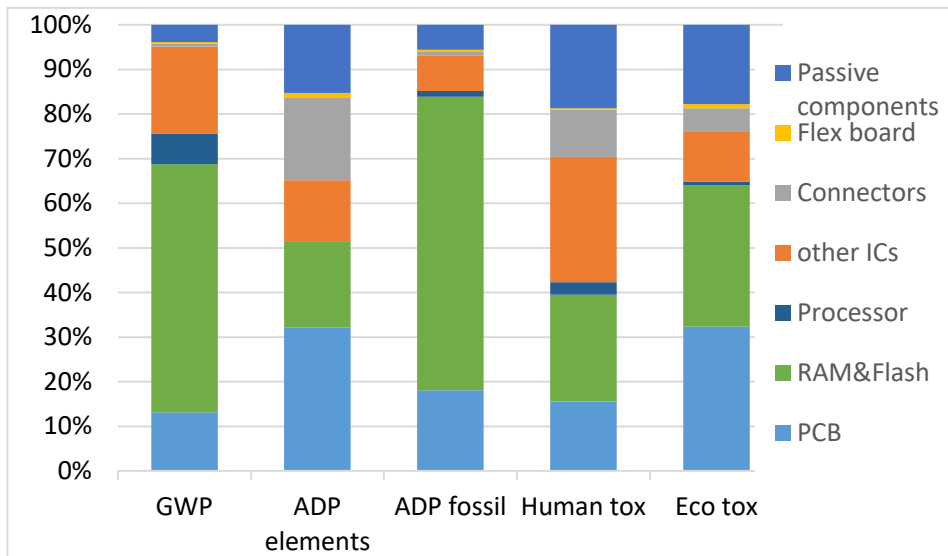


Figure 4-5: Relative impact of the core module per component type

### 4.3.2

#### Use phase

The use phase emissions cause a smaller share of the life cycle emissions of the Fairphone 3. Within the use phase, emissions caused by Germany's electricity mix have a share of 50 to 60% while making up 44 % of the sales (see Figure 8-1 in the annex).

The effect that the relative environmental impact differs from the share of sales is caused by the different energy grid mixes which exist in the countries across Europe. For instance, the German energy grid mix causes more emissions than the European average. Therefore, the relative environmental impact is higher than the share of sales. In contrast, the French energy grid mix has low GHG emissions leading to a significantly lower share in the environmental impact than the share of sales.

There are no major differences regarding the impact per country between the different impact categories (see Figure 4-6 and Table 8-4 in the annex).

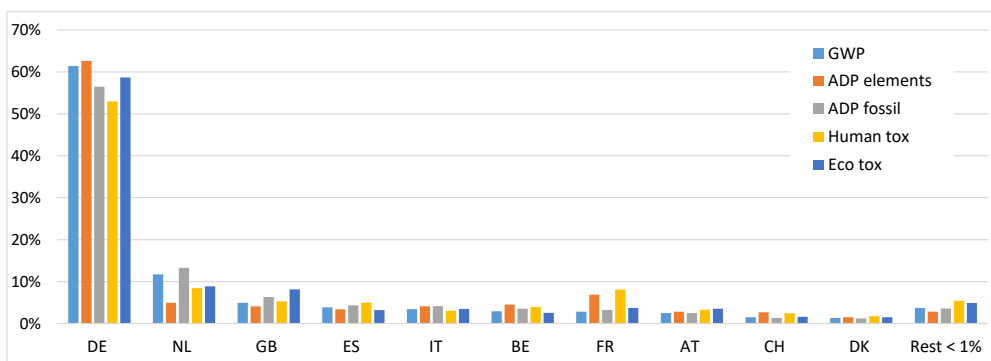


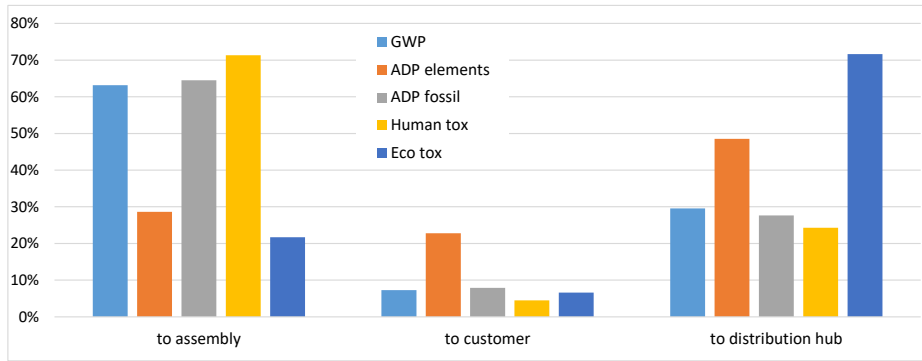
Figure 4-6: Relative impacts of the use phase per country and impact category

### 4.3.3

#### Transport

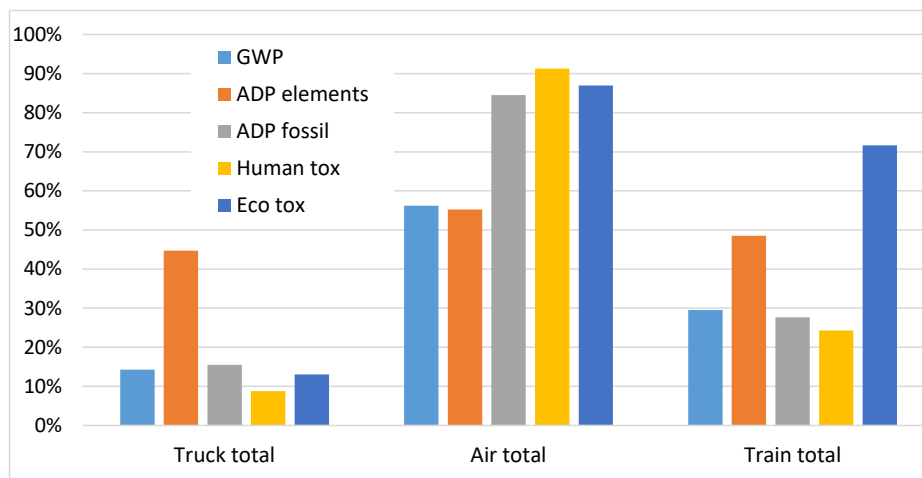
The transportation phase emissions cause a smaller share of the overall life cycle impact. The highest influence of the transportation phase can be seen for the impact category human toxicity.

The main influence from the transport processes is caused by the air freight transport which is mainly located in the transport to some pieces to final assembly (see Figure 4-7).



**Figure 4-7: Relative impact of transportation phases "to assembly", "to distribution", and "to customer" (3-year scenario)**

There are no major differences between the impact categories, except for the impact category Ecotoxicity, which is more influenced by train transport (see Figure 4-8).



**Figure 4-8: Relative impact of transportation phase between modes of transportation "air", "train" and "truck" (3 year scenario)**

The absolute values for the 3-year use scenario can be found in Table 4-4. For the 5-year and 7-year scenario additional transport for one/two batteries is added to this according to Table 8-3 in the annex. The transport to the distribution hub by train is a recent change implemented by Fairphone, which previously took place by air freight. This reduces drastically its related impacts (around 87% lower GWP).

**Table 4-4: Results of the transport phase (3 years scenario)**

Impact category		to assembly	to customer	to distribution hub
GWP	kg CO <sub>2</sub> e	3,75E-01	4,31E-02	1,75E-01
ADP elements	kg Sb-e	1,66E-07	1,32E-07	2,81E-07
ADP fossil	MJ	5,39E+00	6,58E-01	2,31E+00
Human tox	kg DCB-e	2,84E-01	1,78E-02	9,66E-02
Eco tox	kg DCB-e	4,69E-04	1,43E-04	1,55E-03

#### 4.3.4 End-of-Life

The impact values for the end-of-life phase are negative for all impact categories, meaning that they have a positive impact for the environment. The positive effect stems from the precious metal recycling (see Figure 4-9) and thereby mainly from the gold recycling. Battery recycling and copper smelter have a positive value for the toxicity impact categories, but this is outweighed by the impact of precious metal



recycling. Human toxicity shows the strongest differences between the processes. The absolute values compared to whole life cycle small are still small for all impact categories except ADP elements (Table 4-5: Results of the EoL phase (3-year scenario)).

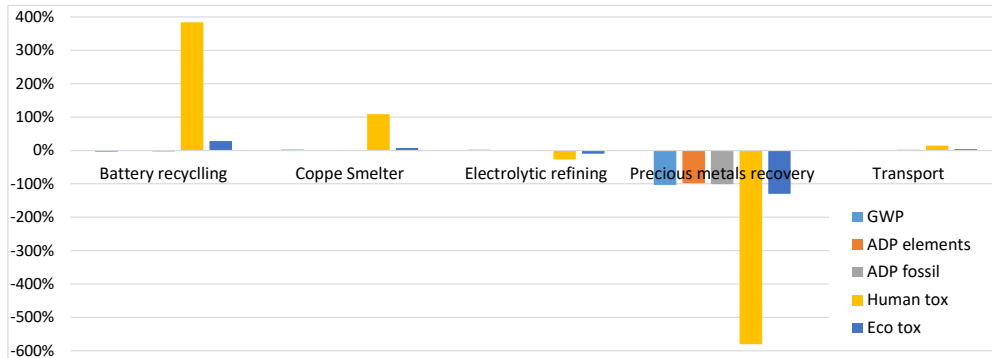


Figure 4-9: Relative impact of EoL phase between battery recycling, copper smelter, electrolytic refining, precious metals recovery and transport (3-year scenario)

Table 4-5: Results of the EoL phase (3-year scenario)

Impact category		Battery recycling	Copper Smelter	Electrolytic refining	Precious metals recovery	Transport
GWP	kg CO <sub>2</sub> e	-6,06E-02	4,84E-02	3,64E-02	-1,72E+00	2,67E-02
ADP elements	kg Sb-e	-7,59E-06	6,40E-09	-2,04E-05	-1,40E-03	6,28E-08
ADP fossil	MJ	-5,53E-01	3,09E-01	9,90E-02	-1,78E+01	4,05E-01
Human tox	kg DCB-e	1,33E-01	3,76E-02	-9,27E-03	-2,01E-01	5,07E-03
Eco tox	kg DCB-e	6,51E-04	1,69E-04	-2,19E-04	-2,98E-03	8,38E-05

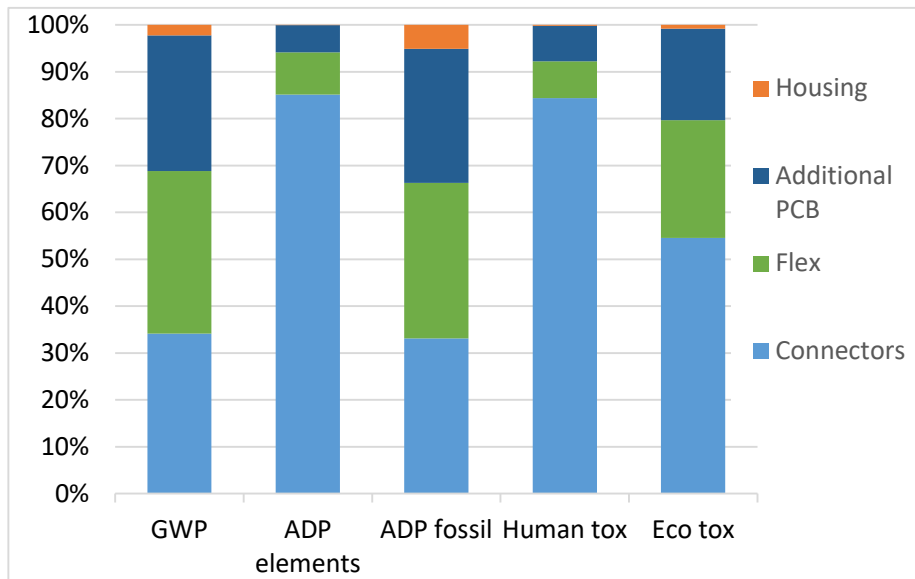
### 4.3.5 Modularity

The impact of the modularity overhead (as it was shown also for the Fairphone 2) is connected to additional module housing, module connectors and the connecting flex boards as well as the additional PCB area for the board-to-board connector between Display and mainboard. The impact is shown in Table 4-6 and Figure 4-10.

Table 4-6: Impacts connected to the modularity

	GWP	ADP elements	ADP fossil	Human tox	Eco tox
	kg CO <sub>2</sub> e	kg Sb eq.	MJ	kg DCB eq.	kg DCB eq.
Totals	7,44E-01	2,60E-04	8,19E+00	5,54E-01	4,53E-03
Connectors	2,54E-01	2,21E-04	2,71E+00	4,68E-01	2,47E-03
Flex	2,58E-01	2,34E-05	2,72E+00	4,35E-02	1,14E-03
Additional PCB	2,16E-01	1,51E-05	2,34E+00	4,21E-02	8,84E-04
Housing	1,64E-02	4,43E-08	4,17E-01	9,18E-04	3,59E-05

For GWP, ADP fossil and Eco tox, additional PCB area, flex cables and connectors cause each about one third of the modularity overhead. ADP elements and Human tox are driven more strongly by gold, leading to the connectors causing a stronger impact. Module housing causes a minor relative impact.



**Figure 4-10: Relative impacts connected to modularity**

The modularity overhead causes between 2.3 % (GWP) and 17.2% (ADP elements) of the total production impact.

## 4.4

### Repair Scenarios

The results of the two different repair scenarios are presented in the following.

#### 4.4.1

##### Repair Scenario A

Table 4-7 shows the additional impact through repair for repair scenario A without battery replacement.

**Table 4-7: Additional impact through repair (scenario A), without battery replacement**

Impact category	Total repair	Spare part	Packaging	Transport
GWP	2,33E+00	2,23E+00	2,28E-02	7,11E-02
ADP elements	2,05E-04	2,05E-04	1,06E-08	1,33E-07
ADP fossil	2,04E+01	1,86E+01	8,49E-01	9,66E-01
Human tox	7,12E-01	6,45E-01	2,99E-02	3,73E-02
Eco tox	8,88E-03	5,45E-03	2,87E-03	5,55E-04

Figure 4-11 shows the results per year of use for the 3-year and 5-year use scenario with and without repair. The impact of the repair itself is rather small and pays off when it leads to longer use. The difference between module replacement (scenario A) and module repair (scenario B) is too small to be visible per year of use. This is mainly caused by the very conservative assumptions of scenario b. Furthermore, the additional benefit of module repair differs significantly between the repaired modules (see discussion in the sensitivity analysis section 4.5).

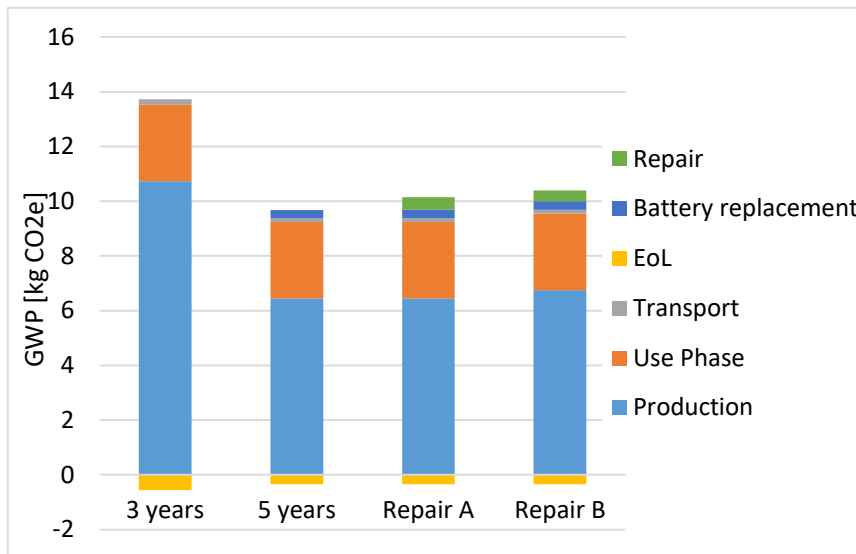


Figure 4-11: Relative impact per year use for the impact category GWP

The recent change in transport done by Fairphone removes a part of the burden associated with repair, namely the air freight emissions. This can be seen in Figure 4-12, where the main drivers in the repair overhead impacts are the spare parts themselves.

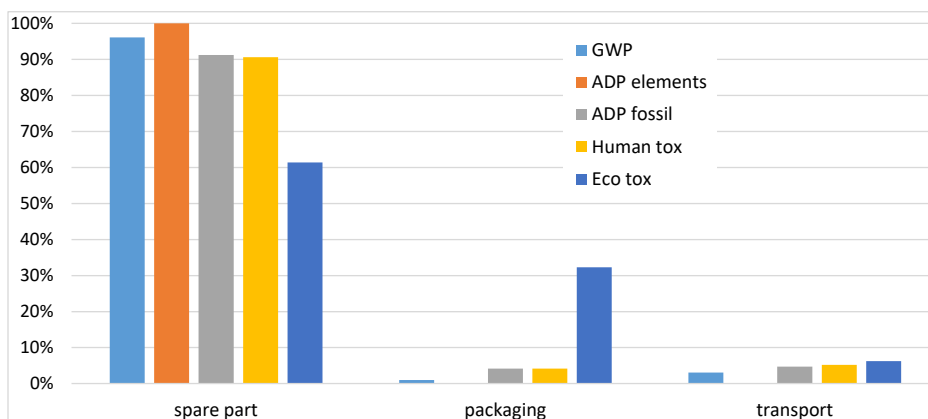


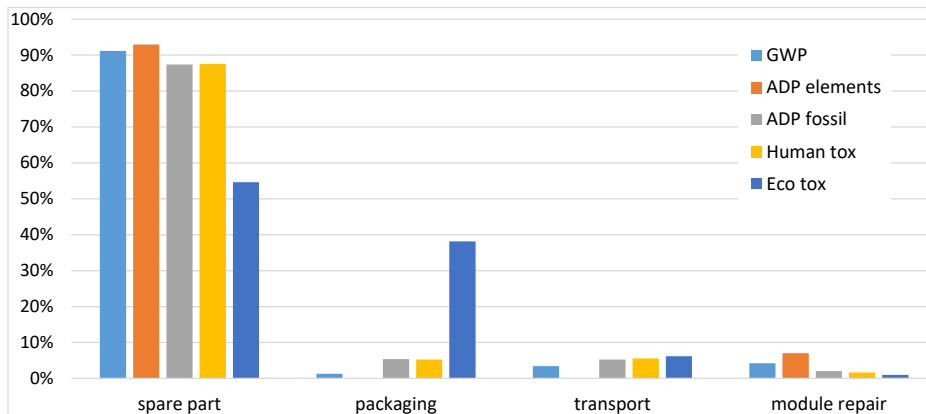
Figure 4-12: Relative impact of repair (scenario A) due to spare part, additional packaging and additional transport

#### 4.4.2 Repair Scenario B

The absolute impact overhead of repairing is reduced due to module-level repair in scenario B. However, the effect is rather low for the assumed share of repairs (see Table 4-8 and Figure 4-13).

Table 4-8: Additional impact through repair (scenario B), without battery replacement

Impact category	Total repair	Spare part	Packaging	Transport	Module repair
GWP	2,03E+00	1,85E+00	2,62E-02	7,02E-02	8,57E-02
ADP elements	1,97E-04	1,83E-04	1,15E-08	1,33E-07	1,39E-05
ADP fossil	1,81E+01	1,59E+01	9,82E-01	9,57E-01	3,73E-01
Human tox	6,59E-01	5,77E-01	3,48E-02	3,66E-02	1,09E-02
Eco tox	8,73E-03	4,77E-03	3,33E-03	5,40E-04	8,54E-05



**Figure 4-13: Relative impact of repair (scenario B) due to spare part, additional packaging and additional transport**

## 4.5

### Sensitivity Analysis and Interpretation

The absolute impact of 39.5 kg CO<sub>2</sub>e as well as the distribution across life cycles are comparable with other smartphone LCAs, which differ in detail but have several similarities as shown by Clément et al.[2020]. Other impact categories are harder to compare as they are not addressed in most of the other studies.

The results and contribution analysis show that the main environmental impact is caused by the mainboard, which includes the ICs and more specifically, the RAM/Flash package. This is in line with other smartphone LCAs, although the relative impact of the RAM/Flash package are higher, which might be caused by the very high die size identified in the IC analysis.

#### 4.5.1

##### Display

The FP3 display was – similar to the FP2 display – modelled based on AUO environmental data as no data set was available in GaBi. The 2018 AUO material and energy consumption per produced panel area was smaller than in 2016 leading to lower relative emissions. Additionally, the IC data set used to model the ICs for the backlight had lower impacts. Although the display size increased from FP2 to FP3, the calculated impact decreased due to the new IC data set. This reduces the impact of the backlight LCDs as well as the display controller ICs. The FP3 has one display controller IC compared to two of the FP2. The overall impact of the display unit is influenced more strongly by the IC data set than by the display panel.

Compared with other smartphone LCAs, the result for the display is quite low. Ercan et al. (2016) state a value for 3.6 kg CO<sub>2</sub>e for a 74 cm<sup>2</sup> display compared to 1.9 kg CO<sub>2</sub>e for 81.9 cm<sup>2</sup> for the FP3 display. Ercan et al. (2016) state a higher electricity consumption for display manufacturing at about 0.1 kWh/cm<sup>2</sup>, compared to 0.008 kWh/cm<sup>2</sup> from AUO (2019). However, the electricity value from AUO does not include the production of upstream materials or display electronics.

#### 4.5.2

##### Connectors

Connectors in the Fairphone 3 are modelled based on the material declaration provided by Fairphone B.V. and their suppliers, therefore neglecting possible losses in the manufacturing processes. For sensitivity reasons, a further analysis was done to assess the possible overhead.

To model the connector manufacturing processes, the following choices were made:

- The functional unit was set to be a female BtB connector and in terms of weight and materials, all connectors are assumed as equal.
- The processes include housing fabrication through injection moulding, the contact fabrication (modelled as sheet rolling of copper) and the contact plating.
- For the process modelling, pre-existing databases from Ecoinvent and Thinkstep were used.

The final individual GWP impact related to the production of a connector was then calculated to be 7.11E-05 kg of CO<sub>2</sub>e. For the sensitivity analysis the focus will be in the board to board connectors, from which Fairphone 3 has 6 in total. A pair each for connecting the top, bottom and camera modules to the mainboard. The overhead modelling does not apply to the pogo pins connector attaching the display and core modules. The total process related overhead would then be 4,266e-4 kg of CO<sub>2</sub>e. Table 4-9 shows that the total share of the connector production alongside the material related impacts is low for the connectors themselves and negligible on a broader scope. It should be borne in mind that the process modelling has a limited scope (not all steps involved in the actual process could be included in the model due to lack of data availability) and that a number of assumptions were done.

**Table 4-9: Connectors manufacturing overhead**

<b>Process impacts</b>	<b>Material impacts</b>	<b>Connectors totals (materials + processes)</b>	<b>Share</b>
[kg CO <sub>2</sub> e]	[kg CO <sub>2</sub> e]	[kg CO <sub>2</sub> e]	
4,266E-4	2,54E-01	2,544E-01	0,17 %

### 4.5.3 Integrated Circuits

ICs have a very strong impact on the overall result. At the same time, it is a topic where up-to-date life cycle data is scarce and technology advances fast. Therefore, these results are connected with higher uncertainties than other aspects of the phone.

All ICs are modelled based on silicon die data, although at least one chip (WiFi) in the Fairphone three contains a Gallium-Arsenide die. However, no life cycle data is available for that material.

Data is scaled by the die size as the area is linked to the production processes more strongly than to the weight of the dies or total chip packages. External data sources were used as described in section 3.1.9.3 as GaBi data on ICs can only be scaled per piece of packaged chip without detailed information on the die size. Thereby the die to package ratio can vary significantly. Ecoinvent data on the other hand is scaled per weight, which is not deemed a reliable factor as especially stacked dies are thinned leading to lower silicon mass but increased production impact. The FP2 LCA contains a comparison with ecoinvent IC data [Proske et al. 2016].

The impact of 3.4 kg CO<sub>2</sub>e/cm<sup>2</sup> for logic chips and 2.5 for DRAM/Flash used in the study are within the range of 2.2 to 4.3 k CO<sub>2</sub>e/cm<sup>2</sup> as used by Andrae et al [214] and Ercan et al. [2016] according to Clément et al. [2020]. The absolute results for the ICs of the Fairphone 3 as well as the resulting share are within the range as reported by Clément et al. [2020] for other smartphone LCAs.

### 4.5.4 Final assembly

Final assembly causes an impact of 1.7 kg CO<sub>2</sub>e per device or a share of 5.5 % of the GWP impact. This is caused mainly by the electricity consumption of 2.2 kWh per phone. There is not much data on energy consumption of assembly processes of

smartphones available, but the number is considerably lower than for the Fairphone 2, for which the manufacturer stated an electricity consumption of 4.7 kWh per phone.

Huawei publishes carbon footprints for their smartphones [Huawei 2018]. The short reports do not state the energy consumption of the final assembly, but the corresponding GWP impact. They range between 2.1 and 3.2 kg CO<sub>2</sub>e per Huawei smartphone, thereby being a little higher but in the same range as the Fairphone assembly.

#### 4.5.5

##### Phone and module repair scenario

The results for the repair scenarios A and B showed little difference between simple module replacement and module repair. This is due to the assumed share of repairs with more than 63% being display replacements, where the display modules themselves cannot be repaired. For the repairable modules, the variations between scenario A and B differ as shown in Figure 4-14). The absolute benefit of module repair is significant for the repair of the mainboard, which also causes the major share of the initial production impact. Keeping as many parts of the ICs in use as possible is therefore beneficial from an environmental perspective. For the camera module, the repair of the module only leads to a reduction of 10% as the submodule with the highest environmental impact (the camera itself) has to be replaced during the process.

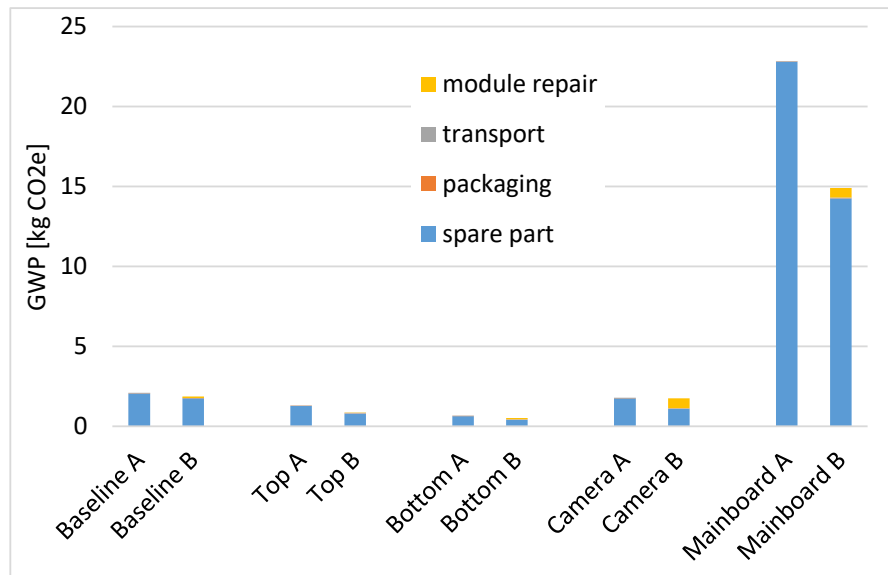
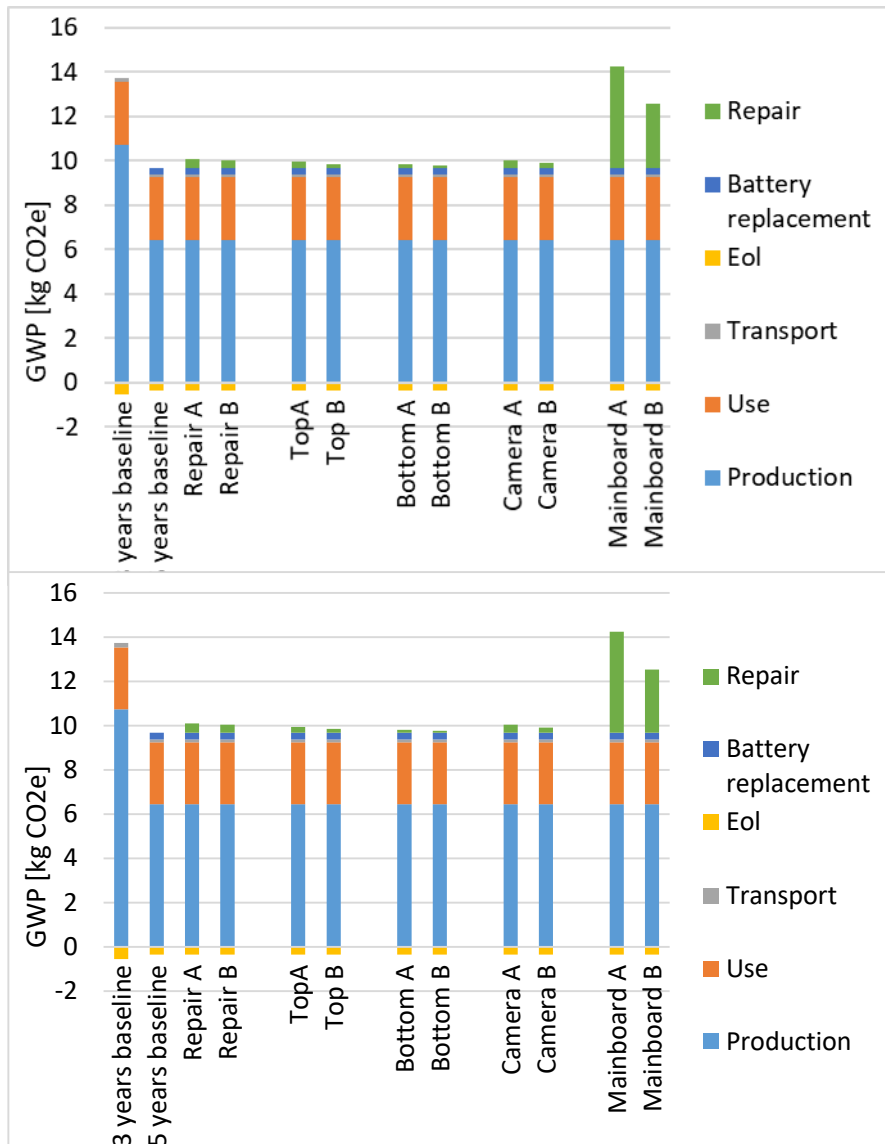


Figure 4-14: Variation between different repairs

Looking at the whole life cycle and the pay-off of smartphone repair, the results show that the environmental impact strongly depends on the module which is replaced. As shown in Figure 4-15, repair leads to reduced emissions per year of use for all parts except the main board. As the main board causes the major share of the absolute impact, replacing it to extend the time of active use by 2 years is not beneficial. However, if this is connected to on-board repair, it is beneficial – even if this still needs a share of 62.5 % new mainboards (as only 37.5% modules can be re-used based on the assumed return and repair rates).



**Figure 4-15: Variation of different repairs – per year of use compared to baseline scenarios**

It is nonetheless important to point out that those results are heavily influenced by the assumptions made in terms of the share of effectively repaired modules. For instance, as seen above the main driver in repair overhead is the production of new modules or parts, which under the assumptions of this study goes from replacing an entire module to replacing 63% (see 3.5.2). Figures below show the potential benefits of module level repair itself, accounting only for the new parts in the production of the B scenario. Module repair in those diagrams refers to the energy use of the reworking machine modelled as explained in 3.5.2.

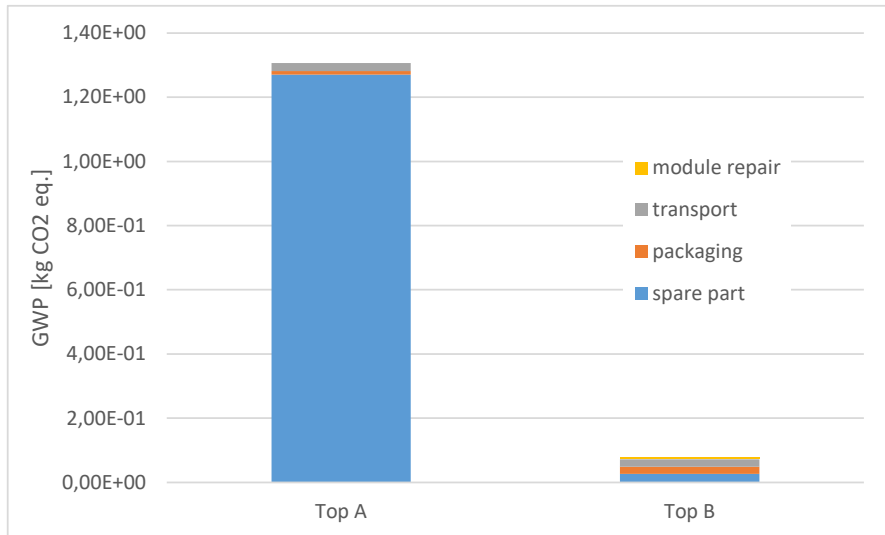


Figure 4-16: Module level repair overhead comparison for top module

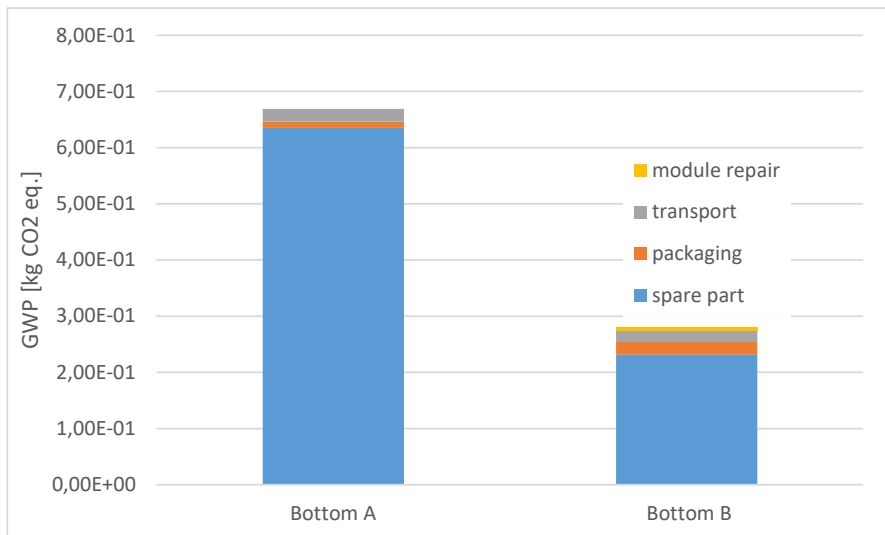


Figure 4-17: Module level repair overhead comparison for bottom module

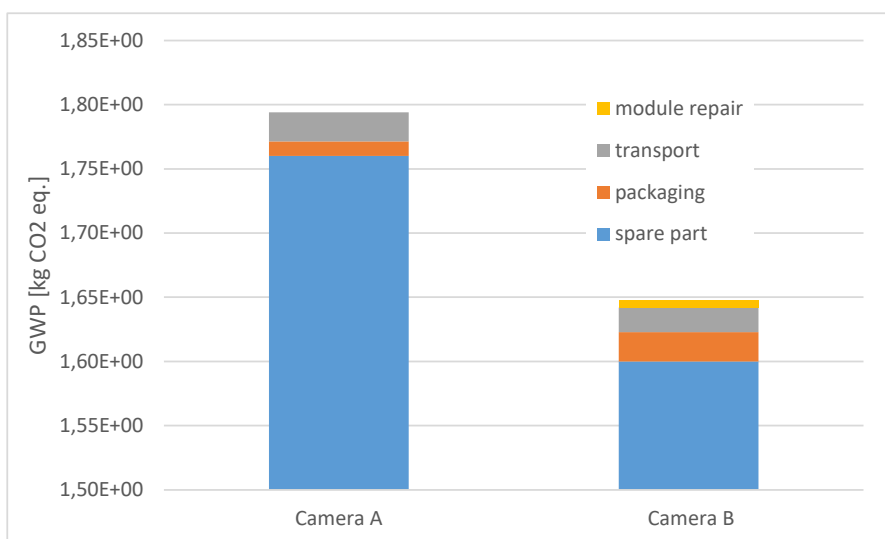
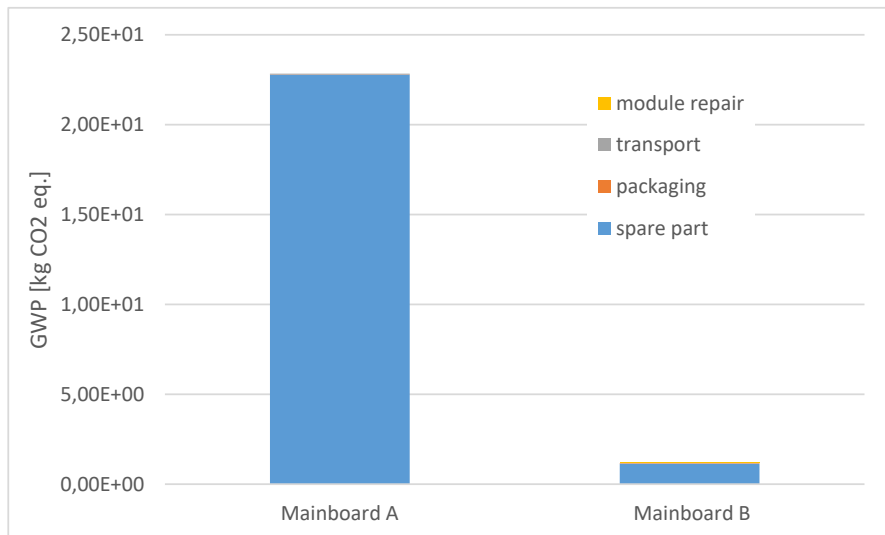


Figure 4-18: Module level repair overhead comparison for camera module





**Figure 4-19: Module level repair overhead comparison for mainboard module**

As seen here, the top and mainboard modules show the highest benefit opportunities since they have the largest production related impacts. The camera module shows the smallest benefit due to the fact that the camera itself it's being replaced within the module, which is the main driver for its production impacts. It is therefore seen that, while the potential benefits of enabling module level repair are noticeable, they are also highly dependent on the replaced pieces and parts as well as the means of transport used for the modules (as commented earlier).

#### 4.5.6 Modularity

The "impact of modularity" is calculated in section 4.3.5 to make a comparison with the Fairphone 2 and show the effect of the new connectors. However, to assign these connectors to the module boards solely to the feature "modularity" is not truly correct, as it neglects that conventional smartphones have more and more connectors on the mainboard, as well, leading flex cables to sub-parts and sub-boards (see Schischke et al. 2019). So, the real hardware differences to achieve modularity are lower than the impact shown there. The only parts really differing from conventional smartphones are the display connector (but even this became smaller compared to the Fairphone 2) and the module housing which have no significant impact on the overall phone.

It can be discussed whether the modular design leads to higher PCB area (not due to the connectors which is calculated in section 4.3.5). The individual module boards do not exist in many other smartphone designs. The impact of the module boards together makes up one third of the mainboard PCB (Table 4-10) due to lower PCB area and less PCB layers.

**Table 4-10: Impact of PCBs**

	GWP	ADP elements	ADP fossil	Human tox	Eco tox
	kg CO <sub>2</sub> e	kg Sb eq.	MJ	kg DCB eq.	kg DCB eq.
PCB totals	4,03E+00	2,81E-04	4,38E+01	7,98E-01	1,67E-02
Mainboard	3,01E+00	2,15E-04	3,27E+01	6,10E-01	1,28E-02
Top module	2,54E-01	1,44E-05	2,76E+00	4,72E-02	9,96E-04
Camera module	1,25E-01	8,47E-06	1,35E+00	2,30E-02	4,84E-04
Bottom module	3,12E-01	2,12E-05	3,38E+00	5,75E-02	1,21E-03
Display module	3,31E-01	2,25E-05	3,59E+00	6,10E-02	1,29E-03

However, the manufactured PCB areas differ across smartphone designs and the total Fairphone 3 PCB area is within the range of conventional smartphone designs and depends strongly on the shape of the PCB. L- and especially U-shaped PCBs lead to

more produced PCB area compared to rectangular PCBs. PCB layout placing on the production panel by the PCB manufacturer also has an impact as the comparison of Fairphone 2 and Fairphone 3 PCB production shows. FP2 PCBs were more strongly nested and closer arranged on the production panel leading to less cut-off area.

#### 4.5.7

##### Comparison with Fairphone 2

In this section, a comparison with the prior Fairphone model will be carried out in order to identify environmental trends with the new design. The Fairphone 2 results were recalculated using the newest life cycle inventory database updates in order to foster comparability between the two models (see Figure 4-20 and Figure 4-21).

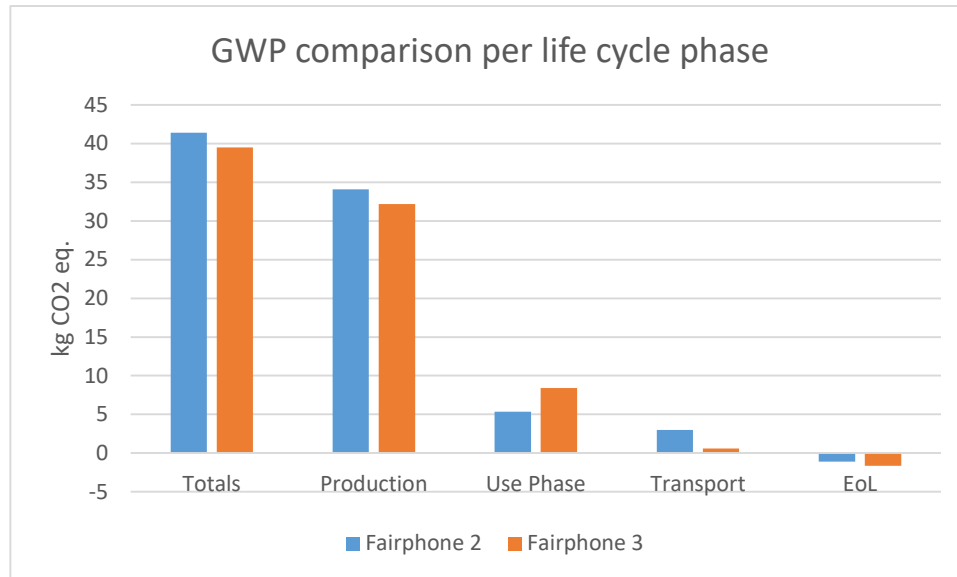


Figure 4-20: GWP comparison per life cycle phase

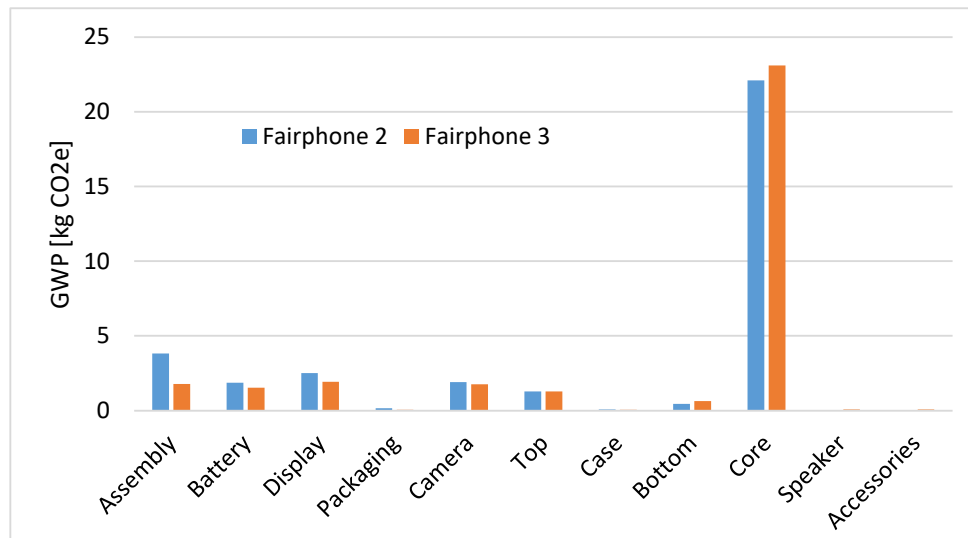


Figure 4-21: GWP comparison at production level

The overall values are quite similar, as seen in Figure 4-20, although the overall relative impacts of the Fairphone 3 are a bit lower. Transport shows the greatest decrease due to the replacing of air freight by train transport from final assembly to the distribution hub. Use phase-related impact has, on the contrary, increased for the newer model due to the higher battery capacity. End of life and production phases seem to be in the

same range as the previous model, although production shows to have a smaller impact in comparison.

In Figure 4-21 the decomposition of the production phase into its constituents can be seen. While the core module shows higher impacts the assembly related impacts and the display ones are lower.

The end-of-Life results show a slight relative increase on environmental benefits, which are tied to a higher amount of recovered gold. This can be attributed mainly due to the improved data availability for the Fairphone 3, where for the majority of components a full material declaration was available.

### Use phase

The base case use phase results show a noticeable divergence between Fairphone 2 and Fairphone 3. Table 4-11 below shows a summary of the main aspects of the use phase modelling for both devices.

**Table 4-11: Use phase comparison**

Characteristic	Fairphone 2	Fairphone 3
Use period (yr.)	3	3
Charging frequency assumed	Daily	Daily
Battery size (Wh)	9,196	11,628
Capacity and efficiency	Constant	Average (with ageing)
GWP (kg CO2 eq.)	5,6	8,4

The two main differences are the following: battery size and charging efficiency. The Fairphone 3 has a bigger battery (3060 mAh compared to 2420 mAh) which, based on the assumption of one complete charging cycle per day increases consequently the amount of energy used by the phone. The other main cause of the difference is the chosen efficiency. The batteries tested in-house at Fraunhofer IZM (see section 3.2) showed a drop on capacity and efficiency. This has in turn been reflected and an average value has been chosen as a proxy. Additionally, in order to estimate the energy use of the phone for one charging cycle in-house testing has been carried out, giving away a higher value as compared to the estimation done based on the charger nominal efficiency and the battery size, which was the approach in the previous model's LCA (Proske et al. 2016).

### Integrated circuits

Integrated circuits are a component where modelling differs between Fairphone 2 and Fairphone 3. Figure 4-22 shows the difference in the impact category of GWP in the ICs of both models, distributed by parts.

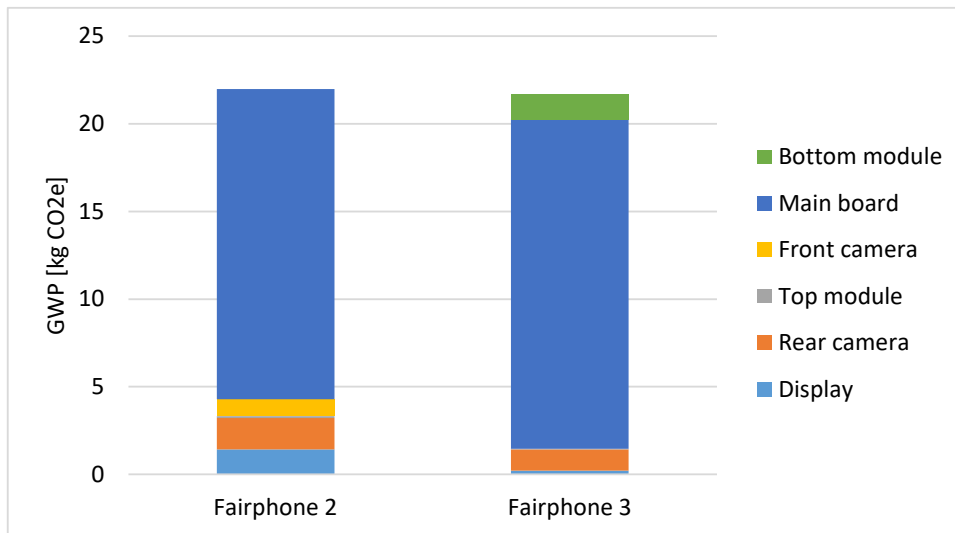


Figure 4-22: GWP impact of IC per module

CT imaging, x-rays and grinding have been used in order to measure the die size of the main ICs of the main board, due to their central role in the most relevant impact categories related to electronics (namely GWP and ADP). Figure 4-23 below shows the difference in the measured areas. Although for the Fairphone 2 LCA, grinding and x-rays were used as well, FP2 ICs were grinded horizontally and FP3 ICs vertically, leading to a better differentiation of stacked dies, which proved to be specially relevant in the Flash memory IC. The rest of the differences in die areas are most likely due to differences in the IC technology of the phone.

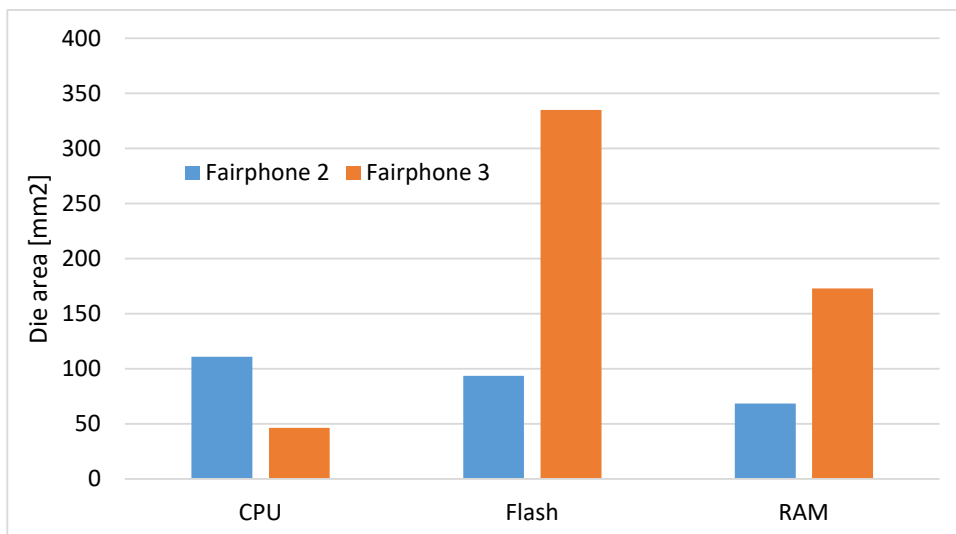


Figure 4-23: Measured die area for the main ICs

When comparing the figure above with Figure 4-22 it can be seen that the main differences in die area for the main ICs in Fairphone 3 and Fairphone 2 models are not directly correspondent in their GHG emissions impact, which are only slightly higher for the FP3 model in the main board and actually a bit smaller as a whole due to a different data source used for the storage and memory chip as explained in section 3.1.9.3.

### Connectors

One of the main design changes following Fairphone 2 were the connectors. Table 4-12 shows the comparison between the GWP and ADP elements impact for Fairphone 2 and Fairphone 3.

**Table 4-12: Connectors comparative impact summary**

Model	Impact	Unit	BtB connectors	Flex cables	Sub-housing	Extra PCB (connector related)
Fairphone 2	GWP	kg CO <sub>2</sub> e	0,94	-	4,21E-02	0,66
	ADP elements	kg Sb e.	7,92E-04	-	9,72E-07	4,02E-05
Fairphone 3	GWP	kg CO <sub>2</sub> e	0,25	0,26	1,64E-02	0,22
	ADP elements	kg Sb e	2,21E-04	2,34E-05	4,43E-08	1,51E-05

As the numbers point out, a noticeable reduction has been achieved in this regard, that is central to the modularity overhead. The main reason for this reduction is a change in the connectors used to bring the modules and the main board together. In the FP2 case pogo pin connectors were used, which are bigger and contain more gold. They were identified as a hotspot regarding the modularity in the FP2 LCA [Proske et al. 2016] and were substituted by flex cables and press-point male female connector pairs in the Fairphone 3. Since those connectors are smaller than the previous pogo pins, the additional PCB area is also reduced and thus the related impacts.

Table 4-12 shows that although Fairphone 3 ends up having more connectors (two pairs of male/female connectors per each flex cable) and a higher flex board use (which was not present in the FP2), the overall impacts are still favourable to the Fairphone 3 design since the pogo pins had more gold and the rigid PCB has greater impacts than flex cable.

### Display

Table 4-13 below shows the comparison between the GWP impact of the display for both FP2 and FP3 as well as their size.

**Table 4-13: Display comparison**

Characteristic	Fairphone 2	Fairphone 3
Size (inch)	5	5,65
GWP (kg CO <sub>2</sub> eq.)	2.67	1.92

Despite the screen being now bigger for the Fairphone 3 the related impact is nonetheless lower. This is due to two main reasons: firstly, as commented above, the corrected IC modelling amounts to a lower impact compared to the modelling used for FP2. On the other hand, the GHG emissions reported by the AUO Environmental Report [AUO 2016, 2019] used as reference show a decrease of around 30 % on the impact per produced area from 2015 to the latest data in 2018. Those therefore outweigh the added impact due to the larger display. Additionally, the FP3 display unit has only one display control IC compared to two display control ICs for the FP2.

### Extra module

Another main difference between the Fairphone 3 and Fairphone 2 models is the extra module: the separate speaker module in the FP3. The impact on the total results is rather low. The speaker module only includes the speaker itself, the housing and the connector and represents only 0.24 % of the GWP impact for production. Table 4-14 below shows the comparison for the relative contribution in GWP for each module in both models.

**Table 4-14: Module GWP contribution comparison**

Module	Fairphone 2 %	Fairphone 3 %
Core	62.5	71.6
Battery	5.4	4.8

Display	7.5	6.0
Camera	5.4	5.5
Top	3.6	4.0
Bottom	1.5	2.0
Speaker		0.2
Back cover	0.2	0.1
Assembly	13.4	5.5
Packaging	0.6	0.1
Accessories		0.2

Impact Assessment

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## 5

# Potential impact of recycled content as input material

Fairphone B.V. developed a list of focus materials in order to invest effort in tackling some environmental and social hotspots:

- Gold
- Copper
- Tin
- Tungsten
- Lithium
- Cobalt
- Neodymium
- Plastics

A separate analysis was carried out to assess the environmental impact of these materials within the phone and to determine a potential reduction of such impact through using recycled materials instead. The analysis is performed for each material individually and may vary between the materials due to different technical possibilities of material retraction and recycling, life cycle data for primary and secondary material and market forces (is the recycling market already established, are there differences in cost and quality, etc.). Due to limited data availability, the environmental impact is limited to global warming potential (GWP) for most materials and also differences in the GWP between different sources will be shown. It should therefore be kept in mind that the presented values for GWP might differ from the values used in the aforementioned LCA. The LCA is mainly calculated with datasets from GaBi whose terms of use do not allow to cite individual impacts of data sets.

The amount of material within the phone is determined in a similar way for all focus materials. The BoM was combined with the material composition as stated by the supplier to calculate the total amount per material, taking into account not only homogenous materials (e.g. copper foils for copper or gold-plated connector pins for gold), but also material within electronic components. If a component is supplied by different suppliers, only the first supplier in the material list is considered.

### 5.1

#### Gold

<b>Gold</b>	<b>0,143 g</b>
Main contributor	Battery, PCBs
Estimated benefit	Increase of 3,146 kg CO <sub>2</sub> eq. in GWP (decrease in all other relevant impact categories)

#### Impact of primary production

The GWP impact of primary gold production varies between 11,500 and 55,000 kg CO<sub>2</sub>e/kg gold according to different studies [Giegrich et al. 2012, Nuss & Eckelman 2014, Mudd 2007, Norgate & Haque 2012, Hagelüken & Meskers 2010, Chen et al. 2018, Dell 2017]. The differences stem mainly from different electricity production (e.g. coal or hydro power) and declining ore grade (Mudd 2007). The majority of sources state values around 15,000 kg CO<sub>2</sub>e/kg gold.

#### Impact for secondary production

The data on the environmental impact of recycled gold is much more limited than on primary gold. According to Dell [2017], the impact is significantly lower for most

environmental impact categories. However, for GWP the environmental impact is about 2.5 times higher – about 37,000 kg CO<sub>2</sub>e/kg gold – due to higher energy consumption in hydrometallurgical processes [Dell 2017]. Calculations with the software GaBi present benefits through recycling, however the numerical results cannot be presented in the public report.

Potential impact of recycled content as input material  
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**Recycling processes and qualities**

The processes for gold recycling are well established and available on a large scale. The environmental impact and technology used depend on the sources of the gold scrap (e.g. jewellery or electronic scrap).

**Market**

Markets for gold recycling are well established. Recycled gold accounted for approximately a third of the total gold supply from 1995 through 2014. Most of this, roughly 90%, is high-value recycled gold, mostly jewellery, gold bars and coins. The other 10% are industrial recycled gold, for example from e-waste. This value has doubled from 2004 to 2014. However, gold content in WEEE is decreasing, meaning that recyclers will have to process larger amounts of scrap to extract the same amount of gold. Gold made up 90% of bonding wires in 2008, for example, a value which had fallen to 50% in 2015 already [Hewitt 2015].

As is the case with many other recycling industries, gold recycling fluctuates in accordance to fluctuations in gold price and economic conditions. Interestingly, economic crisis boost gold recycling as gold is often used as a liquid asset to raise cash. An increase in gold price leads to an increase in gold recycling, as well [Hewitt 2015].

**Conclusion**

Based on the well-established market and technologies for gold recycling even from WEEE and no quality differences between primary and secondary material, recycled gold is widely available on the market. Recycling methods are so well established, in fact, that buyers might not even be able to distinguish, whether they purchased primary or secondary gold. So, there is no additional market stimulation achieved through purchasing recycled gold specifically and rates are mainly influenced by the gold price. Therefore, it is recommended to calculate with a market average for the input material within environmental assessments and focus efforts on good EoL collection and treatment to increase the amounts of devices which enter the correct recycling stream.

**5.2**

**Copper**

<b>Copper</b>	<b>8,145 g</b>
Main contributor	PCBs
Estimated benefits	Decrease of between 41,38 g and 19,22 g CO <sub>2</sub> eq. in GWP

**Impact of primary production**

The impact of primary copper production varies between 2.8 and 5.4 kg CO<sub>2</sub>e/kg copper [Giegrich et al. 2007/2012, Farjana et al. 2019, Nuss & Eckman 2014, BIR 2008].

**Impact for secondary production**

Values given for life cycle data and GWP of recycled Copper vary. Jingjing et al. conducted an LCA on secondary copper production in China and calculated a GWP



value of 0.32 kg CO<sub>2</sub>e/kg recycled copper. In comparison, their LCA yields a GWP value of 3.4 kg CO<sub>2</sub>e/kg copper for virgin copper. The GWP of recycled Copper is, in this case, therefore 90% smaller than that of virgin copper [Jingjing, 2019]. Similarly, the BIR cites 0.44 kg CO<sub>2</sub>e/kg copper recycled from copper scrap [BIR, 2008]. Giegrich et al. conducted an LCA for copper recycling based on industry data and concluded that the recycling of copper scrap containing 60% copper has a GWP of 1.24kgCO<sub>2</sub>/kg recycled copper product [Giegrich, 2007].

Potential impact of recycled content as input material

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### Recycling processes and qualities

Copper is fully recyclable without any loss in quality or quantity [Bonnin 2015 and van Beers 2007]. It was estimated in 2012 that 85% of copper in use could be recovered through recycling [SCF, 2012]. Additionally, recycling methods for copper are well established. Pyrometallurgical recycling is the prevalent method, but an established hydrometallurgical process also exists [Bonnin, 2015].

PCB scrap presents a high concentration of copper, but its recycling suffers from low collection rates, just like other e-waste recycling methods [Veit, 2005].

### Market

Markets for the recycling of copper are well established. In 2008, approximately 37% of copper used worldwide was recycled copper [Bonnin, 2015] while figures for Europe today are up to 50% [ECI, 2018]. Because of its high economic value and comparably large availability in e-waste, recycling copper is economically feasible [Hagelüken, 2006].

### Conclusion

Similarly to gold, recycling technologies and markets for copper recycling are well established. Margins are a lot lower for copper, nickel, and tin than for precious metals. If WEEE recycling is considered, gold, copper and tin will be recycled from the same stream. Therefore, the same approach for considering environmental impact is considered: calculate LCA impacts with a market average for the input material and focus efforts on good EoL collection and treatment to increase the amount of devices which enter the correct recycling stream.

## 5.3

### Tin

<b>Tin</b>	<b>2,48 g</b>
Main contributor	Solder paste
Estimated benefit	Decrease of 42,1 g CO <sub>2</sub> eq. in GWP

### Impact of primary production

The stated impact of primary tin production varies between 2.18 and 17.1 kg CO<sub>2</sub>e/kg tin with two of the three sources citing values around 17 kg CO<sub>2</sub>e/kg tin [BIR 2008, Giegrich et al. 2007, Nuss & Eckman 2014].

### Impact for secondary production

Life cycle data on the recycling of tin could only be found in a report from the Bureau of International Recycling [BIR, 2008]. Here, they state the GWP of recycled tin to be 0.024 kgCO<sub>2</sub>e/kg recovered tin. Seeing as their initial values for primary tin were much lower than the ones from other sources, however, this number should be considered in comparison to the BIR GWP value for primary tin rather than in comparison to the

other sources' values. But even when comparing the value to the BIR GWP value for virgin tin the recycled material's GWP is 99% smaller.

Potential impact of recycled content as input material

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### Recycling processes and qualities

Tin can be recovered through pyro- and hydrometallurgical processes [BIR, 2008]. Metals such as tin are highly recyclable due to their intrinsic properties and relatively high economic value [ITA, 2020]. Approximately 44% of refined tin is being used in PCBs. Recycling of electronic waste is therefore an important factor in securing the tin supply for the upcoming years. One of the main problems of recovering tin from e-waste is, as mentioned above for other materials already, the low collection rate for recycling, with take-back numbers being as low as 12% in some developed countries. As there are also more valuable metals in e-waste, tin has not been a priority in the recovery [Yang, 2017].

### Market

According to the International Tin Association (ITA), the contribution of secondary tin towards the total tin consumption was 31% in 2018. 13% of this was re-refined tin with the remainder being reused or reformulated alloys. According to the ITA the contribution of recycled tin towards the total tin use was steady around 30-35% over the last decade, with dips roughly corresponding to periods of low tin prices [ITA, 2020]. In general, tin is highly used in the electronics industry. Yang et al. assumed in 2017 that at this rate, tin reserves would be depleted 16 years from then – in 2033. Improving the waste collection and recycling processes and increasing the amount of recycled materials is therefore very important. In 2014, for example, the amount of tin in e-waste reached 35% of the mined material in the same year, thus making it a great option to slow down tin depletion [Yang, 2017].

### Conclusion

Tin is highly recyclable. Large amounts of tin mined annually are used within the electronics industry. However, collection and recycling rates of electronic waste leave much to be desired. It is crucial to further stimulate the collection and recycling of electronic waste with a focus on tin, amongst other materials, to secure the tin supply for the upcoming decades.

## 5.4

### Tungsten

<b>Tungsten</b>	<b>0,013 g</b>
Main contributor	Vibration motor
Estimated benefit	Not enough data

### Impact of primary production

The life cycle data for tungsten is very scarce. According to Giegrich et al. [2012] the GWP of tungsten is about 2.9 kg CO<sub>2</sub>e/kg tungsten. Nuss & Eckman [2014], on the other hand, state a value of 12.6 kg CO<sub>2</sub>e/kg tungsten. For the LCA of the Fairphone 3, figures from Giegrich et al. [2012] for tungsten are used, as even the commercial data bases of GaBi and ecoinvent do not contain life cycle data on tungsten.

### Impact for secondary production

No figures on the environmental impact of recycled tungsten are available in literature or commercial data bases, even though significant parts of the world's tungsten supply are covered through recycled tungsten, as suggested by the International Tungsten Industry Association (ITIA) [ITIA, 2016].

## Recycling processes and qualities

Methods for the recycling of tungsten are well established and there are a variety of such available. The level of quality of recovered tungsten differs depending on the process used and input scrap material, but many of the processes are well established and tested [ITIA, 2016].

Potential impact of recycled content as input material  
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## Market

The ITIA suggests that 35% of tungsten used for producing intermediate products in 2016 was recycled [ITIA, 2018]. Tungsten is therefore in the top third of metals when it comes to recycling [UNEP, 2013].

## Conclusion

Tungsten recycling is well established with recycled tungsten making up a significant amount of total tungsten used for production. However, life cycle data is not readily available, thereby making it difficult to estimate the effects of using recycled tungsten. Tungsten is one of the materials with a comparatively high recycling rate, yet there is still room for improvement [ITIA, 2018].

## 5.5

### Lithium

<b>Lithium</b>	<b>5,2 g</b>
Main contributor	Battery
Estimated benefit	Not enough data

## Impact of primary production

Life cycle data for lithium is very scarce. Nuss & Eckman [2014], the only publicly available source found, state a value of 7.1 kg CO<sub>2</sub>e/kg lithium as GWP.

## Impact for secondary production

No lifecycle data on secondary lithium was found, probably because lithium recycling has not been of great interest in the past.

## Recycling processes and qualities

Different types of lithium batteries, such as li-Ion batteries, have been recycled for several decades now. Up until a few years ago, however, the focus was the recovery of scarce metals such as cobalt and nickel [Georgi-Maschler, 2012]. It was not economic to recover lithium, as there was an abundance of natural lithium and demand and prices were comparatively low [Buchert, 2018]. With the increase in demand and in price for lithium, however, mainly due to the increasing production of electronic vehicles, the recovery of lithium from scrap materials is becoming a topic of interest [Buchert, 2018].

It has been stated by some sources, though, that the most prominent recycling technologies for lithium are not yet cost-effective on a large scale [Kushnir, 2015].

Many new research projects on the topic of lithium battery recycling have emerged in the last few years. Most of them, however, heavily focusing on electric vehicle batteries, many proposing a closed-loop approach, thereby not creating secondary lithium for other market segments. Batteries for electric vehicles are much larger than smartphone batteries and their disposal is easier to control, which makes research into the field of recycling them more appealing.

## Market

At the moment, there is no real market for secondary lithium for smartphone batteries with only few companies recovering lithium from scrap materials.

Potential impact of recycled content as input material

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## Conclusion

Recovery methods for lithium are not well established. Much research is conducted and funded in this area mainly focusing, however, on lithium batteries for electric vehicles. It is therefore unlikely to be possible to substitute primary lithium with secondary lithium in smartphone batteries any time soon. An alternative might be using batteries that substitute other materials and combine them with primary lithium (see section on cobalt).

## 5.6

### Cobalt

<b>Cobalt</b>	<b>11,24 g</b>
Main contributor	Battery
Estimated benefits	Not enough data

#### Impact of primary production

Few sources are available on the GWP of cobalt mining and production. Determined GWP values for cobalt vary between 8.3 and 11.73 kg CO<sub>2</sub>e/kg cobalt, depending on the source [Nuss & Eckman 2014, Farjana 2019]. The variation in values cited by the sources is much smaller than for some of the other materials.

#### Impact for secondary production

No lifecycle data on secondary cobalt was found. It was, however, possible to find data on recycled lithium-cobalt-oxide (LiCoO<sub>2</sub>). The only part of the FP3 that contains larger amounts of cobalt is the phone's battery. Recycling information on LiCoO<sub>2</sub> is therefore also valuable [Umicore, 2011].

Umicore lists the GWP value of primary LiCoO<sub>2</sub> as 10.1 kg Co<sub>2</sub>e/kg LiCoO<sub>2</sub>. In comparison, the GWP value of secondary LiCoO<sub>2</sub> is stated to be 2.8 kg CO<sub>2</sub>e/kg LiCoO<sub>2</sub>, leading to a significant reduction in CO<sub>2</sub>-emission. Umicore combines secondary cobalt with newly sourced lithium to produce LiCoO<sub>2</sub>, any reduction in the LiCoO<sub>2</sub>'s GWP value is therefore due to a reduction in the GWP value of cobalt [Georgi-Maschler, 2012].

#### Recycling processes and qualities

Methods for recycling cobalt from a range of applications, such as li-Ion batteries or catalytic converters, exist [Buchert, 2012]. Recovery quotes for cobalt in professional recycling plants are already very good, with some plants recovering up to 95% of materials [Buchert, 2018]. Pyro-metallurgical recovery processes to recover cobalt from smartphone and notebook batteries are also already established. Because of their high cobalt content, li-ion batteries are an attractive end-of-life product [Buchert, 2012]

## Market

The end-of-life recycling rate for cobalt in the EU was estimated to be around 35% in 2016. The old scrap ratio is calculated at 50% [UNEP, 2011]. Recycling cobalt is currently not profitable on a big scale. The number of recycling plants is therefore limited and recycling mainly occurs together with primary production [Kotnis, 2018]. The market for cobalt recycling is not well developed.

Umicore is the biggest recycling company for cobalt from li-ion batteries with an input capacity of 7 000 tons of li-ion and nickel metal hydride batteries in 2011 [Umicore, 2011]. Demand for cobalt is likely going to increase further with an increase in electric vehicles, thus probably also increasing the demand for recycled cobalt. It is, however, likely that most research into this field will concentrate on batteries of electric vehicles.

Potential impact of recycled content as input material

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**Conclusion**

Because demand for cobalt is likely going to increase further in the upcoming years, recycling will gain further importance and methods for recycling cobalt from different applications are already established. It is also already possible to recover cobalt from li-ion batteries on an industrial level. One of the biggest challenges, as with many recycling products, is once again the comprehensive collection and thorough separation of the batteries in preparation for shredding [Buchert, 2012].

5.7

Rare earth (neodymium)

<b>Neodymium</b>	<b>0,17 g</b>
Main contributor	Vibration motor (magnet)
Estimated benefits	Not enough data

**Impact of primary production**

Nuss & Eckman [2014] were, again, the only publicly available source found on life cycle data of neodymium. They state the GWP value of neodymium to be 17.6 kg CO<sub>2</sub>e/kg neodymium.

**Impact for secondary production**

No life cycle data on the recycling of neodymium could be found, which is likely due to neodymium recycling being an absolute niche market.

It was, however, possible to find life cycle data on the recycling of neodymium-iron-boron magnets (NdFeB), which is a common type of neodymium magnet. Jin et al. conducted an LCA for a closed-loop-approach to NdFeB-magnet-recycling and concluded that the GWP value for recycled NdFeB magnets was 12.5 kg CO<sub>2</sub>e/kg produced NdFeB-magnet, while it was 27.6 kg CO<sub>2</sub>e/kg for virgin NdFeB magnets. Recycling thereby halves the GWP of NdFeB magnets [Jin, 2016]. These values should, however, be taken with caution as the recycling process used in this study is only effective if the magnet is already separated from other parts. Due to the nature of the application this would not be the case for the FP3, requiring further pre-processing steps and thereby probably increasing the GWP.

**Recycling processes and qualities**

Ciacci, as well as others, states that the recycling rate for neodymium is below 1%. The often very small amount of neodymium in products makes recovery difficult and not economically feasible. For this reason, recycling processes are not well developed [Ciacci, 2019]. Schebek even goes as far as considering none of the currently available recycling methods for neodymium to be on an industrial scale level [Schebek, 2019]. Currently used recycling methods are very energy-intensive and use large amounts of acid to recover the rare earth materials, but less environmentally impactful recycling methods are already being researched [Schebek, 2019.]

**Market**

The market for neodymium recycling is small and not well developed [Ciacci, 2019]. With an increase in electronic vehicles, research into recycling possibilities for

neodymium and rare earth elements in general might become more prominent [Schebek, 2019].

Potential impact of recycled content as input material

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## Conclusion

The market of neodymium recycling is not well developed. Recycling methods are lacking and often not economically feasible. As of right now, it does not seem possible to substitute the neodymium in the FP3's magnets with recycled neodymium.

## 5.8

### Plastics

Plastic is different from the other "focus materials" as it does not describe a specific material, but rather a material group, which is present in many different parts of the phone. One way to differentiate between the different types of plastic could be to separate them into plastics for structural parts (midframe, housings, etc.) and functional parts (e.g. plastics within PCBs, connectors, etc.) In this analysis on recycled content, we chose to focus on structural plastics used for mechanical parts.

For the Fairphone 3, the module housing, midframe and back cover are made of polycarbonate (PC). Additionally, the protection bumper is made from a single material: TPU.

#### Impact of primary production

##### TPU

Data on TPU is very limited in literature as well as in LCA data bases (incl. GaBi and ecoinvent). According to Biron 2018, primary TPU has a GWP of 4.1 kg CO<sub>2</sub>e/kg TPU. This is in line with the value given for rigid PU according to PlasticsEurope [2005] with 4.2 kg CO<sub>2</sub>e/kg PU. However, the production process of TPU can also be compared to other thermoplastics. ABS has – in comparison – a fusion temperature similar to TPU and a GWP of 3.1 kg CO<sub>2</sub>e/kg ABS according to PlasticsEurope [2015]. PA with a higher fusion temperature than TPU has a GWP of 6.4 kg CO<sub>2</sub>e/kg PA [PlasticsEurope 2014 -b].

There are also new material inventions being launched by companies trying to lessen the carbon footprint of TPU. One attempt is, for example, to use CO<sub>2</sub>, which was already created in the production phase, thereby lessening the impact of the virgin TPU produced [Covestro, 2020]. However, these methods are rather new and there is next to no life cycle data publicly available.

##### PC

Life cycle data on polycarbonate is widely unavailable. PlasticsEurope [2019], the only source found, cites the GWP value for PC to be 3.4 kg CO<sub>2</sub>e/kg PC.

#### Impact for secondary production

No life cycle data was found on the impact of secondary production of TPU and PC.

Wäger and Hischier performed a life cycle analysis on the recycling of mixed plastics-rich WEEE and found the GWP for the production of post-consumer-recycled plastics to be only a fifth of that for the production of virgin plastics [Wäger & Hischier, 2015]. They consider a mix of plastics (ABS, PP and HIPS) and do not give absolute numbers, but the tendency is clear.

Garraín et al. conducted an LCA on HDPE recycling with data from the Italian recycling industry and compared it to other sources [2007]. Reversing their normalisation of values, the secondary HDPE has a GWP value of 0.86 kg CO<sub>2</sub>e/kg HDPE. The values they cite from ecoinvent, Buwal and Plasticseurope for the GWP value of virgin HDPE

are around 5.8 to 6.63 kg CO<sub>2</sub>e/kg HDPE, thus reducing the GWP of HDPE by almost 90% through using secondary HDPE. Newer data from Plasticseurope, however, lists the GWP of virgin HDPE at 1.8 kg CO<sub>2</sub>e/kg material [Plasticseurope, 2014 -a]. Unfortunately, no newer data on the GWP for secondary HDPE was found.

Potential impact of recycled content as input material  
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While these types of plastics are not used within the FP3 they clearly indicate a tendency: using secondary plastics reduces the GWP of the parts in question significantly when compared to using virgin plastics.

### **Recycling processes and qualities**

Plastics are, in difference to metals, not recyclable without quality losses. The number of recycling cycles, which are possible, depend on the plastic type and the needed quality. Each cycle leads to down-cycling.

Additionally, certain additives and especially glass fibres used to enhance strengthening of materials such as PC lead to materials, which are not recyclable.

Coherent information on TPU recycling is hard to find. Only few companies seem to be recycling TPU with often highly individualized methods, depending on the type of input [sikoplast, 2015]. Some companies mix secondary and primary TPU granulate to compensate for potential losses in quality during the recycling process [malz-polytec, n.d.]. According to BASF a maximum of 30% of TPU regenerate can be mixed into primary TPU [BASF, n.d.].

As for PC, the typical recycling process is to shred the parts and turn them into PC granulate. There are, however, also other recycling methods available [plastic expert, n.d.]. Little information on the quality of recycled PC was found. Recycled PC may show a reduced impact resistance and resilience in general. It is possible to reduce this effect through additives [AZoM, 2012].

### **Market**

There is a market for recycled plastics. However, currently the market is under-utilized, and potential production volumes exceed purchase volumes. Problems are varying quality and colour variations. Therefore, design for recycling and design from recycling should be considered. To enable the use of recycled content, it should be analysed which material qualities are really necessary from a design perspective and which are requested just out of routine.

### **Conclusion**

As the market is still growing and needs stimulation, the use of recycled input material does actually enhance the market. Therefore, it is also arguable that LCAs calculated with recycled input materials and using recycled plastics should be a focus strategy in design for environment.

## 6 Conclusions and Recommendations

The results of the Fairphone 3 LCA show that environmental impacts are production driven, with the electronic components causing the main impact. Housing and structural parts play a minor role on the overall impact. Design aspects such as form factor influence the whole LCA of the device, mainly through impacts on the display and battery size, but not through the impact of housing material.

As the main impact is caused by production, prolonging the use phase is still a strong measure to influence the overall environmental impact for all impact categories except ADP elements, which can be reduced through efficient precious metal recycling. The comparison of 3, 5 and 7 years of use shows that the impact per year of use drops significantly with longer lifetime. This is still the case if repair is needed, as shown by the repair scenarios. However, as analysed in the sensitivity analysis, replacing the core module/mainboard with new modules is only beneficial if the additional time of use is as long as the use-time before the repair, because the mainboard causes the major share of environmental impact. With board-level repair, repair again becomes beneficial in case of mainboard replacement, being nonetheless dependent on the replaced parts and pieces and the extent to which said reparations can actually take place.

The “modularity overhead”, which is caused by the design features allowing for repair, causes a lower impact than for the Fairphone 2 due to smaller connectors with less material usage. Additionally, comparison with conventional smartphones shows that small press-point connectors with flex cables are no stand-alone feature of the Fairphone anymore, so the additional impact through the feature of modularity would be even lower.

As described in the inventory and in the interpretation, the availability of specific and up-to-date life cycle data on electronics is still not sufficient and discrepancies between different data bases and sources is high. Nevertheless, the overall results are deemed reliable.

### ICs

ICs cause the major share of environmental impact and are at the same time directly enabling the functional spectrum of the device. Limiting or reducing ICs is therefore not a sensible option to improve the impact of the device as it would be done for material-driven parts. ICs production impact decreases over time when technology advances as it is shown by e.g. Boyd [2012].

Nevertheless, balance between designing an up-to-date product which can keep up with on-going trends and avoiding over-dimensioning is needed at the same time.

### PCBs

PCB area is directly connected to environmental impact. Area and number of layers should therefore be reduced where possible, including efficient production and reduced cut-offs. Reducing the needed area through different connector design was already a good development from Fairphone 2 to Fairphone 3.

### Connectors

The new Fairphone 3 connectors are a progress from environmental perspective as they need less material and less PCB area. Possible further reduction of material should be carefully aligned with reliability considerations as the main the active years of use of the phone as an important parameter for the overall impact. Material reduction should therefore not limit reliability. However, in that context, the new connectors are expected to be more reliable despite their lower material footprint.



## Display

Display size is directly connected to the environmental impact of the display panel and the housing. However, both of them have only a small overall impact. Display impact is more strongly electronics- than panel-driven. Nevertheless, the display size also impacts the energy consumption of the phone leading to a need for a bigger battery and/or more charging cycles. Reducing the display size would therefore be favourable from environmental perspective but has to be considered carefully with market trends as it is directly linked to purchasing decisions.

## Mode of transportation

Fairphone has recently changed the transportation from the production sites to its distribution hub via train for most of its shipments. This has shown to reduce notably the transport related environmental impacts as well as reducing the repair overhead, although delays compared to air shipping are also to be expected.

Additionally, reduced packaging for spare modules has the potential to reduce associated transport emissions as these parts have a high relative weight of packaging.

## Data availability/acquisition

Up-to-date and specific life cycle data for electronics is scarce. Collecting primary data from component manufacturers is time consuming and difficult, as e.g. confidentially problems occur. Therefore, it was not possible to derive primary data on production processes from component suppliers within this study. Nevertheless, data on the final assembly, PCB production layouts as well as the majority of full material declarations were available for the LCA. Fairphone B.V. should pursue this good work to derive primary data. Focus on the primary data collection should be on parts and components with a high production impact:

- ICs, especially CPU and memory
- Display
- PCBs
- Battery

Such primary data has the potential to improve the quality of the LCA and enhance accurate fitting to the specific Fairphone characteristics. It also builds the foundation for an individual hotspot analysis in the Fairphone manufacturing process.

The effect of an increased share of primary data on the numeric LCA results is difficult to predict. More detailed analyses often result in higher estimated environmental impacts as more processes and materials are covered. This should, however, not be seen as a drawback, as it still helps to improve the overall quality of the assessment and increase the knowledge about the product's manufacturing processes.

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# 8 Annex

## 8.1 Distribution of sales and transport

**Table 8-1: Distribution of sales**

Country	Share
Germany	44.136%
France	14.363%
Netherlands	8.838%
United Kingdom	5.896%
Belgium	5.771%
Spain	4.481%
Switzerland	3.520%
Austria	3.338%
Italy	3.308%
Sweden	2.437%
Denmark	1.712%
Norway	1.117%
Luxembourg	0.492%
Ireland	0.466%
Finland	0.315%
Czech Republic	0.298%
Portugal	0.250%
Poland	0.129%
Hungary	0.112%
Estonia	0.056%
Slovakia	0.056%
Croatia	0.052%
Slovenia	0.047%
Greece	0.043%
Romania	0.043%
Latvia	0.022%
Liechtenstein	0.022%
Cyprus	0.022%
San Marino	0.013%
Lithuania	0.013%
Monaco	0.013%
Malta	0.009%
Bulgaria	0.0043%

**Table 8-2: Transport to customer**

Share of sales	Country	Distance	Weighted tkm
44.136%	Germany	442.77	7.55E-02
14.363%	France	814.08	4.51E-02
8.838%	Netherlands	97.66	3.33E-03
5.896%	United Kingdom	1028.4	2.34E-02
5.771%	Belgium	183.75	4.09E-03
4.481%	Spain	1702.38	2.95E-02
3.520%	Switzerland	758.87	1.03E-02
3.338%	Austria	979.41	1.26E-02
3.308%	Italy	1550.72	1.98E-02

Share of sales	Country	Distance	Weighted tkm
2.437%	Sweden	1551.77	1.46E-02
1.712%	Denmark	808.31	5.34E-03
1.117%	Norway	1374.12	5.93E-03
0.492%	Luxembourg	254.21	4.83E-04
0.466%	Ireland	1237.63	2.23E-03
0.315%	Finland	2500.37	3.04E-03
0.298%	Czech Republic	910.92	1.05E-03
0.250%	Portugal	2041.42	1.97E-03
0.129%	Poland	1062.45	5.31E-04
0.112%	Hungary	1365.7	5.91E-04
0.056%	Estonia	2094.64	4.54E-04
0.056%	Slovakia	1419.83	3.08E-04
0.052%	Croatia	1350.95	2.70E-04
0.047%	Slovenia	1210.66	2.22E-04
0.043%	Greece	2541.71	4.23E-04
0.043%	Romania	1955.13	3.25E-04
0.022%	Latvia	1881.52	1.57E-04
0.022%	Liechtenstein	776.58	6.48E-05
0.022%	Cyprus	3771.74	3.15E-04
0.013%	San Marino	1313.81	6.54E-05
0.013%	Lithuania	1648.11	8.21E-05
0.013%	Monaco	1303.3	6.49E-05
0.009%	Malta	2577.61	8.56E-05
0.004%	Bulgaria	2363.06	3.92E-05

## 8.2

### Results

#### 8.2.1

##### Battery replacement

Table 8-3: Results for the replacement of one battery

Impact category	Unit	Battery production	Battery packaging	Battery transport
GWP	kg CO <sub>2</sub> e	1,54E+00	1,61E-02	4,40E-02
ADP elements	kg Sb eq.	8,55E-05	4,32E-09	8,21E-08
ADP fossil	MJ	1,66E+01	6,10E-01	5,95E-01
Human tox	kg DCB eq.	6,57E-01	2,52E-02	2,31E-02
Eco tox	kg DCB eq.	4,32E-03	2,41E-03	3,42E-04

#### 8.2.2

##### Use phase

Table 8-4: Absolute impact of the use phase per country (3 year scenario)

	GWP	ADP elements	ADP fossil	Human tox	Eco tox
	kg CO <sub>2</sub> e	kg Sb-e	MJ	Kk DCB-e	kg DCB-e
Use Phase	2,80E+00	1,13E-06	3,01E+01	1,14E-01	2,83E-03
DE	1,72E+00	7,08E-07	1,70E+01	6,04E-02	1,66E-03
NL	3,28E-01	5,56E-08	4,00E+00	9,63E-03	2,50E-04
GB	1,38E-01	4,61E-08	1,90E+00	6,03E-03	2,30E-04
ES	1,08E-01	3,82E-08	1,30E+00	5,67E-03	9,12E-05



	<b>GWP</b>	<b>ADP elements</b>	<b>ADP fossil</b>	<b>Human tox</b>	<b>Eco tox</b>
	kg CO <sub>2</sub> e	kg Sb-e	MJ	Kk DCB-e	kg DCB-e
IT	9,67E-02	4,61E-08	1,24E+00	3,49E-03	9,88E-05
BE	8,17E-02	5,11E-08	1,06E+00	4,49E-03	7,17E-05
FR	7,85E-02	7,79E-08	9,73E-01	9,22E-03	1,05E-04
AT	6,97E-02	3,17E-08	7,48E-01	3,74E-03	1,00E-04
CH	4,16E-02	3,01E-08	3,95E-01	2,79E-03	4,49E-05
DK	3,66E-02	1,71E-08	3,62E-01	2,00E-03	4,21E-05
IE	1,79E-02	1,86E-09	2,10E-01	5,06E-04	1,04E-05
LU	1,58E-02	6,96E-09	1,58E-01	6,00E-04	1,54E-05
CZ	1,41E-02	2,28E-09	1,42E-01	3,78E-04	1,25E-05
LV (Rest)	1,27E-02	1,94E-09	1,52E-01	6,19E-04	2,40E-05
PL	8,36E-03	4,57E-10	8,15E-02	2,88E-04	6,89E-06
SE	7,85E-03	1,03E-08	5,51E-02	1,83E-03	3,46E-05
PT	6,73E-03	1,66E-09	7,96E-02	3,59E-04	7,08E-06
FI	4,55E-03	9,72E-10	4,60E-02	4,16E-04	7,59E-06
EE	3,96E-03	1,29E-10	3,73E-02	1,25E-04	4,31E-06
HU	3,31E-03	5,94E-10	3,53E-02	2,73E-04	6,00E-06
NO	2,42E-03	3,39E-09	1,75E-02	5,06E-04	2,22E-06
GR	2,23E-03	4,54E-10	2,27E-02	9,94E-05	3,30E-06
SK	1,64E-03	3,66E-10	1,66E-02	7,15E-05	1,86E-06
RO	1,31E-03	3,55E-10	1,46E-02	6,81E-05	1,73E-06
SI	1,23E-03	2,80E-10	1,21E-02	5,24E-05	1,29E-06

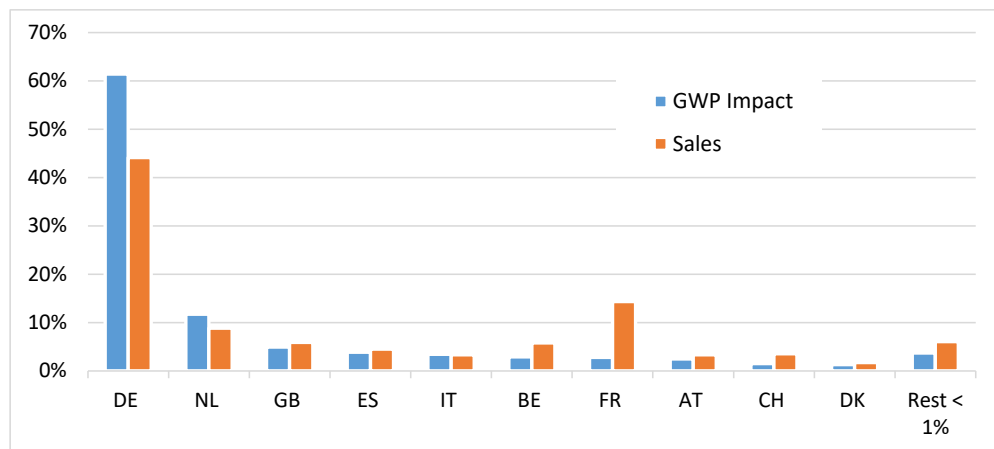


Figure 8-1: Environmental impact GWP in relation to share of sales

## 8.3

### Inventory lists

The following tables describe the inventory lists how the BOM is reflected in the GaBi model.

Level refers to the model in GaBi whether this is a baseline process (process), a process with further inputs (further inputs) or a plan. Scale in Gabi refers to the amount, weight or area that is entered as reference flow in GaBi.

#### 8.3.1

##### Core Module

**Table 8-5: Inventory list core module**

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
8-8902-00-0001	Main Board Ass'y_8902_NATURAL_Main board		#NV	1		see below		
8PCB-8902-0001	PCB_8902_QUAD-BAND_Main board	Electronics, PCBA,	1,85E+01	1		Mainboard PCBA - Core Module FP3	plan	
301-1000-00402	Chip NTC_100 Kohm_± 1%_1/10 W_0402_2.0mm_MURATA_N/A	Electronics, Resistor, MLCR thick film	1,15E-03	2	0402	GLO: Resistor thick film flat chip 0402 (0.75mg) ts	process	6
301-1000-00969	Chip NTC_100 Kohm_± 1%_1/10 W_0201_2.0mm_MURATA_N/A	Electronics, Resistor, MLCR thick film	2,47E-04	1	0201	GLO: Resistor thick film flat chip 0201 (0.15mg) ts	process	120
301-1000-01087	Chip resistor_0.01 Ohm_± 1%_1/2 W_0805_4.0mm_TA-I_N/A	Electronics, Resistor, no datasheet found	3,69E-03	1	0805	GLO: Resistor thick film flat chip 0603 (2.1mg) ts	process	1
301-1000-01010	Chip resistor_1.40 Kohm_± 1%_1/20 W_0201_2.0mm_RALEC_N/A	Electronics, Resistor, no datasheet found	2,24E-04	1	0201	covered with 301-1000-00969		
301-G000-00001	Chip resistor_1.00 Kohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	4	0201	covered with 301-1000-00969		
301-G000-00002	Chip resistor_1.00 Kohm_± 5%_1/20 W_0201_2.0mm_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	4	0201	covered with 301-1000-00969		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
301-G000-00072	Chip resistor_10.0 Kohm_± 1%_1/20 W_0201_2.0mm_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	4	0201	covered with 301-1000-00969		
301-G000-00082	Chip resistor_100 Kohm_± 1%_1/20 W_0201_2.0mm_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	3	0201	covered with 301-1000-00969		
301-G000-00083	Chip resistor_100 Kohm_± 5%_1/20 W_0201_2.0mm_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	15	0201	covered with 301-1000-00969		
301-G000-00085	Chip resistor_100 Kohm_± 5%_1/16 W_0402_2.0mm_N/A	Electronics, Resistor, MLCR thick film	5,97E-04	1	0402	covered with 301-1000-00402		
301-G000-00159	Chip resistor_15.0 Kohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	2	0201	covered with 301-1000-00969		
301-G000-00233	Chip resistor_2.20 Kohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	14	0201	covered with 301-1000-00969		
301-G000-00296	Chip resistor_220 Kohm_± 1%_1/16 W_0402_N/A	Electronics, Resistor, MLCR thick film	5,97E-04	1	0402	covered with 301-1000-00402		
301-G000-00380	Chip resistor_3.90 Kohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	1	0201	covered with 301-1000-00969		
301-G000-00390	Chip resistor_30.0 Kohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	1	0201	covered with 301-1000-00969		
301-G000-00400	Chip resistor_300 Kohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	1	0201	covered with 301-1000-00969		
301-G000-00532	Chip resistor_470 Kohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	1	0201	covered with 301-1000-00969		
301-G000-00554	Chip resistor_5.60 Kohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	1	0201	covered with 301-1000-00969		
301-G000-00609	Chip resistor_6.04 Kohm_± 1%_1/20 W_0201_2.0mm_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	1	0201	covered with 301-1000-00969		
301-G000-00765	Chip resistor_1.0 Mohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	3	0201	covered with 301-1000-00969		
301-G000-01047	Chip resistor_0.00 Ohm_+50 mohm_1/20 W_0201_2.0mm_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	52	0201	covered with 301-1000-00969		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
301-G000-01048	Chip resistor_0.00 Ohm_+50 mohm_1/16 W_0402_2.0mm_N/A	Electronics, Resistor, MLCR thick film	5,97E-04	2	0402	covered with 301-1000-00402		
301-G000-01136	Chip resistor_10.0 Ohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	2	0201	covered with 301-1000-00969		
301-G000-01370	Chip resistor_240 Ohm_± 1%_1/20 W_0201_2.0mm_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	3	0201	covered with 301-1000-00969		
301-G000-01382	Chip resistor_27.0 Ohm_± 5%_1/20 W_0201_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	5	0201	covered with 301-1000-00969		
301-G000-01800	Chip resistor_4.02 Kohm_± 1%_1/20 W_0201_2.0mm_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	1	0201	covered with 301-1000-00969		
302-0214-41043	Chip Capacitor_15.0 pF_± 5%_NPO (COG)_25 V_0201_0.3 mm_MURATA_GRM0335C1E150J_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	GLO: Capacitor ceramic MLCC 0201 (0.17mg) D 0.6x0.3x0.3 ts	process	294
302-0214-41051	Chip Capacitor_33.0 pF_± 5%_NPO (COG)_25 V_0201_0.3 mm_MURATA_GRM0335C1E330J_N/A	Electronics, Capacitor, MLCC	3,30E-04	26	0201	covered with 302-0214-41043		
302-0215-11006	Chip Capacitor_0.50 pF_± 0.25 pF_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1HR50C_T=0.3±0.03	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-01607	Chip Capacitor_0.8 pF_± 0.05 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_MURATA_GRM0335C1HR80W_N/A	Electronics, Capacitor, MLCC	3,30E-04	2	0201	covered with 302-0214-41043		
302-0215-11017	Chip Capacitor_1.50 pF_± 0.25 pF_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H1R5C_T=0.3±0.03	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-0215-41039	Chip Capacitor_10.0 pF_± 5%_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H100J_T=0.3±0.03	Electronics, Capacitor, MLCC	3,30E-04	2	0201	covered with 302-0214-41043		
302-1000-00317	Chip Capacitor_10.0 uF_± 20%_X5R_6.3 V_0402_N/A_MURATA_GRM155R60J106M_N/A	Electronics, Capacitor, MLCC	3,10E-03	7	0402	GLO: Capacitor ceramic MLCC 0603 (6mg) D 1.6x0.8x0.8 ts	process	55

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
302-1000-00394	Chip Capacitor_2.20 pF_± 0.25 pF_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H2R2C_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-01425	Chip Capacitor_10.0 uF_± 10%_X5R_10 V_0603_0.8 mm_MURATA_GRM188R61A106K_N/A	Electronics, Capacitor, MLCC	8,10E-03	1	0603	GLO: Capacitor ceramic MLCC 0603 (6mg) D 1.6x0.8x0.8 ts	process	42
302-1000-01454	Chip Capacitor_3.30 pF_± 0.10 pF_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H3R3B_N/A	Electronics, Capacitor, MLCC	3,30E-04	3	0201	covered with 302-0214-41043		
302-1000-01476	Chip Capacitor_2.20 uF_± 10%_X5R_10 V_0402_0.5 mm_MURATA_GRM155R61A225K_N/A	Electronics, Capacitor, MLCC	1,60E-03	6	'0402	covered with 302-1000-00317		
302-1000-01487	Chip Capacitor_22.0 uF_± 20%_X5R_10 V_0603_0.8 mm_MURATA_GRM188R61A226M_N/A	Electronics, Capacitor, MLCC	9,10E-03	3	0603	covered with 302-1000-01425		
302-1000-01533	Chip Capacitor_4.70 uF_± 20%_X5R_10 V_0402_0.5 mm_2.0mm_TAIYOYUDEN_LDK105BBJ475MVLN_N/A	Electronics, Capacitor, no datasheet found	1,42E-03	7	0402	covered with 302-1000-00317		
302-1000-01549	Chip Capacitor_56.0 pF_± 2.0%_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H560G_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-01556	Chip Capacitor_4.70 pF_± 0.10 pF_NPO (COG)_25 V_0201_0.3 mm_MURATA_GRM0335C1E4R7B_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-01603	Chip Capacitor_22.0 uF_± 20%_X5R_16 V_1206_0.85 mm_4.0mm_MURATA_GRM319R61C226M_N/A	Electronics, Capacitor, MLCC	2,40E-02	1	1206	GLO: Capacitor ceramic MLCC 1210 (50mg) D 3.2x3.2x1.6 ts	process	1
302-1000-01609	Chip Capacitor_0.50 pF_± 0.10 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_EYANG_C0201C0G0R5B500NTA_N/A	Electronics, Capacitor, MLCC	2,50E-04	1	0201	covered with 302-0214-41043		
302-1000-01617	Chip Capacitor_1.20 pF_± 0.10 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_EYANG_C0201C0G1R2B500NTA_N/A	Electronics, Capacitor, MLCC	2,50E-04	1	0201	covered with 302-0214-41043		
302-1000-01635	Chip Capacitor_3.00 pF_± 0.25 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_EYANG_C0201C0G3R0C500NTA_N/A	Electronics, Capacitor, MLCC	2,50E-04	1	0201	covered with 302-0214-41043		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
302-1000-01640	Chip Capacitor_3.90 pF_± 0.25 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_EYANG_C0201C0G3R9C500NTA_N/A	Electronics, Capacitor, MLCC	2,50E-04	1	0201	covered with 302-0214-41043		
302-1000-01564	Chip Capacitor_27.0 pF_± 2.0%_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H270G_N/A	Electronics, Capacitor, MLCC	0,00E+00	2	0201	covered with 302-0214-41043		
302-1000-02709	Chip Capacitor_18.0 pF_± 2.0%_NPO (COG)_50 V_0201_0.3 mm_2.0mm_MURATA_GRM0335C1H180GA01D_N/A	Electronics, Capacitor, MLCC	0,00E+00	2	0201	covered with 302-0214-41043		
302-0215-21036	Chip Capacitor_8.00 pF_± 0.50 pF_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H8R0D_T=0.3±0.03	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-0215-21037	Chip Capacitor_8.20 pF_± 0.50 pF_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H8R2D_T=0.3±0.03	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-0215-41041	Chip Capacitor_12.0 pF_± 5%_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H120J_T=0.3±0.03	Electronics, Capacitor, MLCC	3,30E-04	3	0201	covered with 302-0214-41043		
302-0215-21038	Chip Capacitor_9.00 pF_± 0.50 pF_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H9R0D_T=0.3±0.03	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-0215-41043	Chip Capacitor_15.0 pF_± 5%_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H150J_T=0.3±0.03	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-01692	Chip Capacitor_33.0 pF_± 5%_NPO (COG)_50 V_0201_0.3 mm_2.0mm_EYANG_C0201C0G330J500NTA_N/A	Electronics, Capacitor, MLCC	2,50E-04	2	0201	covered with 302-0214-41043		
302-1000-01604	Chip Capacitor_39.0 pF_± 2.0%_NPO (COG)_50 V_0201_0.3 mm_2.0mm_MURATA_GRM0335C1H390G_N/A	Electronics, Capacitor, MLCC	3,30E-04	3	0201	covered with 302-0214-41043		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
302-1000-01598	Chip Capacitor_100 pF_± 2.0%_NPO (COG)_50 V_0201_0.3 mm_2.0mm_MURATA_GRM0335C1H101GA01D_N/A	Electronics, Capacitor, MLCC	3,30E-04	2	0201	covered with 302-0214-41043		
302-1000-02707	Chip Capacitor_270 pF_± 10%_X7R_50 V_0201_0.3 mm_2.0mm_MURATA_GRM033R71H271KA12D_N/A	Electronics, Capacitor, MLCC	0,00E+00	2	0201	covered with 302-0214-41043		
302-1000-01553	Chip Capacitor_22.0 pF_± 2.0%_NPO (COG)_50 V_0201_0.3 mm_2.0mm_MURATA_GRM0332C1H220G_N/A	Electronics, Capacitor, MLCC	3,30E-04	2	0201	covered with 302-0214-41043		
302-0215-41063	Chip Capacitor_100 pF_± 5%_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H101J_T=0.3±0.03	Electronics, Capacitor, MLCC	3,30E-04	16	0201	covered with 302-0214-41043		
302-1000-02522	Chip Capacitor_4.70 uF_± 10%_X5R_35 V_0603_0.8 mm_4.0mm_EYANG_C0603X5R475K350NTK_N/A	Electronics, Capacitor, no datasheet found	5,60E-03	2	0603	covered with 302-1000-01425		
302-1000-01108	Chip Capacitor_470 nF_± 10%_X5R_6.3 V_0201_0.3 mm_2.0mm_MURATA_GRM033R60J474K_N/A	Electronics, Capacitor, MLCC	3,30E-04	7	0201	covered with 302-0214-41043		
302-1000-02552	Chip Capacitor_2.20 uF_± 20%_X5R_6.3 V_0201_0.3 mm_2.0mm_MURATA_GRM033R60J225ME47D_T=0.3 9 MAX	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-02527	Chip Capacitor_3.60 pF_± 0.05 pF_NPO (COG)_25 V_0201_0.3 mm_1.0mm_MURATA_GRM0335C1E3R6W_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-02597	Chip Capacitor_0.8 pF_± 0.05 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_EYANG_C0201C0G0R8A500NTA_N/A	Electronics, Capacitor, MLCC	2,50E-04	1	'0201	covered with 302-0214-41043		
302-1000-02708	Chip Capacitor_560 pF_± 10%_X7R_50 V_0201_0.3 mm_2.0mm_MURATA_GRM033R71H561KA12D_N/A	Electronics, Capacitor, MLCC	0,00E+00	2	0201	covered with 302-0214-41043		
302-1000-02530	Chip Capacitor_0.50 pF_± 0.05 pF_NPO (COG)_25 V_0201_0.3 mm_1.0mm_MURATA_GRM0335C1ER50W_N/A	Electronics, Capacitor, MLCC	3,30E-04	3	0201	covered with 302-0214-41043		
302-1000-02617	Chip Capacitor_22.0 nF_± 20%_X5R_16 V_0201_0.3 mm_2.0mm_EYANG_C0201X5R223M160NTA_N/A	Electronics, Capacitor, MLCC	2,50E-04	1	0201	covered with 302-0214-41043		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
302-1000-01453	Chip Capacitor_3.90 pF_± 0.10 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_MURATA_GRM0335C1H3R9B_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-02640	Chip Capacitor_1.00 pF_± 0.10 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_EYANG_C0201C0G1R0B500NTA_N/A	Electronics, Capacitor, MLCC	2,50E-04	1	0201	covered with 302-0214-41043		
302-1000-02645	Chip Capacitor_4.30 pF_± 0.10 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_EYANG_C0201C0G4R3B500NTA_N/A	Electronics, Capacitor, MLCC	2,50E-04	2	0201	covered with 302-0214-41043		
302-1000-02667	Chip Capacitor_3.00 pF_± 0.25 pF_NPO (COG)_25 V_0201_0.3 mm_2.0mm_MURATA_GJM0335C1E3R0CB01D_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-G000-00023	Chip Capacitor_1.00 nF_± 10%_X7R_25 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	6	0201	covered with 302-0214-41043		
302-G000-00143	Chip Capacitor_10.0 nF_± 10%_X5R_16 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,20E-04	11	0201	covered with 302-0214-41043		
302-G000-00182	Chip Capacitor_100 nF_± 10%_X5R_10 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	100	0201	covered with 302-0214-41043		
302-G000-00191	Chip Capacitor_100 nF_± 10%_X5R_6.3 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	3	'0201	covered with 302-0214-41043		
302-G000-00196	Chip Capacitor_100 nF_± 10%_X7R_16 V_0402_N/A_N/A_N/A	Electronics, Capacitor, MLCC	1,60E-03	8	0402	covered with 302-1000-00317		
302-G000-00488	Chip Capacitor_220 nF_± 20%_X5R_6.3 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-G000-00516	Chip Capacitor_27.0 nF_± 10%_X7R_16 V_0402_0.5 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	1,60E-03	1	0402	covered with 302-1000-00317		
302-G000-00807	Chip Capacitor_470 nF_± 10%_X5R_10 V_0402_N/A_N/A_N/A	Electronics, Capacitor, MLCC	1,60E-03	2	0402	covered with 302-1000-00317		
302-G000-00826	Chip Capacitor_470 nF_± 20%_X5R_6.3 V_0402_N/A_N/A_N/A	Electronics, Capacitor, MLCC	1,60E-03	3	0402	covered with 302-1000-00317		



Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
302-G000-01475	Chip Capacitor_220 pF_± 10%_X7R_25 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	2	0201	covered with 302-0214-41043		
302-G000-01629	Chip Capacitor_330 pF_± 10%_X7R_50 V_0201_0.3 mm_N/A_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-G000-02041	Chip Capacitor_1.00 uF_± 10%_X5R_35 V_0603_0.8 mm_4.0mm_N/A	Electronics, Capacitor, MLCC	6,30E-03	4	0603	covered with 302-1000-01425		
302-G000-02058	Chip Capacitor_1.00 uF_± 20%_X5R_10 V_0402_N/A_N/A_N/A	Electronics, Capacitor, MLCC	1,60E-03	8	0402	covered with 302-1000-00317		
302-G000-02068	Chip Capacitor_1.00 uF_± 20%_X5R_6.3 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	67	0201	covered with 302-0214-41043		
302-G000-02113	Chip Capacitor_10.0 uF_± 20%_X5R_10 V_0603_N/A_N/A_N/A	Electronics, Capacitor, MLCC	5,12E-03	5	0603	covered with 302-1000-01425		
302-G000-02163	Chip Capacitor_2.20 uF_± 20%_X5R_6.3 V_0402_0.5 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	1,60E-03	8	0402	covered with 302-1000-00317		
302-G000-02197	Chip Capacitor_22.0 uF_± 20%_X5R_6.3 V_0603_0.8 mm_4.0mm_N/A	Electronics, Capacitor, MLCC	9,10E-03	24	0603	covered with 302-1000-01425		
302-G000-02232	Chip Capacitor_4.70 uF_± 10%_X5R_10 V_0603_N/A_N/A_N/A	Electronics, Capacitor, MLCC	6,30E-03	2	0603	covered with 302-1000-01425		
302-G000-02234	Chip Capacitor_4.70 uF_± 10%_X5R_16 V_0603_0.8 mm_4.0mm_N/A	Electronics, Capacitor, MLCC	8,10E-03	1	0603	covered with 302-1000-01425		
302-G000-02258	Chip Capacitor_4.70 uF_± 20%_X5R_6.3 V_0402_0.5 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	2,50E-03	13	0402	covered with 302-1000-00317		
302-1000-02666	Chip Capacitor_1.10 pF_± 0.25 pF_NPO (COG)_25 V_0201_0.3 mm_2.0mm_MURATA_GJM0335C1E1R1CB01D_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	'0201	covered with 302-0214-41043		
303-1000-01295	Chip Inductor_7.50 nH_± 3%_0201_500 Mhz_0.4 mm_2.0mm_MURATA_LQP03HQ7N5H02D_N/A	Electronics, Inductor, Ceramic Chip Inductor Film Type (High Q Type)	2,20E-04	1	0201	GLO: inductor production, low value multilayer chip ecoinvent 3.5	process	1.05e-1 g
303-1000-00040	Chip Ferrite bead_120 ohm_± 25%_0603_100 Mhz_MURATA_BLM18PG121SN1D_DCR=0.05 Ohm	Electronics, Inductor, Ferrite Bead	4,63E-03	2	0603	covered with 303-1000-01295		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
303-1000-00819	Chip Inductor_1.60 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_MURATA_LQP03TG1N6B02D_DCR<0.15,Idc:0.6A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		
302-1000-01494	Chip Capacitor_1.50 pF_± 0.10 pF_NPO (COG)_25 V_0201_0.3 mm_MURATA_GRM0335C1E1R5B_N/A	Electronics, Inductor, ??? GRM is used for Capacitors at Murata's (see Datasheet). This is probably a Ceramic Chip Inductor.	3,30E-04	1	0201	GLO: electronic component production, passive, unspecified ecoinvent 3.5	process	2.05e-1g
303-1000-00830	Chip Inductor_5.60 nH_± 3%_0201_500 Mhz_0.3 mm_MURATA_LQP03TG5N6H02D_DCR<0.88,Idc:0.25 A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	3	0201	covered with 303-1000-01295		
303-1000-00445	Chip Ferrite bead_1000 ohm_± 25%_0402_100 Mhz_MURATA_BLM15HD102SN1D_N/A	Electronics, Inductor, Ferrite Bead	1,21E-03	6	0402	covered with 302-1000-01494		
303-1000-00825	Chip Inductor_3.00 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TG3N0B02D_DCR<0.25,Idc:0.45A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		
303-1000-00709	Chip Inductor_3.30 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TN3N3B02D_DCR<0.25,Idc:450mA	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		
303-1000-00798	Chip Ferrite bead_240 ohm_± 25%_0201_100 Mhz_0.3 mm_MURATA_BLM03AX241SN1D_DCR<0.38,Idc=350 mA	Electronics, Inductor, Ferrite Bead	3,00E-04	1	0201	covered with 302-1000-01494		
303-1000-00800	Chip Ferrite bead_1000 ohm_± 25%_0603_100 Mhz_0.8 mm_TDK_MPZ1608S102A_DCR<0.3 OHM,Idc<0.8A	Electronics, Inductor, Ferrite Bead		3	0603	covered with 302-1000-01494		
303-1000-00881	Chip Inductor_1.00 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TG1N0B02D_DCR<0.15,Idc:600mA	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	2	0201	covered with 303-1000-01295		
303-1000-00818	Chip Inductor_1.50 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TG1N5B02D_DCR<0.15,Idc:0.6A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
303-1000-00821	Chip Inductor_2.00 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TG2N0B02D_DCR<0.25,ldc:0.45A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	2	0201	covered with 303-1000-01295		
303-1000-00931	Chip Inductor_7.50 nH_± 3%_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TG7N5H02D_DCR<1.22,ldc:200mA	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		
303-1000-00980	Chip Inductor_0.7 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_MURATA_LQP03TG0N7B02D_DCR<0.1Ohm,ldc:750mA	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		
303-1000-00999	Chip Inductor_15.0 nH_± 3%_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TG15NH02D_DCR<1.90,ldc:0.17A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		
303-1000-01002	Chip Wire Wound Inductor_0.47 uH_± 20%_0806_1.0 Mhz_1.0 mm_4.0mm_INPAQ_WIP201610P-R47ML_Rdc<0.04ohm,Irms<3.3A	Electronics, Inductor, Metal Molding Power Induction (Material Code: Iron Powder)	1,79E-02	2		covered with 302-1000-01494		
303-1000-01044	Chip Ferrite bead_120 ohm_± 25%_0402_100 Mhz_0.5 mm_2.0mm_TDK_MMZ1005Y121CT_DCR<0.2.1 OHM,<400mA	Electronics, Inductor, Ferrite Bead		2	0402	covered with 302-1000-01494		
303-1000-01297	Chip Inductor_6.80 nH_± 3%_0201_500 Mhz_0.4 mm_2.0mm_MURATA_LQP03HQ6N8H02D_N/A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	2,20E-04	1	0201	covered with 303-1000-01295		
303-1000-01066	Chip Inductor power_1.00 uH_± 20%_1008_1.0 Mhz_0.9 mm_4.0mm_MODAL-INOCHIPS_MP252010S1R0MFR_DCR:40mohm IDC:4.2A	Electronics, Inductor, no datasheet found	2,48E-02	1		covered with 302-1000-01494		
303-1000-01070	Chip Ferrite bead_50 ohm_± 25%_0201_100 Mhz_0.3 mm_2.0mm_MURATA_BLM03EB500SN1D_DCR<0.58ohm,ldc=0.4A	Electronics, Inductor, Ferrite Bead	3,00E-04	2	0201	covered with 302-1000-01494		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
303-1000-01100	Chip Inductor power_1.00 uH_± 20%_0603_1.0 Mhz_0.8 mm_4.0mm_SHENZHEN SUNLORD_MPH160809S1R0MT_DCR<0.25Ohm,Idc:0.8 A	Electronics, Inductor, no data sheet found	6,40E-03	1	0603	covered with 302-1000-01494		
303-1000-01136	Chip Inductor power_10.0 uH_± 20%_2520_1.0 Mhz_0.9 mm_4.0mm_TDK_VLS252010HBU-100M_RDC<0.696ohm,Idc=1.3A	Electronics, Inductor, Typ: Wound Metal (?)	2,60E-02	1		covered with 302-1000-01494		
303-1000-01145	Chip Inductor_1.00 uH_± 20%_0603_2.0 Mhz_0.75 mm_4.0mm_CHILISIN_HEI160808B-1R0M-Q8DG_RDC<0.115ohm,Idc<1.7A	Electronics, Inductor, Ferrite (Molding Power Inductor)	6,90E-03	1	0603	covered with 302-1000-01494		
303-1000-01152	Chip Inductor_160 nH_± 5%_0603_25 Mhz_0.8 mm_4.0mm_TDK_MLJ1608WR16JT_DCR<0.16 Ohm,Idc:600mA	Electronics, Inductor, Inductor Power Shielded Multi-Layer, 15Q-Factor Ferrite		2	0603	covered with 302-1000-01494		
303-1000-01158	Chip Inductor power_4.70 uH_± 20%_1008_1.0 Mhz_0.9 mm_4.0mm_MURATA_DFE2520MFT-4R7M=P2_DCR<0.024 Ohm, Idc: 1.9A	Electronics, Inductor, Wound Metal Alloy (further specification not possible from Datasheet (Murata Product Line Up))	2,82E-02	1	1008	covered with 302-1000-01494		
303-1000-01162	Chip Inductor power_1.00 uH_± 20%_1008_1.0 Mhz_0.95 mm_4.0mm_MODA-INNOCHIPS_MP252010H1R0MFR_N/A	Electronics, Inductor, no datasheet found	2,48E-02	1	1008	covered with 302-1000-01494		
303-1000-01167	Chip Inductor_1.50 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q1N5BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	4	0201	covered with 303-1000-01295		
303-1000-01168	Chip Inductor_1.80 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q1N8BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	2	0201	covered with 303-1000-01295		
303-1000-01169	Chip Inductor_2.00 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q2N0BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	2	0201	covered with 303-1000-01295		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
303-1000-00823	Chip Inductor_2.40 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TG2N4B02D_DCR<0.25,Idc:0.45A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		
303-1000-01170	Chip Inductor_2.70 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q2N7BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	1	0201	covered with 303-1000-01295		
303-1000-01171	Chip Inductor_5.60 nH_± 0.2 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q5N6CT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	2	0201	covered with 303-1000-01295		
303-1000-01172	Chip Inductor_6.80 nH_± 3%_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q6N8HT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	1	0201	covered with 303-1000-01295		
303-1000-01173	Chip Inductor_2.20 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q2N2BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	1	0201	covered with 303-1000-01295		
303-1000-01174	Chip Inductor_1.00 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q1N0BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	3	0201	covered with 303-1000-01295		
303-1000-01175	Chip Inductor_10.0 nH_± 3%_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q10NHT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	1	0201	covered with 303-1000-01295		
303-1000-01176	Chip Inductor_6.20 nH_± 0.2 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q6N2CT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	3	0201	covered with 303-1000-01295		
303-1000-00982	Chip Inductor_9.10 nH_± 3%_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TG9N1H02D_DCR<1.4,Idc:0.2A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		
303-1000-01179	Chip Inductor_3.30 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q3N3BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	1	0201	covered with 303-1000-01295		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
303-1000-01180	Chip Inductor_4.30 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q4N3BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	1	0201	covered with 303-1000-01295		
303-1000-01181	Chip Inductor_5.10 nH_± 0.2 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q5N1CT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	1	0201	covered with 303-1000-01295		
303-1000-01182	Chip Inductor_2.40 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q2N4BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	4	0201	covered with 303-1000-01295		
303-1000-00828	Chip Inductor_4.70 nH_± 3%_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TG4N7H02D_DCR<0.72, I dc:0.25A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		
303-1000-01184	Chip Inductor_8.20 nH_± 3%_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q8N2HT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	1	0201	covered with 303-1000-01295		
303-1000-01204	Chip Inductor power_2.20 uH_± 20%_0806_1.0 Mhz_0.9 mm_4.0mm_MODA-INNOCHIPS_MP201610H2R2MFR_N/A	Electronics, Inductor, no datasheet found	1,79E-02	3	0806	covered with 303-1000-01295		
303-1000-01212	Chip Inductor power_1.00 uH_± 20%_0806_1.0 Mhz_0.9 mm_4.0mm_MODA-INNOCHIPS_MP201610H1R0MFR_N/A	Electronics, Inductor, no datasheet found	1,79E-02	2	0806	covered with 303-1000-01295		
303-1000-01218	Chip Inductor_12.0 nH_± 5%_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q12NJT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	2	0201	covered with 303-1000-01295		
303-1000-01220	Chip Inductor_27.0 nH_± 5%_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q27NJT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	2	0201	covered with 303-1000-01295		
303-1000-01224	Chip Inductor_9.10 nH_± 3%_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q9N1HT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	2	0201	covered with 303-1000-01295		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
303-1000-01241	Chip Inductor_1.60 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q1N6BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	2	0201	covered with 303-1000-01295		
303-1000-01243	Chip Inductor_0.80 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_SHENZHEN SUNLORD_SDCL0603Q0N8BT02B02_N/A	Electronics, Inductor, Multilayer Chip Ceramic Conductor	3,00E-04	1	0201	covered with 303-1000-01295		
303-1000-01285	Chip Inductor_1.7 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_2.0mm_MURATA_LQP03TG1N7B02D_N/A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	1,75E-04	1	0201	covered with 303-1000-01295		
303-1000-01299	Chip Inductor_20.0 nH_± 3%_0201_500 Mhz_0.4 mm_2.0mm_MURATA_LQP03HQ20NH02D_N/A	Electronics, Inductor, Ceramic Chip Inductor Film Type (High Q Type)	2,20E-04	1	0201	covered with 303-1000-01295		
303-1000-01298	Chip Inductor_0.80 nH_± 0.1 nH_0201_500 Mhz_0.4 mm_2.0mm_MURATA_LQP03HQ0N8B02D_N/A	Electronics, Inductor, Ceramic Chip Inductor Film Type (High Q Type)	2,20E-04	1	0201	covered with 303-1000-01295		
303-1000-01296	Chip Inductor_3.40 nH_± 0.1 nH_0201_500 Mhz_0.4 mm_2.0mm_MURATA_LQP03HQ3N4B02D_N/A	Electronics, Inductor, Ceramic Chip Inductor Film Type (High Q Type)	2,20E-04	1	0201	covered with 303-1000-01295		
305-0000-00176	Crystal Resonator_X2R019200BZ1H-CHZ_19.2 MHZ_±10.0ppm_SMD-2.5*2mm-4Pin_4.0mm_HARMONY.ELE_Built-In Thermistor	Electronics, Oscillator, Quartz Crystal	1,58E-02	1		GLO: Oscillator crystal (500mg) 11.05x4.65x2.5 ts	1	process
305-0000-00241	Crystal Resonator_1ZZHAE48000ZZ0A_48.0 MHZ_±20ppm_SMD-2.05*1.65mm-4Pin_4.0mm_KDS_N/A	Electronics, Oscillator, no datasheet found	5,81E-03	1		covered with 302-1000-01494		
308-0000-00281	ESD protection_5.0V_IMG0505350FR_0402_2.0mm_MODAL-INOCHIPS_Cp=35 pF	Electronics, no datasheet found	1,40E-03	12	0402	covered with 302-1000-01494		
308-0000-00321	CHIP BIPOLARTVS_5.0V_ESD5311N-2/TR_DFN_2.0mm_WILLSEMI_Cj<0.4pF	Electronics, 1-Line, Bi-directional, Ultra-low Capacitance, transient voltage surpressor diode	1,49E-03	7	DFN1006-2L	GLO: Diode signal SOD123/323/523 (1.59mg) 0.8x0.75x1.6 with Au-Bondwire ts	process	36
308-0000-00325	CHIP BIPOLARTVS_5.0V_ESD73031N-2/TR_DFN_2.0mm_WILLSEMI_N/A	Electronics, 1-Line, Bi-directional, Ultra-low Capacitance, Transient Voltage Suppressors, transient voltage surpressor diode	1,73E-03	23	DFN1006-2L	covered with 308-0000-00321		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
308-0000-00328	CHIP BIPOLARTVS_5.0V_ESD5451R-2/TR_0402_2.0mm_WILLSEMI_Packing:DFP1006-2L	Electronics, 1-Line, Bi-directional, Transient Voltage Suppressors, transient voltage surpressor diode	0,00E+00	5	DFP1006-2L	covered with 308-0000-00321		
309-0000-00274	Diode Schottky_RB520S-30G_N/A_2pin_SOD-523_200mA/0.6V_LISION_1.7*0.7*0.77mm	Electronics, Diode, Schottky barrier diode, Construction: Silicon epitaxial planar	0,00E+00	2	SOD-523	GLO: Diode signal SOD123/323/523 (9.26mg) 2.4x1.6x1 with Au-Bondwires	process	4
309-0000-00309	Diode Schottky_WSB5503W-2/TR_N/A_2pin_SOD-323_1A/<0.57V_4.0mm_WILLSEMI_N/A	Electronics, Diode, Middle Power Schottky Barrier Diode	4,60E-03	1	SOD-323	covered with 309-0000-00274		
311-0000-01713	I.C POWER AMP MODULE(RF)_BGA824N6E6327_TSLP-6-2_6 PINS_NoMemory_INFINEON_GNSS LNA	Electronics, IC,	9,16E-04	1		IC modelling explained in section 3.1.9.3		
311-0000-01957	I.C WLAN MODULE_WCN-3680B-0-79BWLNSP-TR-05-1_WLNSP_79 Balls_NoMemory_8.0mm_QUALCOMM_3.805x3.82x0.36mm	Electronics, IC,	1,90E-02	1		IC modelling explained in section 3.1.9.3		
311-0000-02100	I.C LDO_AP7341D-12FS4-7_DFN_4 PINS_NoMemory_4.0mm_DIODES_1.2V	Electronics, IC,	1,33E-03	1		IC modelling explained in section 3.1.9.3		
311-0000-02104	I.C AUDIO POWER AMPLIFIER_WCD-9326-0-113FOWPSP-TR-03-0_FOWPSP_113 Balls_NoMemory_8.0mm_QUALCOMM_N/A	Electronics, IC,	2,44E-02	1		IC modelling explained in section 3.1.9.3		
311-0000-02114	I.C ANALOG SWITCH_RF1683TR13-5K_MODULE_22BALLS_NoMemory_4.0mm_QORVO_N/A	Electronics, IC,		1		IC modelling explained in section 3.1.9.3		
311-0000-02380	I.C POWER AMP MODULE(RF)_QM56022TR13-5K_SMT_42 balls_NoMemory_8.0mm_QORVO_N/A	Electronics, IC,		1		IC modelling explained in section 3.1.9.3		
311-0000-02136	I.C WLAN MODULE_RFFM8516TR7-5K_QFN_16BALLS_NoMemory_4.0mm_QORVO_N/A	Electronics, IC,		1		IC modelling explained in section 3.1.9.3		
311-0000-02250	I.C POWER MANAGEMENT UNIT(PMU)_PM-8953-0-187FOWNSP-TR-01-0-VV_FOWNSP_187BALLS_NoMemory_8.0mm_QUALCOMM_N/A	Electronics, IC,	4,46E-02	1		IC modelling explained in section 3.1.9.3		



Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
311-0000-02263	I.C DC-DC CONVERT_QET4101-0-12-WLNSP-TR-00-0-VV_WLNSP_12 Balls_NoMemory_4.0mm_QUALCOMM_N/A	Electronics, IC,	2,26E-02	1		IC modelling explained in section 3.1.9.3		
311-0000-02298	I.C Front End Module_QM57508TR13-5K_SMT_44 BALLS_NoMemory_8.0mm_QORVO_N/A	Electronics, IC,		1		IC modelling explained in section 3.1.9.3		
311-0000-02689	I.C STACKED MEMORY_KMRH60014A-B614_FBGA_221 balls_64G+4G_16.0mm_SAMSUNG_N/A	Electronics, IC,	3,01E-01	1		Memory (311-0000-02689) - FP3 <LZ> (IC modelling explained in section 3.1.9.3)	plan	
311-0000-02383	I.C DC-DC CONVERT_KTD3111EAA-20-1-TR_WLCSP_9 Balls_NoMemory_4.0mm_KINETIC_2P8S LED Driver	Electronics, IC,	2,03E-03	1		IC modelling explained in section 3.1.9.3		
311-0000-02411	I.C DC-DC CONVERT_TPS612564CYFFR_DSBGA_9 BALLS_NoMemory_2.0mm_TI_NFC	Electronics, IC,	1,90E-03	1		IC modelling explained in section 3.1.9.3		
311-0000-02413	I.C ANALOG SWITCH_BGSA14RN10_TSNP_10 Pins_NoMemory_4.0mm_INFINEON_N/A	Electronics, IC,	1,89E-03	1		IC modelling explained in section 3.1.9.3		
311-0000-02600	I.C SENSOR_ICM-20602-Z_LGA_16Pins_NoMemory_8.0mm_INVENSENSE_3x3x0.75mm	Electronics, IC,		1		IC modelling explained in section 3.1.9.3		
311-0000-02447	I.C LDO_ET51518YB_DFN_4Pins_NoMemory_2.0mm_ETERK_N/A	Electronics, IC,	2,24E-03	1		IC modelling explained in section 3.1.9.3		
311-0000-02460	NFC Microcontroller_NQ310A1EV/C101_VFBGA_64 BALLS_NoMemory_8.0mm_NXP_NFC controller designed for Qualcomm	Electronics, IC,	2,68E-02	1		IC modelling explained in section 3.1.9.3		
311-0000-02494	I.C LDO_RP114K331D-TRB_DFN_4 PIN_NoMemory_2.0mm_RICOH_N/A	Electronics, IC,	1,35E-03	1		IC modelling explained in section 3.1.9.3		
311-0000-02495	I.C CHARGE_KTS1680AEUZ-TR_WLCSP_12 Balls_NoMemory_4.0mm_KINETIC_N/A	Electronics, IC,	2,85E-03	1		IC modelling explained in section 3.1.9.3		
311-0000-02513	I.C LDO_RP115L181D-E2_DFN_8Pins_NoMemory_4.0mm_RICOH_N/A	Electronics, IC,	2,35E-03	1		IC modelling explained in section 3.1.9.3		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
311-0000-02574	I.C TRANSCEIVER_WTR-3925-2-106BWLSP-TR-03-0-VV_WLPSP_106BALLS_NoMemory_8.0mm_QUALCOM M_N/A	Electronics, IC,	2,04E-02	1		IC modelling explained in section 3.1.9.3		
311-0000-02599	I.C AUDIO POWER AMPLIFIER_AW8898QNR_QFN_24 Pins_NoMemory_8.0mm_AWINIC_N/A	Electronics, IC,	3,35E-02	1		IC modelling explained in section 3.1.9.3		
311-0000-02690	I.C BASEBAND PROCESSOR_SDM-632-0-792NSP-TR-00-0-AA_NSP_792Balls_NoMemory_16.0mm_QUALCOMM_N/A	Electronics, IC,	2,30E-01	1		CPU (311-0000-02690) - FP3 <LZ> IC modelling explained in section 3.1.9.3	plan	
311-0000-02617	I.C SENSOR_AK09918C_WLCSP_4 balls_NoMemory_2.0mm_ASAHI KASEI_N/A	Electronics, IC,	8,04E-04	1		IC modelling explained in section 3.1.9.3		
311-0000-02618	I.C POWER MANAGEMENT UNIT(PMU)_PMI-632-9-WLNSP81B-TR-02_WLNSP_81Balls_NoMemory_8.0mm_QUALCOMM_N/A	Electronics, IC,	1,53E-02	1		IC modelling explained in section 3.1.9.3		
311-0000-02629	I.C LDO_RP114K281D-TRB_DFN_4 balls_NoMemory_2.0mm_RICOH_2.8V,300mA	Electronics, IC,	1,35E-03	1		IC modelling explained in section 3.1.9.3		
314-0000-00808	CON. RF CONNECTOR WITH SWITCH_C90P106-00004-H_0.500 mm_4 pin_4.0mm_SPEED_AC250V/50 Ohm,12GHz,2x2x0.9 mm	Electronics, Connector,	2,55E-02	3		Connector RF switch (314-0000-00808) - Core Module FP3	plan	
314-0000-01119	CON. SPRING CONNECTOR_J9Y802K02308_NA_1 pin_4.0mm_KUNZHON_H=2.0mm	Electronics, Connector,	4,00E-03	13		Spring connectors FP3 (314-0000-01119)	plan	
314-0000-00982	CON. SPRING CONNECTOR_J9Y802K00001_1.500 mm_1 pin_4.0mm_KUNZHON_H=1.1mm	Electronics, Connector,	3,50E-03	3		Spring connector small FP3 (314-0000-00982)	plan	3,5e-3 g
		Nickel compounds	8,00E-05			GLO: Nickel mix ts	process	8e-5 g
		Gold	2,00E-05			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	2e-5 g
		Tin	1,80E-04			GLO: Copper mix (99,999% from electrolysis) ts	process	1,8e-4 g

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
		Copper	3,20E-03			GLO: Tin ts	process	3,2e-3 g
314-0000-00947	CON. PCB FEMALE CONNECTOR_BM20B(0.8)-50DS-0.4V(51)_0.400 mm_50 pin_4.0mm_HIROSE_H=0.8mm	Electronics, Connector,	3,36E-02	3		Connector 50 pin (314-0000-00947) - Core Module FP3	plan	3*3.36e-2 g
		SV CONTACT(2), Copper	1,16E-02			GLO: Copper mix (99,999% from electrolysis) ts	process	1.2e-2 g
		SV CONTACT(2), Nickel (metallic)	1,25E-03			GLO: Nickel mix ts	process	1.28e-3 g
		SV CONTACT(2), Red phosphorous	2,41E-05			neglected		
		SV CONTACT(2), Lead	2,54E-06			EU-28: Lead primary and secondary mix ILA <t-agg>	process	2.8e-6 g
		SV CONTACT(2), Cadmium	1,27E-07			GLO: Cadmium ts	process	3.92e-5g
		SV CONTACT(2), Cobalt metal powder	2,50E-07			GLO: Cobalt, refined (metal) CDI	process	2.03e-5 g
		SV CONTACT(2), Tin	1,02E-03			GLO: Tin ts	process	1.02e-3 g
		SV CONTACT(2), Gold	4,98E-05			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	5.37e-5 g
		SV CONTACT(2), Iron	1,27E-05			DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	1.3e-5 g
		SV CONTACT(2), Zinc	2,54E-05			GLO: Special high grade zinc ELCD/IZA	process	2.04e-4 g
		SV REINFORCED METAL FITTINGS, Cobalt metal powder	2,00E-05			covered with cobalt above		
		SV REINFORCED METAL FITTINGS, Iron	2,64E-07			covered with iron above		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
		SV REINFORCED METAL FITTINGS, Copper	3,48E-04			covered with copper above		
		SV REINFORCED METAL FITTINGS, Nickel (metallic)	2,80E-05			covered with nickel above		
		SV REINFORCED METAL FITTINGS, Zinc	1,79E-04			covered with zinc above		
		SV REINFORCED METAL FITTINGS, Gold	3,98E-06			covered with gold above		
		SV REINFORCED METAL FITTINGS, Cadmium	3,91E-05			covered with cadmium above		
		SV REINFORCED METAL FITTINGS, Lead	2,63E-07			covered with lead above		
		HOUSING, Talc containing asbestiform fibers	5,70E-03			EU-28: Talcum powder (filler) ts	process	5.7e-3 g
		HOUSING, Wholly aromatic liquid crystal polyester(LCP)	1,11E-02			DE: Polyester Resin unsaturated (UP) ts	process	1.11e-2 g
		HOUSING, Carbon black (airborne, unbound particles of respirable size)	2,85E-04			DE: Carbon black (furnace black; general purpose) ts	process	2.85e-4 g
		HOUSING, Fatty acids, montan-wax, ethylene esters	9,50E-06			neglected		
		HOUSING, Calcium Stearate	1,90E-05			neglected		
		HOUSING, Misc., not to declare	9,48E-06			neglected		
		HOUSING, Glass wool fibers (inhalable and biopersistent)	1,90E-03			EU-28: Glass wool ts	process	1.9e-3 g
314-0000-01120	CON. RF CONNECTOR WITH SWITCH_C87P101-N0003-H_NA_4 pin_4.0mm_SPEED TECH CORP(BEIJING)_H=0.6mm	Electronics, Connector,	5,20E-03	2		Connector RF switch (314-0000-01120) - Core Module FP3	plan	2*5.2e-3 g
		Au plating, Aurate(1-), bis(cyano-kappa.C)-, potassium (1:1)	9,90E-05			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	1e-4 g

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
		C2680, Lead	8,00E-07			EU-28: Red brass ts <t-agg>	process	1,60E-03
		C2680, Copper	1,09E-03			covered with brass above		
		C2680, Zinc	5,10E-04			covered with brass above		
		C2680, Iron	8,00E-07			covered with brass above		
		Ni plating, nickel bis(sulfamidate); nickel sulfamate	7,00E-05			GLO: Nickel mix ts	process	1e-4 g
		Ni plating, Water	3,00E-05			covered above		
		C5191, Copper	1,85E-03			RoW: bronze production ecoinvent 3.5	process	2e-3 g
		C5191, Red phosphorous	7,00E-06			covered with bronze above		
		C5191, Tin	1,40E-04			covered with bronze above		
		MG-350 BPRL, Talc containing asbestiform fibers	4,06E-04			EU-28: Talcum powder (filler) ts	process	4.06e-4 g
		MG-350 BPRL, Glass wool fibers (inhalable and biopersistent)	3,50E-04			EU-28: Glass wool ts	process	3.5e-4 g
		MG-350 BPRL, Carbon black (airborne, unbound particles of respirable size)	1,40E-05			DE: Carbon black (furnace black; general purpose) ts	process	1.4e-5 g
		MG-350 BPRL, 1,3-Benzenedicarboxylic acid, polymer with 1,4-benzenedicarboxylic acid, [1,1'-biphenyl]-4,4'-diol and 4-hydroxybenzoic acid	6,30E-04			neglected		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
314-0000-01138	CON. SPRING CONNECTOR_818010053_NA_1 pin_4.0mm_ECT_H=1.75mm	Electronics, Connector,	4,55E-03	4		Spring connector 4mm (314-0000-01138) - Core Module FP3	plan	4*4.55 e-3 g
		SUS 301, Iron	3,38E-03			DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	4.53e-3 g
		SUS 301, Red phosphorous	1,81E-06			covered with stainless steel above		
		SUS 301, Nickel (metallic)	3,08E-04			covered with stainless steel above		
		SUS 301, Silicon	1,36E-05			covered with stainless steel above		
		SUS 301, Carbon	2,27E-06			covered with stainless steel above		
		SUS 301, manganese	5,44E-05			covered with stainless steel above		
		SUS 301, chromium	7,70E-04			covered with stainless steel above		
		SUS 301, Sulfur	1,36E-06			covered with stainless steel above		
		Plate with nickel, Nickel (metallic)	1,00E-05			GLO: Nickel mix ts	process	1e-5 g
		Gold-plated, Gold	1,00E-05			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	1e-5 g
314-0000-01198	CON. PIN STICK (POGO) CONTACT_LHHPG006-CS-R_2.000 mm_32 pin_16.0mm_SPEED TECH CORP_N/A	Electronics, Connector,	1,18E+00	1		Connector 32 pin (314-0000-01198) - Core module FP3	plan	1.18 g
		Plating Au, Gold	1,00E-03			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	1e-3 g
		Housing LCP E130i BK210P, LCP	2,80E-01			DE: Polyester Resin unsaturated (UP) ts	process	5.39e-1 g

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
		Housing LCP E130i BK210P, Glass wool fibers (inhalable and biopersistent)	1,20E-01			EU-28: Glass wool ts	process	2.31e-1 g
		Spring SUS304, Nickel (metallic)	1,05E-03			EU-28: Stainless steel cold rolled coil (304) Eurofer <t-agg>	process	1e-2 g
		Spring SUS304, Disodium tetraborate, anhydrous	2,50E-06			covered with stainless steel above		
		Spring SUS304, Antimony oxide (Antimony trioxide)	2,50E-06			covered with stainless steel above		
		Spring SUS304, Boric acid	2,50E-06			covered with stainless steel above		
		Spring SUS304, Alkanes, chloro	1,00E-06			covered with stainless steel above		
		Spring SUS304, Cobalt metal powder	1,00E-04			covered with stainless steel above		
		Spring SUS304, Copper	1,00E-04			covered with stainless steel above		
		Spring SUS304, Iron	8,74E-03			covered with stainless steel above		
		CAP LCP E130i BK211P, LCP	2,59E-01			covered with polyester resin above		
		CAP LCP E130i BK211P, Glass wool fibers (inhalable and biopersistent)	1,11E-01			covered with glass wool above		
		Plunger/Borrel C6801, Zinc	9,99E-02			GLO: Special high grade zinc ELCD/IZA	process	9.99e-2 g
		Plunger/Borrel C6801, Copper	1,70E-01			GLO: Copper mix (99,999% from electrolysis) ts	process	1.7e-1 g

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
		Shell 锌锡镍合金, Carbon	1,63E-02			DE: Carbon black (furnace black; general purpose) ts	process	1.63e-2 g
		Shell 锌锡镍合金, manganese	8,45E-02			ZA: Manganese ts	process	8.45e-2 g
		Shell 锌锡镍合金, Sulfur	6,50E-03			neglected		
		Shell 锌锡镍合金, Silicon	5,07E-03			DE: Silicone rubber (RTV-2, condensation) ts	process	5.07e-3 g
		Shell 锌锡镍合金, Nickel (metallic)	1,44E-02			GLO: Nickel mix ts	process	1.64e-2 g
		Shell 锌锡镍合金, Red phosphorous	3,25E-03			neglected		
		Plating Ni , Nickel (metallic)	2,00E-03			covered with nickel above		
314-0000-01201	CON. SPRING CONNECTOR_788640001_1.6 mm_4 pin_8.0mm_MOLEX_N/A	Electronics, Connector,	2,56E-02	3		Spring Connector 8mm (314-0000-01201) - Core Module FP3	plan	3*2.56e-2 g
		Nickel Plating, Nickel (metallic)	4,39E-04			GLO: Nickel mix ts	process	4.39e-4 g
		Tin Plating, Tin	1,20E-05			GLO: Tin ts	process	1.2e-5 g
		Gold Plating, Gold	5,00E-06			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	5e-6 g
		High Performance Copper Alloy Unplated, Copper	1,12E-02			GLO: Copper mix (99,999% from electrolysis) ts	process	1.12e-2 g
		High Performance Copper Alloy Unplated, Titanium	3,65E-04			GLO: Titanium ts	process	3.65e-4 g



Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
		High Performance Copper Alloy Unplated, Iron	2,30E-05			DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	2.3e-5 g
		LCP GF BLACK, LCP	9,18E-03			DE: Polyester Resin unsaturated (UP) ts	process	9.18e-3 g
		LCP GF BLACK, Carbon black (airborne, unbound particles of respirable size)	6,80E-05			DE: Carbon black (furnace black; general purpose) ts	process	6.8e-5 g
		LCP GF BLACK, Further Additives	2,02E-04			neglected		
		LCP GF BLACK, GF-Fibre	4,05E-03			EU-28: Glass wool ts	process	4.05e-3 g
314-0000-01202	CON. BATTERY CONNECTOR_02-0024-01_2.000 mm_4 pin_12.0mm_YU LIANG_N/A	Electronics, Connector,	4,40E-01	1		Connector Battery (314-0000-01202) - Core Module FP3	plan	4.4e-1 g
		PA9T, Polychlorinated naphthalene	9,40E-02			RoW: glass fibre reinforced plastic production, polyamide, injection moulded ecoinvent 3.5	process	2e-1 g
		PA9T, Additives	2,00E-02			covered above		
		PA9T, Glass wool fibers (inhalable and biopersistent)	8,60E-02			covered above		
		C2680, Iron	9,70E-05			EU-28: Brass (CuZn39Pb3) ts <t-agg>	process	9.7e-2 g
		C2680, Nickel (metallic)	4,85E-04			covered with brass above		
		C2680, Copper	6,31E-02			covered with brass above		
		C2680, Zinc	3,33E-02			covered with brass above		
		C2680, /	4,85E-05			covered with brass above		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
		PLATING Ni, 3,7-diamino-2,8-dimethyl-5-phenylphenazinium chloride	2,50E-02			GLO: Nickel mix ts	process	4.17e-2 g
		PLATING Ni, nickel bis(sulfamidate); nickel sulfamate	1,67E-02			covered above		
		PLATING Au, 1,2,3-Propanetricarboxylic acid, 2-hydroxy-	9,92E-03			neglected		
		PLATING Au, citric acid, potassium salt	2,67E-02			neglected		
		PLATING Au, Gold	1,53E-03			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	1.53e-3 g
		PLATING MATTE, tin(II) methanesulphonate	1,90E-02			GLO: Tin ts	process	6.32e-2 g
		PLATING MATTE, methanesulphonic acid	4,42E-02			covered above		
321-0000-00790	PCB_8901_FR4-HF_136.1*65.52mm_1.000 mm_12 Layer_Selective Gold+O.S.P_GOLD CIRCUIT_8901MB-008,3-6-3	Electronics, PCB, FR4 HF 12 Layers	3,00E+00	1	89.16 cm2	GLO: Printed Wiring Board 12-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts	process	7.14e-3 m2
326-0000-00320	Filter Dual Mode_ICMF062P900MFR_100MHz_2.0mm_MODA-INNOCHIPS_Common Mode,4pin,90 Ohm,100mA,0.87x0.67x0.47mm	Electronics, Filter, Ceramic multilayer type SMD component	1,38E-03	10	603	covered with 302-1000-01494		
326-0000-00349	Filter SAW_SAFFB1G56KB0F0AR15_1561.10/1575.42/1602 MHz_4.0mm_MURATA_50/50 OHM-SMD 5PIN	Electronics, Filter, SAW Filter	1,71E-03	2	5 Pin, 1.1x0.9x0.5	GLO: Filter SAW (25mg) 3x7x1 ts	process	19

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
326-0000-00352	Filter SAW_SAFFB942MANOF0AR15_942.5MHz_MURATA_G SM900/BAND8 Rx-SMD 5 pin	Electronics, Filter, SAW Filter	1,71E-03	1	5 Pin, 1.1x0.9x0.5	covered with 326-0000-00349		
326-0000-00354	Filter SAW_SAFFB1G84AB0F0AR15_1842.5 ± 35.1MHz_MURATA_Band3 Rx 50/50 Ohm-SMD 5 PIN	Electronics, Filter, SAW Filter	1,71E-03	1	5 Pin, 1.1x0.9x0.5	covered with 326-0000-00349		
326-0000-00363	Filter SAW_SAFFB2G14AA0F0AR15_2140MHz±30MMZ_MURATA_Band1/Band4 Rx 50/50 Ohm 5PIN	Electronics, Filter, SAW Filter	1,71E-03	1	5 Pin, 1.1x0.9x0.5	covered with 326-0000-00349		
326-0000-00364	Filter SAW_SAFFB1G96AB0F0AR15_1960MHz±30MHZ_MURATA_Band2,50/50 Ohm,SMD 5PIN	Electronics, Filter, SAW Filter	1,71E-03	1	5 Pin, 1.1x0.9x0.5	covered with 326-0000-00349		
326-0000-00473	Filter Bandpass_RFLPF1608060F18Q1C_673~2690 MHz_4.0mm_WALSIN_LTE Application,SMD 0603 3PIN	Electronics, Filter, Multilayer Ceramic (low pass filter)	2,57E-03	1	0603	covered with 302-1000-01494		
326-0000-00482	Filter SAW_SAFFB876MAA0F0AR15_876.5±17.5MHZ_2.0mm_MURATA_Band26 Unbalanced 50/50 ohm 5PIN	Electronics, Filter, SAW Filter	1,71E-03	1	5 Pin, 1.1x0.9x0.5	covered with 326-0000-00349		
326-0000-00537	Filter Bandpass_RFLPF1005040YM1T76_766.5±20.5MHz,_2.0mm_WALSIN_LOW PASS FILTER6 PIN	Electronics, Filter, Multilayer Ceramic (low pass filter)	9,90E-04	1	402	covered with 302-1000-01494		
326-0000-00539	Filter SAW_SAFFB742MAA0F0AR15_737.5MHz±8.5MHZ_2.0mm_MURATA_Band12+13/Unbalanced,50/50Ohm SMD 5 PIN	Electronics, Filter, SAW Filter	1,71E-03	1	5 Pin, 1.1x0.9x0.5	covered with 326-0000-00349		
326-0000-00634	Filter SAW_SAFFB806MAB0F0AR1X_806±15 MHz_2.0mm_MURATA_For B20 DRx,50/50 Ohm, 5PIN	Electronics, Filter, SAW Filter	1,70E-03	1	5 Pin, 1.1x0.9x0.5	covered with 326-0000-00349		
326-0000-00635	Filter SAW_SAFFB2G65AC0F0AR1X_2655±35 MHz_2.0mm_MURATA_Band7, 50/50 Ohm, 5PIN	Electronics, Filter, SAW Filter	1,71E-03	1	5 Pin, 1.1x0.9x0.5	covered with 326-0000-00349		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
326-0000-00646	Filter Bandpass_QM22545TR13-15K_2.4GHz_4.0mm_QORVO_N/A	Electronics, Filter, no datasheet found	0,00E+00	1		covered with 302-1000-01494		
326-0000-00650	Filter Balance_RFBLN1608070F48Q1C_673 ~ 2700 MHz_4.0mm_WALSIN_Filter+Balun, 50Ohm, 0603, 6Pins	Electronics, Filter,	2,94E-03	1	0603, 6 Pins	covered with 302-1000-01494		
329-0000-00169	SAW Duplexer_B39781B8620P810_EPCOS_LTE Band 13, 782/751MHz,8PIN	Electronics, Duplexer (Filter?), Ni, Au-plated terminals	4,00E-03	1	1.8 x 1.4 mm <sup>2</sup>	covered with 302-1000-01494		
329-0000-00170	SAW Duplexer_B39851B8622P810_EPCOS_LTE Band 20, 847/806 MHz,9PIN	Electronics, Duplexer (Filter?), SAW Duplexer, no datasheet found	3,51E-03	1		covered with 326-0000-00349		
329-0000-00188	SAW Duplexer_4.0mm_SAYEY1G73BA0F0AR05_MURATA_1732.5/2132.5MHz,Band4,50/50 8PIN	Electronics, Duplexer (Filter?), SAW Duplexer	5,20E-03	1	8 Pin, 1.8x1.4x0.6(max)	covered with 326-0000-00349		
329-0000-00189	SAW Duplexer_4.0mm_SAYEY1G95GA0F0AR05_MURATA_1950/2140MHz,Band1,50/50 8PIN	Electronics, Duplexer (Filter?), SAW Duplexer	5,20E-03	1	8 Pin, 1.8x1.4.0.6	covered with 326-0000-00349		
329-0000-00198	SAW Duplexer_4.0mm_SAYEY831MBA0B0AR05_MURATA_831.5/876.5MHz,Band26, 50/50 ohm 8PIN	Electronics, Duplexer (Filter?), SAW Duplexer	5,20E-03	1	8 Pin, 1.8x1.4.0.6	covered with 326-0000-00349		
329-0000-00202	SAW Duplexer_4.0mm_SAYEY897MBG0F0AR05_MURATA_Band8 Unbalanced LR 1814	Electronics, Duplexer (Filter?), SAW Duplexer	5,20E-03	1	8 Pin, 1.8x1.4.0.6	covered with 326-0000-00349		
329-0000-00259	SAW Diplexer_4.0mm_RFDIP160806ALM6T30_WALSIN_2.4 GHz&5 GHz ISM Band,2450/5425MHz,6PIN	Electronics, Duplexer (Filter?), SAW Diplexer, multilayer ceramic	2,63E-03	1	1.6x0.8x0.6	covered with 326-0000-00349		
329-0000-00283	SAW Duplexer_4.0mm_B39272B8674P810_EPCOS_N/A	Electronics, Duplexer (Filter?), SAW Duplexer	4,02E-03	1	8 Pin, 1.8x1.4.0.6	covered with 326-0000-00349		
329-0000-00285	SAW Duplexer_4.0mm_QM23003_QORVO_N/A	Electronics, Duplexer (Filter?), SAW Duplexer	0,00E+00	1	1814	covered with 326-0000-00349		
329-0000-00286	SAW Duplexer_4.0mm_QM23002TR13_QORVO_N/A	Electronics, Duplexer (Filter?), SAW Duplexer	0,00E+00	1	1814	covered with 326-0000-00349		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
415-59290-0024	HOLDER_5929_SILVER_STAINLESS STEEL_Plating Ni-Sn_Coaxial cable holder_PLIGHT(JIANGSU)_h=1.34mm	Mechanical, Shielding, Stainless steel, Plating Ni-Sn	4,10E-03	5	5,11E+00	EU-28: Stainless steel sheet (EN15804 A1-A3) ts <t-agg>	process	5.11 g
415-89010-0002	CASE_8901_SILVER_COPPER-NICKEL-ZINC ALLOY_N/A_BT/WIFI Shielding COVER_CJR_N/A	Mechanical, Shielding, Copper-Nickel-Zinc alloy	4,42E-01	1	3,14E+00	Nickel-Silver sheet - FP3	further inputs	3.14 g
415-89010-0003	CASE_8901_SILVER_COPPER-NICKEL-ZINC ALLOY_N/A_GPS Shielding COVER_CJR_N/A	Mechanical, Shielding, Copper-Nickel-Zinc alloy	9,10E-02	1		covered with 415-89010-0002		
415-89010-0018	CASE_8901_SILVER_COPPER-NICKEL-ZINC ALLOY_N/A_Audio shielding cover_CJR_N/A	Mechanical, Shielding, Copper-Nickel-Zinc alloy	3,00E-01	1		covered with 415-89010-0002		
415-89010-0017	SHEET_8901_SILVER_COPPER ALLOY_N/A_NFC SHD Frame_CJR_N/A	Mechanical, Shielding, Copper-Nickel-Zinc alloy	3,10E-01	1		covered with 415-89010-0002		
415-89010-0004	CASE_8901_SILVER_STAINLESS STEEL_N/A_NFC Shielding COVER_CJR_N/A	Mechanical, Shielding, Stainless steel		1		covered with 415-59290-0024		
415-89010-0005	CASE_8901_SILVER_COPPER-NICKEL-ZINC ALLOY_N/A_CPU Shielding FRAME_CJR_N/A	Mechanical, Shielding, Copper-Nickel-Zinc alloy	4,95E-01	1		covered with 415-89010-0002		
415-89010-0006	CASE_8901_SILVER_STAINLESS STEEL_N/A_CPU Shielding COVER_CJR_N/A	Mechanical, Shielding, stainless steel	1,86E+00	1		covered with 415-59290-0024		
415-89010-0007	CASE_8901_SILVER_COPPER-NICKEL-ZINC ALLOY_N/A_RF BACK Shielding FRAME_CJR_N/A	Mechanical, Shielding, Copper-Nickel-Zinc alloy	4,55E-01	1		covered with 415-89010-0002		
415-89010-0008	CASE_8901_SILVER_STAINLESS STEEL_N/A_RF BACK Shielding COVER_CJR_N/A	Mechanical, Shielding, stainless steel	1,26E+00	1		covered with 415-59290-0024		
415-89010-0009	CASE_8901_SILVER_COPPER-NICKEL-ZINC ALLOY_N/A_BB Shielding FRAME_CJR_N/A	Mechanical, Shielding, Copper-Nickel-Zinc alloy	8,35E-01	1		covered with 415-89010-0002		
415-89010-0010	CASE_8901_SILVER_STAINLESS STEEL_N/A_BB Shielding COVER_CJR_N/A	Mechanical, Shielding, stainless steel	1,80E+00	1		covered with 415-59290-0024		
415-89010-0011	CASE_8901_SILVER_COPPER-NICKEL-ZINC ALLOY_N/A_RF FRONT Shielding FRAME_CJR_N/A	Mechanical, Shielding, Copper-Nickel-Zinc alloy	2,11E-01	1		covered with 415-89010-0002		
415-89010-0012	CASE_8901_SILVER_STAINLESS STEEL_N/A_RF FRONT Shielding COVER_CJR_N/A	Mechanical, Shielding, stainless steel	1,80E-01	1		covered with 415-59290-0024		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
314-0000-00971	CON. NANO SIM CARD CONNECTOR_SM051-12116A01D_2.540 mm_6 pin_16.0mm_JTCONN_H=1.25mm	Electronics, Connector,	2,76E-01	2		Connector nano SIM (314-0000-00971) - Core Module FP3	2*2.76e-1 g	
		Au PLATING, others	1,50E-06			neglected		
		Au PLATING, Gold	2,99E-06			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	2.99e-6 g
		Au PLATING, Cobalt metal powder	4,50E-06			GLO: Cobalt, refined (metal) CDI	process	4.5e-6 g
		SHELL SUS301, manganese	2,57E-03			DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	1.37e-1 g
		SHELL SUS301, Nickel (metallic)	1,03E-02			covered by stainless steel above		
		SHELL SUS301, Carbon	1,93E-04			covered by stainless steel above		
		SHELL SUS301, Iron	9,26E-02			covered by stainless steel above		
		SHELL SUS301, Silicon	9,65E-04			covered by stainless steel above		
		SHELL SUS301, Sulfur	3,86E-05			covered by stainless steel above		
		SHELL SUS301, chromium	2,19E-02			covered by stainless steel above		
		SHELL SUS301, Red phosphorous	5,79E-05			covered by stainless steel above		
		TERMINAL C5240, Lead	8,64E-06			RoW: bronze production ecoinvent 3.5	process	8.64e-2 g
		TERMINAL C5240, Zinc	5,18E-05			covered by bronze above		
		TERMINAL C5240, Tin	7,78E-03			covered by bronze above		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
		TERMINAL C5240, Iron	2,59E-05			covered by bronze above		
		TERMINAL C5240, Copper	7,85E-02			covered by bronze above		
		TERMINAL C5240, Red phosphorous	6,91E-05			covered by bronze above		
		SPRING SUS301, Iron	5,97E-03			covered by stainless steel above		
		SPRING SUS301, Sulfur	2,49E-06			covered by stainless steel above		
		SPRING SUS301, Carbon	1,24E-05			covered by stainless steel above		
		SPRING SUS301, manganese	1,66E-04			covered by stainless steel above		
		SPRING SUS301, Nickel (metallic)	6,61E-04			covered by stainless steel above		
		SPRING SUS301, Silicon	6,22E-05			covered by stainless steel above		
		SPRING SUS301, chromium	1,41E-03			covered by stainless steel above		
		SPRING SUS301, Red phosphorous	3,73E-06			covered by stainless steel above		
		HOUSING LCP BL3135, LIQUID CRYSTAL POLYMER	2,63E-02			DE: Polyester Resin unsaturated (UP) ts	process	2.63e-2 g
		HOUSING LCP BL3135, Glass wool fibers (inhalable and biopersistent)	1,37E-02			EU-28: Glass wool ts	process	1.37e-2 g
		HOUSING LCP BL3135, PROCESSING ADDITIVES	4,04E-04			neglected		
		Ni PLATING, Nickel (metallic)	6,99E-06			GLO: Nickel mix ts	process	6.99e-6 g
		Ni PLATING, others	1,40E-05			neglected		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
		SLIDE PA46/HF4540, Polyamide 46	8,70E-03			DE: Polyamide 6.6 Granulate (PA 6.6) ts	process	8.7e-3 g
		SLIDE PA46/HF4540, Carbon black (airborne, unbound particles of respirable size)	4,37E-05			DE: Carbon black (furnace black; general purpose) ts	process	4,37E-05
		PULL BAR SUS304, manganese	3,15E-05			EU-28: Stainless steel cold rolled coil (304) Eurofer <t-agg>	process	3,15E-03
		PULL BAR SUS304, Carbon	1,89E-06			covered by stainless steel above		
		PULL BAR SUS304, Nickel (metallic)	2,64E-04			covered by stainless steel above		
		PULL BAR SUS304, chromium	5,99E-04			covered by stainless steel above		
		PULL BAR SUS304, Red phosphorous	1,26E-06			covered by stainless steel above		
		PULL BAR SUS304, Silicon	1,58E-05			covered by stainless steel above		
		PULL BAR SUS304, Sulfur	6,30E-07			covered by stainless steel above		
		PULL BAR SUS304, Iron	2,24E-03			covered by stainless steel above		
314-0000-01148	CON. MICRO SD CONNECTOR_1MSD010D09R1R_00_0.800 mm_8 pin_20.0mm_GOLDENCONN_H=1.28mm	Electronics, Connector, no datasheet found	3,45E-01	1		Micro SD card connector - FP3	plan	
600-0000-00038	Consumable_Solder Paste_SAC305 M8_AIMSOLDER_SAC305 M8	Solder, SAC305,	1,50E+00	1,5		GLO: Solder paste SnAg3Cu0.5 (SAC-Lot) ts	process	1.5 g
415-89010-0019	CABLE_8901_BLACK_COPPER ALLOY_N/A_RF CONN_ECT_75.00 mm	Mechanical, Cable, Cable, Copper Alloy	4,17E-01	1	75 mm	GLO: Cable 1-core signal 24AWG mPPE (3.0 g/m) D1.1 ts	process	0,075



Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
478-581500-031	WATER DISSOLVE LABEL _Mech. Label_5815_Global_WATER DISSOLVE LABEL_3*3mm_Reel packing_H SIN YI DE		#NV	2	3*3mm	neglected		
402-89010-0005	Rear Cabinet_8901_BLACK_PC_N/A_Rear Cover Ass'y for Lotte SC-110R_CREATOR_N/A	Plastic, Midframe, PC	1,48E+01	1		DE: Polycarbonate Granulate (PC) ts	process	14.8 g
402-89010-0009	Rear Cabinet_8901_BLACK_PC_N/A_8901 REAR COVER SC-1100R FOR ARIMA_CREATOR_N/A	Plastic, PC		1		covered above		
415-89010-0041	GASKET_8901_BLACK_PORON_N/A_MIC sponge_HUALONG_N/A	PORON Foam		2		neglected		
415-89010-0042	GASKET_8901_BLACK_PORON_N/A_speaker sponge_HUALONG_N/A	PORON Foam		1		neglected		
404-89010-0001	Key_8901_BLACK_ALUMINUM_NCVN_N/A_8901 side key assy_CJR_N/A	Aluminium + coating (?)		1		neglected		
415-89010-0046	GASKET_8901_BLACK_PORON_N/A_coaxial sponge_HUALONG_N/A	PORON Foam		1		neglected		
336-0000-00275	Fingerprint module_5246B_NA_Φ10 mm_DOLFA_N/A		3,22E+00	1		Fingerprint sensor - FP3 <t-agg>	further inputs	
		Flex board				GLO: Printed Wiring Board 1-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts	process	1,1129 cm2
321-M000-00244	MODULE_8901_Pi-RoHS_46.85*14.95mm_0.120 mm_2 Layer_Selective Gold+O.S.P_ALL- WINNER_8901SKB-004,Side Key	Electronics, PCB, 2 layers	4,21E-01	1	1.36cm2	GLO: Printed Wiring Board 2-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts	process	1.36e- 4 m2
409-00000-0276	Machine Screw_Flat_Cross(JCIS)_2.5mm_3.5_SILVER_Steel_Platin g_H.N.M_N/A	Mechanical, Screw, Steel	4,61E-02	9	22	Screw 2,5 mm silver (409-00000-0276) - FP3	plan	

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm2]	GaBi Process	Level	Scale in GaBi
415-89010-0015	SLEEVE_8901_SILVER_ALUMINUM_N/A_Pogo pin protective frame_CJR_AL metal + Gasket	Mechanical, Aluminium	5,00E-01	1		EU-28: Aluminium extrusion profile ts	process	0.5 g
321-M000-00245	MODULE_8901_Pi-RoHS_13.5*14.18mm_0.200 mm_3 Layer_Selective Gold+O.S.P_ALL-WINNER_8901CB2-003,Rear Camera	Electronics, PCB, 3 layers (?), Flex PCB Camera	1,22E+00	1	1.82cm2	GLO: Printed Wiring Board 1-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts + connector on both sides	process	7.06e-4 m2
321-M000-00243	MODULE_8901_Pi-RoHS_18.27*14.0mm_0.200 mm_3 Layer_Selective Gold+O.S.P_ALL-WINNER_8901BTBS-004,South FPC	Electronics, PCB, 3 layers (?), Flex PCB Camera	1,28E+00	1	2.25cm2	covered above		
321-M000-00242	MODULE_8901_Pi-RoHS_23.8*21.3mm_0.18 mm_2 Layer_Selective Gold+O.S.P_ALL-WINNER_8901BTBN-004,North FPC	Electronics, PCB, 2 layers, Flex PCB	4,30E-01	1	2.99cm2	covered above		
415-89010-0014	HOLDER_8901_SILVER_STAINLESS STEEL_N/A_Metal Cover MIDDLE_CJR_N/A	Mechanical, Stainless steel	9,00E+00	1		EU-28: Stainless steel sheet (EN15804 A1-A3) ts <t-agg>	process	6.773 g
409-00000-0275	Machine Screw_Flat_TORX_2.5mm_3.0_BLACK_Steel_Plating_H.N.M_N/A	Mechanical, Screw, Steel	4,20E-02	2		Screw 2,5 mm (409-00000-0275) - FP3 <LZ>	plan	
409-00000-0276	Machine Screw_Flat_Cross(JCIS)_2.5mm_3.5_SILVER_Steel_Plating_H.N.M_N/A	Mechanical, Screw, Steel	4,61E-02	13		covered with 409-00000-0276 above		

**8.3.2  
Top module**

Annex

**Table 8-6: Inventory list top module**

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
8-8902-00-0009	PCBA Ass'y_8902_BLACK_North Module sub-assy	Module	5,10E+00	1		FP3 Top Module	Plan	5.1 g
401-89010-0008	Front Cabinet_8901_BLACK_PC_N/A_North Module Front Cover_CREATOR_N/A	Plastic, PC?	1,04E+00	1	1,89E+00	EU-28: Polycarbonate PlasticsEurope	process	1.89 g
313-0000-00352	RECEIVER_SD1206-S-3_12.0 * 6.0mm_32 Ohm_117dB_CHANG ZHOU YU CHENG_N/A		3,87E-01	1		Receiver FP3 Top Module (313-0000-00352)	further inputs	
		Stainless steel2, Nickel (metallic)	7,07E-04			EU-28: Stainless steel sheet (EN15804 A1-A3) ts <t-agg>	process	0.0797 g
		Stainless steel2, Carbon	3,80E-06			see above		
		Stainless steel2, Sulfur	2,28E-06			see above		
		Stainless steel2, chromium	1,49E-03			see above		
		Stainless steel2, Iron	5,32E-03			see above		
		Stainless steel2, Silicon	6,48E-05			see above		
		Stainless steel2, manganese	1,25E-05			see above		
		Stainless steel2, Red phosphorous	2,89E-06			see above		
		NdFeP, other	2,19E-03			neglected		
		NdFeP, Iron	5,98E-02			neglected		
		NdFeP, Praseodymium	1,32E-02			CN: Praseodymium ts	process	1.32e-2 g
		NdFeP, dysprosium	9,12E-04			neglected		
		NdFeP, boron	1,00E-03			GLO: boric oxide production ecoinvent	process	1e-3 g
		NdFeP, Neodymium	1,40E-02			GLO: neodymium oxide to generic market for mischmetal ecoinvent	process	1.4e-2 g
		PPA, Glass wool fibers (inhalable and biopersistent)	1,54E-02			EU-28: Glass wool ts	process	1.54e-2 g

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		PPA, Impact Modifier	2,57E-03			neglected		
		PPA, Anti Oxidant	1,17E-03			neglected		
		PPA, Other additives	9,36E-04			neglected		
		PPA, Polyphthalamide	2,67E-02			EU-28: Polyamide 6.6 fibres (PA 6.6) ts	process	2.74e-2 g
		Cold rolled plate, Red phosphorous	3,54E-05			DE: Steel cold rolled coil <1,5mm ts <t-agg>	process	0,151 g
		Cold rolled plate, Carbon	1,06E-04			covered with colled rolled steel above		
		Cold rolled plate, Sulfur	3,54E-05			covered with colled rolled steel above		
		Cold rolled plate, Iron	7,00E-02			covered with colled rolled steel above		
		Cold rolled plate, manganese	5,66E-04			covered with colled rolled steel above		
		PEEK, Polyetheretherketone	1,80E-03			DE: Polyetherether ketone granulate (PEEK) ts	process	1.8e-3 g
		Super high line, Polyamide	7,30E-04			covered with polyamide above		
		Super high line, Copper	1,33E-02			GLO: Copper mix (99,999% from electrolysis) ts	process	1.33e-2 g
		Super high line, Silver	5,84E-04			GLO: Silver mix ts	process	5.84e-4 g
		Stainless steel, Sulfur	2,16E-05			covered with stainless steel above		
		Stainless steel, manganese	1,19E-04			covered with stainless steel above		
		Stainless steel, Red phosphorous	2,74E-05			covered with stainless steel above		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		Stainless steel, Iron	5,05E-02			covered with stainless steel above		
		Stainless steel, Carbon	3,61E-05			covered with stainless steel above		
		Stainless steel, Nickel (metallic)	6,71E-03			covered with stainless steel above		
		Stainless steel, Silicon	6,14E-04			covered with stainless steel above		
		Stainless steel, chromium	1,41E-02			covered with stainless steel above		
		PEN, Poly ethylene naphthalate	1,60E-03			neglected		
		PEN, Silicon dioxide	3,20E-06			neglected		
		Cold rolled plate2, Red phosphorous	4,02E-05			covered with colled rolled steel above		
		Cold rolled plate2, Sulfur	4,02E-05			covered with colled rolled steel above		
		Cold rolled plate2, manganese	6,42E-04			covered with colled rolled steel above		
		Cold rolled plate2, Iron	7,95E-02			covered with colled rolled steel above		
		Cold rolled plate2, Carbon	1,20E-04			covered with colled rolled steel above		
335-0000-00280	CAMERA MODULE CMOS_HTE1006_8MP_HOLITECH_N/A		2,29E-01	1		Camera Module CMOS (335-0000-00280) - Top Module FP3 <t-agg>	plan	
		12X5BT, Silicon dioxide	4,50E-06			neglected		0,0001445 g
		12X5BT, Acrylic resin	2,25E-05			neglected		
		12X5BT, Carbon black (airborne, unbound particles of respirable size)	2,25E-05			DE: Carbon black (furnace black; general purpose) ts	process	0,0009265 g

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		12X5BT, Polyethylene Terephthalate (PET)	9,00E-05			EU-28: Polyethylene terephthalate fibres (PET) ts	process	0,000389 g
		12X5BT, Wax	1,05E-05			EU-28: Wax / Paraffins at refinery ts	process	0,0000105 g
		LCP E525T, LCP	2,13E-02			DE: Polyester Resin unsaturated (UP) ts	process	0,02128 g
		LCP E525T, Carbon black (airborne, unbound particles of respirable size)	8,00E-04			covered in carbon black above		
		LCP E525T, Inorganic filler	9,92E-03			neglected		
		Copper Foil, chromium	1,40E-06			RER: chromium productionecoinvent 3.5	process	0,0000014 g
		Copper Foil, Zinc	5,60E-06			DE: Zinc redistilled mix ts	process	0,0000056 g
		Copper Foil, Copper	1,40E-02			GLO: Copper mix (99,999% from electrolysis) ts	process	0,0173159 g
		Copper Foil, Nickel (metallic)	7,00E-06			GLO: Nickel mix ts	process	0,001585 g
		FH8633, Hardener	3,00E-05			neglected		
		FH8633, Formaldehyde, polymer with 2-(chloromethyl)oxirane and phenol	7,50E-05			DE: Formaldehyde (HCHO; 100%) ts	process	0,0000075 g
		FH8633, Calcium carbonate	4,50E-05			EU-28: Calcium carbonate > 63 microns IMA-Europe/ELCD	process	0,0000045 g
		TAM-LCM-75, Oxycarboxylic acid	1,35E-03			neglected		
		TAM-LCM-75, Oxycarboxylic acid salt	5,80E-04			neglected		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		TAM-LCM-75, Oxalic acid salt	2,30E-04			neglected		
		TAM-LCM-75, ammonia ....%	1,50E-04			neglected		
		TAM-LCM-75, Amino-carboxylic acid salt	6,90E-04			neglected		
		TAM-LCM-75, Water	7,00E-03			EU-28: Process waters	process	0,01712 g
		C5191R, Copper	1,31E-03			covered in copper above		
		C5191R, Tin	8,40E-05			GLO: Tins	process	0,001157 g
		C5191R, Red phosphorous	2,10E-06			neglected		
		Ti3O5, Ti3O5	1,20E-05			neglected		0,000147 g
		Ti3O5, Ti3O5	1,35E-04			neglected		
		Conductive cloth, Copper	3,60E-05			covered in copper above		
		Conductive cloth, Polyethylene Terephthalate (PET)	1,80E-05			covered in PET above		
		Conductive cloth, Nickel (metallic)	1,80E-05			covered in nickel above		
		Conductive cloth, Viscose	4,80E-05			neglected		
		C5191, Copper	1,86E-03			covered in copper above		
		C5191, Tin	1,33E-04			covered in tin above		
		C5191, Red phosphorous	7,00E-06			neglected		
		SP168GN, Glass wool fibers (inhalable and biopersistent)	4,50E-03			EU-28: Glass wool ts	process	0,005176 g
		SP168GN, Inorganic Filler	2,50E-03			neglected		
		SP168GN, Halogen-free Epoxy Resin Blend	3,00E-03			neglected		
		Gold wire, Gold	3,00E-04			GLO: Gold (primary) ts	process	0,0003 g

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		BRASS, Zinc	7,11E-03			EU-28: Brass (CuZn39Pb3) ts <t-agg>	process	2.19e-2 g
		BRASS, Copper	1,38E-02			covered with brass above		
		BRASS, Tin	1,10E-04			covered with brass above		
		BRASS, Iron	1,10E-04			covered with brass above		
		BRASS, Cadmium	2,19E-07			covered with brass above		
		BRASS, Lead	1,97E-05			covered with brass above		
		BRASS, Bismuth	7,68E-04			covered with brass above		
		X5R ceramics powder , Yttrium oxide	1,00E-05			neglected		
		X5R ceramics powder , Barium oxide (BaO)	4,40E-04			GLO: barium oxide production ecoinvent 3.5	process	0,00044 g
		X5R ceramics powder , Calcium oxide (CaO)	8,00E-05			neglected		
		X5R ceramics powder , Titanium dioxide (airborne, unbound particles of respirable size)	4,10E-04			RER: titanium dioxide production, chloride process ecoinvent 3.5	process	0,00041 g
		NI, Nickel (metallic)	1,25E-03			covered in nickel above		
		S-380W, Sulfuric acid, barium salt (1:1)	2,40E-03			neglected		
		S-380W, epoxy resin	3,60E-03			DE: Epoxy Resin (EP) Mix ts	process	0,00367 5 g



Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		S-380W, Ethanol, 2-(2-ethoxyethoxy)-, 1-acetate	6,00E-04			neglected		
		S-380W, Talc containing asbestiform fibers	6,00E-04			covered in talcum powder above	process	0,00665 g
		S-380W, Defoaming agent	1,20E-04			neglected		
		S-380W, SiO <sub>2</sub>	6,00E-04			neglected		
		S-380W, (2-methoxymethylethoxy)propanol	6,00E-04			neglected		
		S-380W, Inorganic pigment	3,48E-03			neglected		
		Nickel, Nickel (metallic)	2,00E-05			covered in nickel above		
		LCP, Talc containing asbestiform fibers	1,04E-03			covered in talcum powder above		
		LCP, Glass wool fibers (inhalable and biopersistent)	6,76E-04			covered in glass wool above		
		LCP, Carbon black (airborne, unbound particles of respirable size)	1,04E-04			covered in carbon black above		
		LCP, Aromatic Polyester	3,38E-03			neglected		
		M705-S101ZH, Silver	2,70E-06			GLO: Solder paste SnAg3Cu0.5 (SAC-Lot) ts	process	9.5e-5 g
		M705-S101ZH, Copper	3,00E-06			covered with solder paste above		
		M705-S101ZH, solvent	9,30E-06			covered with solder paste above		
		M705-S101ZH, Tin	8,00E-05			covered with solder paste above		
		M705-S101ZH, Rosin	5,00E-06			covered with solder paste above		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		SF305C, 1H,3H-Benzo[1,2-c:4,5-c']difuran-1,3,5,7-tetrone, polymer with 4,4'-oxybis[benzenamine]	7,80E-03			neglected		
		SF305C, Halogen-free adhesive of epoxy resin	4,20E-03			neglected		
		A-11D, 1,3,5-Triazine-2,4,6(1H,3H,5H)-trione, compd. with 6-[2-(2-methyl-1H-imidazol-1-yl)ethyl]-1,3,5-triazine-2,4-diamine (1:1)	2,20E-04			neglected		
		A-11D, Epichlorohydrin-bisphenol A resin	5,85E-04			neglected		
		A-11D, Others	5,50E-05			neglected		
		A-11D, Silicon dioxide	1,40E-04			neglected		
		SF202, Copper	3,06E-02			covered in copper above		
		SF202, 1H,3H-Benzo[1,2-c:4,5-c']difuran-1,3,5,7-tetrone, polymer with 4,4'-oxybis[benzenamine]	5,40E-03			neglected		
		7972, Silicones, monoorgano	3,50E-06			neglected		
		7972, 2-Ethylhexyl acrylate	6,55E-05			neglected		
		7972, Pulp, cellulose	3,07E-04			neglected		
		7972, Polyethylene Terephthalate (PET)	1,31E-04			covered in PET above		
		Tin, Tin	4,00E-05			covered in tin above		
		Copper Termination, Copper	1,20E-04			covered in copper above		
		SV-55, aluminium oxide	4,05E-05			GLO: aluminium oxide productionecoinvent	process	0,0000405 g
		SV-55, Quartz (SiO <sub>2</sub> )	9,45E-05			neglected		
		OKP1, Fluorene based polyester copolymer	8,54E-03			neglected		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		Sn, Tin	9,00E-04			covered in tin above		
		UV HQ210, acrylate	4,60E-04			neglected		
		Nickel Paste for X5R, Nickel (metallic)	2,90E-04			covered in nickel above		
		FH8808, Modified epoxy resin	3,00E-05		0.78cm2	GLO: Printed Wiring Board 1-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts	process	7.8e-5 m2
		FH8808, curing agent	4,50E-05			covered above		
		FH8808, epoxy resin	7,50E-05			covered above		
		12inch-ClS, Silicon	5,80E-04		0,180093	IC-Front-End - FP2	process	1.80093 e-5 m2
		NPG-1-AS, Water	6,15E-03			covered in water above		
		NPG-1-AS, Nickel(II) sulfate hexahydrate (1:1:6)	3,56E-03			neglected		
		NPG-1-AS, Carboxylic acid salt	2,90E-04			neglected		
		ZEONEX K26R, Polycycloolefin Resin	5,61E-03			neglected		
		ZEONEX K26R, Polymer Stabilizer	1,14E-04			neglected		
		PET, Polyethylene Terephthalate (PET)	1,50E-04			covered in PET above		
		AU, Aurate(1-), bis(cyano- $\kappa$ C)-, potassium (1:1)	1,25E-03			neglected		
		SF-PC6000-U1, Silver	2,04E-04					
		SF-PC6000-U1, Copper	8,04E-04			covered in copper above		
		SF-PC6000-U1, Polyethylene Terephthalate (PET)	1,01E-02			covered in PET above		
		SF-PC6000-U1, Epoxy Resin Formulation	9,24E-04			covered in epoxy resin above		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		PC DN-5615B, Talc containing asbestiform fibers	5,01E-03			covered in talcum powder above		
		PC DN-5615B, Carbonic dichloride, polymer with 4,4'-(1-methylethylidene)bis[phenol]	2,84E-02			neglected		
		Si2O, Quartz (SiO2)	8,00E-06			neglected		
		TPD-35-B, Phosphinic acid, sodium salt (1:1)	1,03E-03			neglected		
		TPD-35-B, Water	3,97E-03			covered in water above		
		PSR4000MEH, Heavy aromatic solvent naphtha	1,32E-03			neglected		
		PSR4000MEH, Silica	2,16E-03			DE: Silica sand (flour) ts	process	0,00216 g
		PSR4000MEH, Other	8,40E-03			neglected		
		PSR4000MEH, Fluorides	1,20E-04			neglected		
402-89010-0004	Rear Cabinet_8901_BLACK_PLASTIC+METAL_N/A_North Module-Rear Cover ASSY_CREATOR_N/A		1,61E+00	1		see below		
409-00000-0275	Machine Screw_Flat_TORX_2.5mm_3.0_BLACK_Steel_Plating_H.N.M_N/A	Mechanical, Screw, Steel	4,20E-02	3		Screw 2,5 mm (409-00000-0275) - FP3 <LZ>	plan	
8-8902-00-0002	Daughter Board_8902_NATURAL_North board		#NV	1		see below		
8PCB-8901-0002	PCB_8901_NON_North board	Electronics, PCB,	1,38E+00	1		PCBA Top Module FP3	plan	1.384 g
301-G000-00235	Chip resistor_2.20 Kohm_± 1%_1/16 W_0402_N/A_N/A	Electronics, Resistor, Chip Resistor: Ceramic Substrate, SN Plating, Ni Plating	5,97E-04	1	0402	GLO: resistor production, surface-mounted ecoinvent 3.5	process	8.21e-4 g

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
301-G000-01340	Chip resistor_22.0 Ohm_± 1%_1/20 W_0201_N/A	Electronics, Resistor, Chip Resistor: Ceramic Substrate, SN Plating, Ni Plating	2,24E-04	1	0201	covered with 301-G000-00235		
302-0214-41051	Chip Capacitor_33.0 pF_± 5%_NPO (COG)_25 V_0201_0.3 mm_MURATA_GRM0335C1E330J_N/A	Electronics, Capacitor, MLCC	3,30E-04	6	0201	GLO: Capacitor ceramic MLCC 0201 (0.17mg) D 0.6x0.3x0.3 ts	process	4
302-0222-52104	Chip Capacitor_47.0 nF_± 10%_X5R_10 V_0402_N/A_N/A_MURATA_GRM155R61A473K_N/A	Electronics, Capacitor, MLCC	1,60E-03	1	0402	GLO: Capacitor ceramic MLCC 0603 (6mg) D 1.6x0.8x0.8 ts	process	2
302-1000-01476	Chip Capacitor_2.20 uF_± 10%_X5R_10 V_0402_0.5 mm_MURATA_GRM155R61A225K_N/A	Electronics, Capacitor, MLCC	1,60E-03	1	0402	covered with 302-0222-52104		
302-1000-02552	Chip Capacitor_2.20 uF_± 20%_X5R_6.3 V_0201_0.3 mm_2.0mm_MURATA_GRM033R60J225ME47D_T=0.39 MAX	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41051		
302-G000-00182	Chip Capacitor_100 nF_± 10%_X5R_10 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41051		
302-G000-02068	Chip Capacitor_1.00 uF_± 20%_X5R_6.3 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	2	0201	covered with 302-0214-41051		
303-0321-86076	Chip Inductor_100 nH_± 5%_0402_100 Mhz_0.55 mm_MURATA_LQG15HNR10J02D_N/A	Electronics, Inductor, Multilayer Ceramic Chip Inductor (RF Inductor)	1,07E-03	1	0402	GLO: inductor production, low value multilayer chip ecoinvent 3.5	process	1.45e-2 g
303-1000-00099	Chip Ferrite bead_1800 ohm_± 25%_0402_100 Mhz_0.5 mm_MURATA_BLM15HD1825N1D_DCR<2.2 ohm	Electronics, Inductor, Ferrite Bead	1,21E-03	4	0402	covered with 303-0321-86076		
303-1000-00799	Chip Ferrite bead_220 ohm_± 25%_0603_100 Mhz_0.6 mm_MURATA_BLM18KG2215N1D_DCR<0.05,Idc=220 0 mA	Electronics, Inductor, Ferrite Bead	4,63E-03	1	0603	covered with 303-0321-86076		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
303-1000-01079	Chip Ferrite bead_1000 ohm_± 25%_0402_100 Mhz_0.5 mm_2.0mm_MURATA_BLM15BX102SN1D_DCR=0.65ohm,I <sub>dc</sub> =300mA	Electronics, Inductor, Ferrite Bead	1,16E-03	1	0402	covered with 303-0321-86076		
303-1000-01080	Chip Ferrite bead_1000 ohm_± 25%_0402_100 Mhz_0.5 mm_2.0mm_CHILISIN_SBJ100505T-102Y-N_DCR<0.95ohm,I <sub>dc</sub> <200mA	Electronics, Inductor, Ferrite Bead	1,40E-03	2	0402	covered with 303-0321-86076		
308-0000-00227	CHIP BIPOLARTVS_12V_AIES12U020R2_0402_AMOTECH_C p<0.3pF	Electronics, , transient voltage suppressor diode	4,77E-04	1	0402	GLO: Diode signal SOD123/323/523 (1.59mg) 0.8x0.75x1.6 with Au-Bondwire ts	process	9
308-0000-00281	ESD protection_5.0V_IMG0505350FR_0402_2.0mm_MODAL-INNOCHIP_S_Cp=35 pF	Electronics, , no datasheet found	1,40E-03	6	0402	covered with 308-0000-00227		
308-0000-00328	CHIP BIPOLARTVS_5.0V_ESD5451R-2/TR_0402_2.0mm_WILLSEMI_Packing:DFP1006-2L	Electronics, , transient voltage suppressor diode, 1-Line, Bi-directional, Transient Voltage Suppressors	0,00E+00	2	0402	covered with 308-0000-00227		
309-0000-00204	LED Full Color_19-337/R6GHBHC-A01/2T_RED/GREEN/BLUE_6pin_SMD6_20mA/R=100,G=180,B=50mcd_4.0mm_EVERLIGHT_N/A	Electronics, LED, AlInGaN / InGaN / InGaN	1,80E-03	1	1.6x1.6x0.35	GLO: LED SMD low-efficiency max 50mA (35mg) without Au 3.2x2.8x1.9 ts	process	1 piece
311-0000-02639	I.C SENSOR_MN25733DKDSJD_DFN_8pins_NoMemory_8.0mm_EMINENT_Light Sensor w/ Built-in IR LED	Electronics, IC,	7,77E-02	1	9,75E-03	CMOS logic - FP3 <LZ>	process	9.75e-7 m2
312-0000-00094	MEMS MIC_MSM261D4030Z1CM_64 'dB_- 26dB_± 1.0dB_4*3*1mm_DIGT_BOTTOM_8.0mm_MEMSENSIN_G_N/A	Electronics, Microphone, metal can LGA package	3,77E-04	1	4mm x 3mm x 1mm	GLO: IC WLP CSP 49 (10.2mg) 3.17x3.17x0.55mm CMOS logic (22 nm node) ts	process	1 piece

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
314-0000-00982	CON. SPRING CONNECTOR_J9Y802K00001_1.500 mm_1 pin_4.0mm_KUNZHON_H=1.1mm	Electronics, Connector,	3,50E-03	1		Spring connector small FP3 (314-0000-00982)	plan	
		Nickel compounds	8,00E-05					
		Gold	2,00E-05					
		Tin	1,80E-04					
		Copper	3,20E-03					
314-0000-00989	CON. PCB FEMALE CONNECTOR_BM20B(0.8)-24DS-0.4V(51)_0.400 mm_24 pin_4.0mm_HIROSE_H=0.8mm	Electronics, Connector,	1,73E-02	1		Connector 24 pin (314-0000-00989) - Top Module FP3	plan	1.73e-2 g
		SV CONTACT(2), Tin	4,88E-04			GLO: Tin ts	process	4.88e-4 g
		SV CONTACT(2), Zinc	1,22E-05			GLO: Special high grade zinc ELCD/IZA	process	1.91e-4 g
		SV CONTACT(2), Cadmium	6,10E-07			GLO: Cadmium ts	process	3.79e-5 g
		SV CONTACT(2), Gold	2,39E-05			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	2.79e-5 g
		SV CONTACT(2), Copper	5,58E-03			GLO: Copper mix (99,999% from electrolysis) ts	process	5.93e-3 g
		SV CONTACT(2), Red phosphorous	1,16E-05			neglected		
		SV CONTACT(2), Cobalt metal powder	1,20E-07			GLO: Cobalt, refined (metal) CDI	process	2.01e-5 g
		SV CONTACT(2), Iron	6,10E-06			DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	6,36E-06
		SV CONTACT(2), Nickel (metallic)	6,00E-04			GLO: Nickel mix ts	process	6.28e-4 g
		SV CONTACT(2), Lead	1,22E-06			EU-28: Lead primary and secondary mix ILA <t-agg>	process	1,48E-06

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		HOUSING, Talc containing asbestiform fibers	3,00E-03			EU-28: Talcum powder (filler) ts	process	3e-3 g
		HOUSING, Wholly aromatic liquid crystal polyester(LCP)	5,84E-03			DE: Polyester Resin unsaturated (UP) ts	process	5,84E-03
		HOUSING, Glass wool fibers (inhalable and biopersistent)	1,00E-03			EU-28: Glass wool ts	process	1e-3 g
		HOUSING, Carbon black (airborne, unbound particles of respirable size)	1,50E-04			DE: Carbon black (furnace black; general purpose) ts	process	1,50E-04
		HOUSING, Calcium Stearate	1,00E-05			neglected		
		HOUSING, Fatty acids, montan-wax, ethylene esters	5,00E-06			neglected		
		SV REINFORCED METAL FITTINGS, Cobalt metal powder	2,00E-05			covered by cobalt above		
		SV REINFORCED METAL FITTINGS, Gold	3,98E-06			covered by gold above		
		SV REINFORCED METAL FITTINGS, Nickel (metallic)	2,80E-05			covered by nickel above		
		SV REINFORCED METAL FITTINGS, Zinc	1,79E-04			covered by zinc above		
		SV REINFORCED METAL FITTINGS, Copper	3,48E-04			covered by copper above		
		SV REINFORCED METAL FITTINGS, Lead	2,64E-07			covered by lead above		
		SV REINFORCED METAL FITTINGS, Iron	2,64E-07			covered by iron above		
		SV REINFORCED METAL FITTINGS, Cadmium	3,91E-05			covered by cadmium above		
314-0000-01200	CON. PCB FEMALE CONNECTOR_DF40GB(1.5)-48DS-0.4V(51)_0.400 mm_48 pin_8.0mm_HIROSE_N/A	Electronics, Connector,	8,36E-02	1		FP3 Board-to-board Connector	plan	
		HOUSING, Talc containing asbestiform fibers	1,20E-02					



Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		HOUSING, Carbon black (airborne, unbound particles of respirable size)	6,00E-04					
		HOUSING, Fatty acids, montan-wax, ethylene esters	2,00E-05					
		HOUSING, Wholly aromatic liquid crystal polyester(LCP)	2,34E-02					
		HOUSING, Calcium Stearate	4,00E-05					
		HOUSING, Misc., not to declare	2,00E-05					
		HOUSING, Glass wool fibers (inhalable and biopersistent)	4,00E-03					
		SHIELD BOARD, Gold	2,99E-06					
		SHIELD BOARD, Cobalt metal powder	1,50E-05					
		SHIELD BOARD, Iron	1,99E-05					
		SHIELD BOARD, Copper	1,82E-02					
		SHIELD BOARD, Nickel (metallic)	1,12E-03					
		SHIELD BOARD, Zinc	3,98E-05					
		SHIELD BOARD, Lead	3,98E-06					
		SHIELD BOARD, Tin	1,59E-03					
		SHIELD BOARD, Red phosphorous	3,78E-05					
		SHIELD BOARD, Cadmium	1,99E-07					
		SV(B)CONTACT, Cobalt metal powder	2,40E-07					
		SV(B)CONTACT, Zinc	4,28E-05					
		SV(B)CONTACT, Tin	1,71E-03					
		SV(B)CONTACT, Cadmium	2,14E-07					
		SV(B)CONTACT, Gold	4,78E-05					
		SV(B)CONTACT, Iron	2,14E-05					
		SV(B)CONTACT, Copper	1,96E-02					

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		SV(B)CONTACT, Lead	4,28E-06					
		SV(B)CONTACT, Red phosphorous	4,07E-05					
		SV(B)CONTACT, Nickel (metallic)	1,10E-03					
314-0000-01203	CON. EAR PHONE JACK CONNECTOR_CJE105D21DC-Y-NH_Ø8.50 mm for Phone jack_5 pin_16.0mm_CVILUX_Audio jack 3.5mm	Electronics, Connector,	3,53E-01	1		Ear Phone Jack FP3	further inputs	3,53e-1 g
		Contact2, Red phosphorous	9,70E-05			neglected		
		Contact2, Tin	5,82E-03			GLO: Tin ts	process	7,17e-3 g
		Contact2, Copper	9,11E-02			GLO: Copper mix (99,999% from electrolysis) ts	process	1,12e-1 g
		Au Plating, Gold	7,00E-04			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	7e-4 g
		Contact1, Copper	2,11E-02			covered by copper above		
		Contact1, Tin	1,35E-03			covered by tin above		
		Contact1, Red phosphorous	2,25E-05			neglected		
		BASE, Triphenyl phosphate (TPP)	1,33E-01			GLO: triphenyl phosphate production ecoinvent 3.5	process	1,33e-1 g
		BASE, Carbon black (airborne, unbound particles of respirable size)	4,60E-03			DE: Carbon black (furnace black; general purpose) ts	process	4,6e-3 g
		BASE, Glass wool fibers (inhalable and biopersistent)	9,20E-02			EU-28: Glass wool ts	process	9,2e-2 g
		Nickel Plating, Nickel (metallic)	2,30E-03			GLO: Nickel mix ts	process	2,3e-3 g

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
321-0000-00787	PCB_8901_FR4-HF_16*31mm_0.500 mm_6 Layer_Selective Gold+O.S.P_GOLD CIRCUIT_8901SUBN-007,North,4in1,1-4-1	Electronics, PCB, FR4-HF 6 layers	1,75E+01	1	4.96cm2	GLO: Printed Wiring Board 8-layer rigid FR4 with chemSn elecAuNi finish (Subtractive method) ts	process	8.35e-4 m2
314-0000-01119	CON. SPRING CONNECTOR_J9Y802K02308_NA_1 pin_4.0mm_KUNZHON_H=2.0mm	Electronics, Connector,	4,00E-03	1		Spring connectors FP3 (314-0000-01119) <LZ>	plan	
600-0000-00038	Consumable_Solder Paste_SAC305 M8_AIMSOLDER_SAC305 M8	Solder, SAC305,	2,00E-01	0.2		GLO: Solder paste SnAg3Cu0.5 (SAC-Lot) ts	process	0.2 g
478-890200-006	STICKER LABEL_Packing Label_8902_Global_PET_10*4mm Black_E-LIN(KUNSHAN)	Label, PET	#NV	1		neglected		
415-89020-0002	GASKET_8902_BLACK_PORON_N/A_front camera sponge on holder_HUALONG_with adhesive	PORON Foam + adhesive	#NV	1		neglected		
415-89010-0028	FILTER_8901_BLACK_FELT MESH_N/A_8901 mic mesh_HUALONG_N/A	Felt (Mesh)	7,00E-03	1	1,78E-01	DE: Silicone rubber (RTV-2, condensation) ts	process	1.78e-1 g
415-89010-0029	HOLDER_8901_BLACK_RUBBER_SILICON RUBBER_N/A_8901 psensor rubber_JUSHUO_N/A	Silicon rubber	1,71E-01	1		covered with 415-89010-0028		
415-89010-0030	FILTER_8901_BLACK_FELT MESH_N/A_8901 receiver mesh_HUALONG_N/A	Felt (Mesh)		1		neglected		
403-89010-0003	Lens_8901_BLACK_GLASS_AR Coating_Front camera lens_MINGYONG_N/A	Glass		1		neglected		
415-89010-0045	SHEET_8901_GOLD_COPPER_N/A_north module copper_HUALONG_N/A	Copper (+Gold?)	1,19E-01	1		EU-28: Copper sheet (A1-A3) ts		0.119 g

### 8.3.3 Bottom module

Annex

Table 8-7: Inventory list bottom module

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
8-8902-00-0012	PCBA Ass'y_8902_black_South module sub-assy	Module	1,08E+00	1		FP3 Bottom Module	Plan	42.8 g
401-89010-0003	Front Cabinet_8901_BLACK_PLASTIC+METAL_N/A_South Module Front Cover ASSY_CREATOR_N/A		0,00E+00	1		see processes below		
	Front Cabinet: Plastic part	Plastic, PC	8,29E-01			covered with 402-89010-0002		
	Front cabinet: metal shielding	Metal, Steel	3,84E-01			DE: Stainless Steel slab (X6CrNi17) ts <t-agg>		0.384 g
8-8902-00-0003	Daughter Board_8902_NATURAL_South board	Electronics, PCBA	1,05E+00	1		PCBA Bottom Module FP3	further inputs	
8PCB-8901-0003	PCB_8901_NON_South board	Electronics, PCB	#NV	1	4.3cm2	covered with 321-0000-00786		
301-G000-01047	Chip resistor_0.00 Ohm_+50 mohm_1/20 W_0201_2.0mm_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	2	0201	GLO: Resistor thick film flat chip 0201 (0.15mg) ts	process	
302-0214-41043	Chip Capacitor_15.0 pF_± 5%_NPO (COG)_25 V_0201_0.3 mm_MURATA_GRM0335C1E150J_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	GLO: Capacitor ceramic MLCC 0201 (0.17mg) D 0.6x0.3x0.3 ts	process	
302-0214-41063	Chip Capacitor_100 pF_± 5%_NPO (COG)_25 V_0201_0.3 mm_2.0mm_MURATA_GRM0335C1E101J_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-01445	Chip Capacitor_8.00 pF_± 0.10 pF_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H8R0B_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-01579	Chip Capacitor_3.60 pF_± 0.10 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_MURATA_GRM0335C1H3R6B_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-01604	Chip Capacitor_39.0 pF_± 2.0%_NPO (COG)_50 V_0201_0.3 mm_2.0mm_MURATA_GRM0335C1H390G_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
302-1000-01605	Chip Capacitor_13.0 pF_± 2.0%_NPO (COG)_50 V_0201_0.3 mm_2.0mm_MURATA_GRM0335C1H130G_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-01606	Chip Capacitor_8.20 pF_± 0.25 pF_NPO (COG)_50 V_0201_0.3 mm_2.0mm_MURATA_GRM0335C1H8R2C_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-1000-01608	Chip Capacitor_100 nF_± 10%_X5R_35 V_0201_0.3 mm_2.0mm_MURATA_GRM033R6YA104K_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-G000-00023	Chip Capacitor_1.00 nF_± 10%_X7R_25 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	2	0201	covered with 302-0214-41043		
302-G000-00182	Chip Capacitor_100 nF_± 10%_X5R_10 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	1	0201	covered with 302-0214-41043		
302-G000-01475	Chip Capacitor_220 pF_± 10%_X7R_25 V_0201_0.3 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	3,30E-04	2	0201	covered with 302-0214-41043		
302-G000-02041	Chip Capacitor_1.00 uF_± 10%_X5R_35 V_0603_0.8 mm_4.0mm_N/A	Electronics, Capacitor, MLCC	6,30E-03	1	0603	covered with 302-0214-41043		
303-0321-86076	Chip Inductor_100 nH_± 5%_0402_100 Mhz_0.55 mm_MURATA_LQG15HNR10J02D_N/A	Electronics, Inductor, Multilayer Ceramic Chip Inductor (RF Inductor)	1,07E-03	2	0402	GLO: inductor production, low value multilayer chip ecoinvent 3.5	process	1,07E-02
303-0323-84054	Chip Wire Wound Inductor_19.0 nH_± 2%_0402_100 Mhz_MURATA_LQW15AN Series	Electronics, Inductor, Ceramic Chip Inductor (RF Inductor) - Wire-Wound Ferrite Core Type	7,60E-04	1	0402	covered with 303-0321-86076		
303-1000-01294	Chip Wire Wound Inductor_160 nH_± 5%_0603_10 Mhz_0.8 mm_4.0mm_MURATA_LQW18CNR16J00D_N/A	Electronics, Inductor, Ceramic Chip Inductor (RF Inductor) - Wire-Wound Non-Magnetic Core Type	3,80E-03	2	0603	covered with 303-0321-86076		
303-1000-00091	Chip Ferrite bead_220 ohm_± 25%_0603_100 Mhz_0.6 mm_4.0mm_TDK_MPZ1608S221AT_DCR<0.05 Ohm,Idc<2A	Electronics, Inductor, Ferrite Bead	4,63E-03	2	0603	covered with 303-0321-86076		
303-1000-00928	Chip Inductor_0.60 nH_± 0.1 nH_0201_500 Mhz_0.3 mm_MURATA_LQP03TG0N6B02D_DCR<0.08,Idc:850 mA	Electronics, Inductor, Ceramic Chip Inductor (RF Inductor) - Film Type	1,75E-04	1	0201	covered with 303-0321-86076		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
308-0000-00201	ESD protection_5.0V_IECS0505C040FR_0402 ICT_C=0.4pF	Electronics, transient voltage suppressor diode	7,80E-04	2		covered with 308-0000-00321		
308-0000-00321	CHIP BIPOLARTVS_5.0V_ESD5311N-2/TR_DFN_2.0mm_WILLSEMI_Cj<0.4pF	Electronics, transient voltage suppressor diode, 1-Line, Bi-directional, Ultra-low Capacitance	1,49E-03	2		GLO: Diode signal SOD123/323/523 (1.59mg) 0.8x0.75x1.6 with Au-Bondwire ts	process	9
308-0000-00323	CHIP BIPOLARTVS_12V_ESD9N12BA-2/TR_DFN_2.0mm_WILLSEMI_Cj<20pF	Electronics, transient voltage suppressor diode	1,64E-03	2		covered with 308-0000-00321		
308-0000-00328	CHIP BIPOLARTVS_5.0V_ESD5451R-2/TR_0402_2.0mm_WILLSEMI_Packing:DFP1006-2L	Electronics, transient voltage suppressor diode, 1-Line, Bi-directional, Transient Voltage Suppressors	0,00E+00	2		covered with 308-0000-00321		
308-0000-00298	CHIP TVS_26V_PTVS26VZ1USK_SOD-964_2.0mm_NXP_N/A	Electronics, transient voltage suppressor diode	9,23E-04	1		covered with 308-0000-00321		
311-0000-02413	I.C ANALOG SWITCH_BGSA14RN10_TSNP_10 Pins_NoMemory_4.0mm_INFINEON_N/A	Electronics, IC	1,89E-03	1	8,47E-03	IC Front-End - FP2 IC Back-End - FP2	process	
312-0000-00094	MEMS MIC_MSM261D4030Z1CM_64 'dB_ - 26dB_± 1.0dB_4*3*1mm_DIGT_BOTTOM_8.0mm_MEMSENSI NG_N/A	Electronics, metal can LGA package	3,77E-04	1	4mm x 3mm x 1mm	GLO: IC WLP CSP 49 (10.2mg) 3.17x3.17x0.55mm CMOS logic (22 nm node) ts	process	1 piece
314-0000-01119	CON. SPRING CONNECTOR_J9Y802K02308_NA_1 pin_4.0mm_KUNZHON_H=2.0mm	Electronics, Connector	4,00E-03	1		Spring connectors FP3 (314-0000-01119)	plan	4*0.004 g
		Plating, Gold	2,00E-05			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	4*2e-5 g
		Plating, nickel bis(sulfamidate); nickel sulfamate	8,00E-05			GLO: Nickel mix ts	process	4*8e-5
		Spring, Red phosphorous	4,00E-05			neglected		
		Spring, Copper	3,47E-03			GLO: Copper mix (99,999% from electrolysis) ts	process	4*3.47e-3

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		Spring, Tin	3,90E-04			<a href="#">GLO: Tin ts</a>	process	4*3.9e-4
314-0000-01025	CON. SPRING CONNECTOR_J9Y802K00203_NA_1 pin_4.0mm_KUNZHON_C5210,H=1.25mm	Electronics, Connector	4,00E-03	2		covered with 314-0000-01119		
		Spring, Tin	3,90E-04			covered with 314-0000-01119		
		Spring, Copper	3,47E-03			covered with 314-0000-01119		
		Spring, Red phosphorous	4,00E-05			covered with 314-0000-01119		
		Plating, Gold	2,00E-05			covered with 314-0000-01119		
		Plating, nickel bis(sulfamidate); nickel sulfamate	8,00E-05			covered with 314-0000-01119		
314-0000-01111	CON. SPRING CONNECTOR_J9Y802K06308_NA_1 pin_4.0mm_KUNZHON_H=2.0mm	Electronics, Connector	4,00E-03	1		covered with 314-0000-01119		
		Plating, Gold	2,00E-05			covered with 314-0000-01119		
		Plating, nickel bis(sulfamidate); nickel sulfamate	8,00E-05			covered with 314-0000-01119		
		Spring, Tin	3,90E-04			covered with 314-0000-01119		
		Spring, Red phosphorous	4,00E-05			covered with 314-0000-01119		
		Spring, Copper	3,47E-03			covered with 314-0000-01119		
314-0000-01196	TYPE C CONNECTOR_UC16SM115_0.400 mm_16 pin_12.0mm_ASSEM_N/A	Electronics, Connector	3,53E-01	1		USB-C connector	further inputs	0.353 g
		Shell, Sulfur	5,70E-05			<a href="#">DE: Stainless Steel slab (X6CrNi17) ts &lt;t-agg&gt;</a>	process	2e-1 g
		Shell, chromium	3,42E-02			covered with stainless steel above		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		Shell, manganese	3,80E-03			covered with stainless steel above		
		Shell, Iron	1,35E-01			covered with stainless steel above		
		Shell, Red phosphorous	8,55E-05			covered with stainless steel above		
		Shell, Silicon	1,90E-03			covered with stainless steel above		
		Shell, Carbon	1,52E-04			covered with stainless steel above		
		Shell, Nickel (metallic)	1,52E-02			covered with stainless steel above		
		Mid-Plate, Sulfur	3,00E-06			covered with stainless steel above		
		Mid-Plate, Nickel (metallic)	8,00E-04			covered with stainless steel above		
		Mid-Plate, Silicon	1,00E-04			covered with stainless steel above		
		Mid-Plate, Red phosphorous	4,50E-06			covered with stainless steel above		
		Mid-Plate, Iron	7,08E-03			covered with stainless steel above		
		Mid-Plate, manganese	2,00E-04			covered with stainless steel above		
		Mid-Plate, Carbon	8,00E-06			covered with stainless steel above		
		Mid-Plate, chromium	1,80E-03			covered with stainless steel above		
		Contact, Copper	2,27E-02			GLO: Copper mix (99,999% from electrolysis) ts	process	2.27e-2 g
		Contact, Tin	6,84E-05			GLO: Tin ts	process	6.84e-5 g



Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		Contact, Nickel (metallic)	1,14E-05			GLO: Nickel mix ts	process	1.14e-5 g
		Contact, Zinc	2,28E-05			GLO: Special high grade zinc ELCD/IZA	process	2.28e-5 g
		Contact, Red phosphorous	1,14E-05			neglected		
		Shell Plating, Aurate(1-), bis(cyano-.kappa.C)-, potassium (1:1)	1,00E-03			neglected		
		Housing, 1,10-decanediamine polymer with 1,4-Benzenedicarboxylic acid	3,38E-02			covered with glass wool		
		Housing, Glass wool fibers (inhalable and biopersistent)	4,13E-02			EU-28: Glass wool ts	process	1.3e-1 g
		Housing, Additives - Proprietary Data	3,75E-03			covered with glass wool		
		Housing, Poly[imino(1,6-dioxo-1,6-hexanediy)imino-1,6-hexanediy]	1,88E-02			covered with glass wool		
		Housing, Frame retardant - Proprietary Data	2,75E-02			covered with glass wool		
		Contact Plating, Aurate(1-), bis(cyano-.kappa.C)-, potassium (1:1)	4,60E-03			neglected		
314-0000-01200	CON. PCB FEMALE CONNECTOR_DF40GB(1.5)-48DS-0.4V(51)_0.400 mm_48 pin_8.0mm_HIROSE_N/A	Electronics, Connector	8,36E-02	1		Board-to-board connector FP3	Plan	8.36e-2 g
		HOUSING, Talc containing asbestiform fibers	1,20E-02			EU-28: Talcum powder (filler) ts	process	1,20E-02
		HOUSING, Carbon black (airborne, unbound particles of respirable size)	6,00E-04			DE: Carbon black (furnace black; general purpose) ts	process	6e-4 g
		HOUSING, Fatty acids, montan-wax, ethylene esters	2,00E-05			neglected		
		HOUSING, Wholly aromatic liquid crystal polyester(LCP)	2,34E-02			DE: Polyester Resin unsaturated (UP) ts	process	2,34E-02
		HOUSING, Calcium Stearate	4,00E-05			neglected		
		HOUSING, Misc., not to declare	2,00E-05			neglected		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		HOUSING, Glass wool fibers (inhalable and biopersistent)	4,00E-03			EU-28: Glass wool ts	process	4e-3 g
		SHIELD BOARD, Gold	2,99E-06			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	5.07e-5 g
		SHIELD BOARD, Cobalt metal powder	1,50E-05			GLO: Cobalt, refined (metal) CDI	process	1.52e-5 g
		SHIELD BOARD, Iron	1,99E-05			DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	4,13E-05
		SHIELD BOARD, Copper	1,82E-02			GLO: Copper mix (99,999% from electrolysis) ts	process	3,78E-02
		SHIELD BOARD, Nickel (metallic)	1,12E-03			GLO: Nickel mix ts	process	2.22e-3 g
		SHIELD BOARD, Zinc	3,98E-05			GLO: Special high grade zinc ELCD/IZA	process	8.26e-5 g
		SHIELD BOARD, Lead	3,98E-06			EU-28: Lead primary and secondary mix ILA <t-agg>	process	8.26e-5 g
		SHIELD BOARD, Tin	1,59E-03			GLO: Tin ts	process	3.3e-3 g
		SHIELD BOARD, Red phosphorous	3,78E-05			neglected		
		SHIELD BOARD, Cadmium	1,99E-07			GLO: Cadmium ts	process	4.13e-7 g
		SV(B)CONTACT, Cobalt metal powder	2,40E-07			covered with cobalt above		
		SV(B)CONTACT, Zinc	4,28E-05			covered with zinc above		
		SV(B)CONTACT, Tin	1,71E-03			covered with tin above		
		SV(B)CONTACT, Cadmium	2,14E-07			covered with cadmium above		
		SV(B)CONTACT, Gold	4,78E-05			covered with gold above		
		SV(B)CONTACT, Iron	2,14E-05			covered with iron above		
		SV(B)CONTACT, Copper	1,96E-02			covered with copper above		
		SV(B)CONTACT, Lead	4,28E-06			covered with lead above		
		SV(B)CONTACT, Red phosphorous	4,07E-05			neglected		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		SV(B)CONTACT, Nickel (metallic)	1,10E-03			covered with nickel above		
321-0000-00786	PCB_8901_FR4-HF_24.2*25.4mm_0.500 mm_6 Layer_Selective Gold+O.S.P_GOLD CIRCUIT_8901SUBS-007,South,4in1,1-4-1	Electronics, PCB, FR4 HF 6 layers	1,75E+01	1	6 cm2	GLO: Printed Wiring Board 8-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts	process	1.01e-3 m3
326-0000-00320	Filter Dual Mode_ICMF062P900MFR_100MHz_2.0mm_MODAL-INNOCHIPS_Common Mode,4pin,90 Ohm,100mA,0.87x0.67x0.47mm	Electronics, Filter, Ceramic multilayer type SMD component	1,38E-03	1		GLO: electronic component production, passive, unspecified ecoinvent 3.5	process	0,001376 264
303-1000-01297	Chip Inductor_6.80 nH ± 3%_0201_500 Mhz_0.4 mm_2.0mm_MURATA_LQP03HQ6N8H02D_N/A	Electronics, Inductor, Ceramic Chip Inductor Film Type (Standard Type)	2,20E-04	1	0201	covered with 303-0321-86076		
600-0000-00038	Consumable_Solder Paste_SAC305 M8_AIMSOLDER_SAC305 M8	Solder, SAC305	2,00E-01			GLO: Solder paste SnAg3Cu0.5 (SAC-Lot) ts	process	0.2 g
402-89010-0002	Rear Cabinet_8901_BLACK_PC_N/A_South Module Rear Cover ASSY_CREATOR_N/A	Plastic, PC	8,88E-01	1	1,72E+00	EU-28: Polycarbonate PlasticsEurope	process	1.72 g
409-00000-0275	Machine Screw_Flat_TORX_2.5mm_3.0_BLACK_Steel_Plating_H.N.M_N/A	Mechanical, Screw, Steel	4,20E-02	2		Asia: Steel Hot Rolled Coil worldsteel	plan/process	4.2e-2 g per screw
320-0000-00113	Vibrator Coin Type With Spring Contact_BVM1030H-TH02-U_φ10.0*3.00mm_Tray_BAOLONG_N/A	Vibration motor	1,14E+00	1		Vibration Motor FP3	plan	1.14 g
		UPPER MAGNET, dysprosium	5,60E-03			neglected	process	
		UPPER MAGNET, Copper	1,92E-03			GLO: Copper mix (99,999% from electrolysis) ts	process	1.11e-1 g
		UPPER MAGNET, boron	1,96E-03			GLO: boric oxide production ecoinvent	process	3,56E-03
		UPPER MAGNET, Neodymium	5,79E-02			GLO: neodymium oxide to generic market for mischmetal ecoinvent	process	1.06e-1 g
		UPPER MAGNET, Nickel (metallic)	2,48E-03			GLO: Nickel mix ts	process	2,53E-02
		UPPER MAGNET, Iron	1,28E-01			GLO: Steel hot rolled coil (ILCD) worldsteel/ELCD	process	5.45e-1 g

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		UPPER MAGNET, Aluminium powder	1,80E-04			EU-28: Aluminium ingot mix ts	process	3.8e-4 g
		UPPER MAGNET, Gallium	1,60E-04			GLO: gallium, in Bayer liquor from aluminium production ecoinvent 3.5	process	2.6e-4 g
		UPPER MAGNET, Cobalt metal powder	1,80E-03			GLO: Cobalt, refined (metal) CDI	process	3.3e-3 g
		SHAFT, Copper	2,00E-04			covered by copper above		
		SHAFT, Iron	2,70E-03			covered by iron above		
		SHAFT, manganese	6,00E-04			ZA: Manganese ts	process	1.2e-3 g
		SHAFT, Nickel (metallic)	9,00E-04			covered by nickel above		
		SHAFT, molybdenum	3,00E-04			RER: molybdenum production ecoinvent 3.5	process	3e-4 g
		SHAFT, chromium	1,30E-03			ZA: Ferro chrome ts	process	1,30E-03
		PLASTIC HOLDER, Glass wool fibers (inhalable and biopersistent)	5,00E-04			EU-28: Glass wool ts	process	7.5e-3 g
		PLASTIC HOLDER, POLYBUTYRENE TEREPHTHALATE (PBT)	1,50E-03			DE: Polybutylene Terephthalate Granulate (PBT) ts	process	2,25E-02
		CASE UPPER, Nickel (metallic)	5,81E-03			covered by nickel above		
		CASE UPPER, manganese	1,88E-04			covered by manganese above		
		CASE UPPER, Silicon	3,13E-05			neglected		
		CASE UPPER, Sulfur	1,57E-05			neglected		
		CASE UPPER, Carbon	1,57E-05			neglected		
		CASE UPPER, Iron	1,56E-01			covered by iron above		
		CASE UPPER, Copper	2,49E-03			covered by copper above		
		CASE UPPER, Red phosphorous	1,57E-05			neglected		
		SPRING, Sulfur	1,00E-06			neglected		
		SPRING, Red phosphorous	1,00E-06			neglected		
		SPRING, Glycine, N-(carboxymethyl)-	2,00E-06			neglected		
		SPRING, Silicon	4,00E-06			neglected		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		SPRING, Copper	4,00E-06			covered by copper above		
		SPRING, Carbon	1,60E-05			neglected		
		SPRING, confidential	9,00E-06			neglected		
		SPRING, Iron	1,87E-03			covered by iron above		
		SPRING, manganese	9,00E-06			covered by manganese above		
		SPRING, Phosphonic acid, P,P',P''-[nitrilotris(methylene)]tris-	8,70E-05			neglected		
		BRUSH, Copper	6,97E-04			covered by copper above		
		BRUSH, manganese	3,00E-06			covered by manganese above		
		BRUSH, Nickel (metallic)	2,00E-04			covered by nickel above		
		BRUSH, Tin	1,00E-04			GLÖ: Tin ts	process	1,53E-03
		H-PCB, Talc containing asbestiform fibers	4,00E-05			RER: Epoxy resin PlasticsEurope	process	4.4e-3 g
		H-PCB, 2,2-bis(acryloyloxymethyl)butyl acrylate trimethylolpropane triacrylate	6,00E-05			covered above		
		H-PCB, confidential	4,00E-03			covered above		
		H-PCB, Solvent naphtha (petroleum), heavy arom.; Kerosine - unspecified	1,60E-05			covered above		
		H-PCB, Copper	3,60E-03			covered with copper above		
		H-PCB, 2-methyl-1-(4-methylthiophenyl)-2-morpholinopropan-1-one	1,20E-04			covered above		
		H-PCB, Pigment Green 7	1,60E-04			covered above		
		H-PCB, Phenol, polymer with formaldehyde, glycidyl ether, acrylate	4,00E-06			covered above		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		BEARING, confidential	1,50E-03			neglected		
		BEARING, Carbon	2,85E-04			neglected		
		BEARING, Tin	1,43E-03			covered by tin above		
		BEARING, Copper	1,54E-02			covered by copper above		
		BEARING, Iron	1,14E-02			covered by iron above		
		Ink, butanone ethyl methyl ketone	1,00E-03			neglected		
		PBT, Glass wool fibers (inhalable and biopersistent)	7,00E-03			covered by glass wool above		
		POLYBUTYRENE TEREPHTHALATE (PBT)	2,10E-02			covered by PBT above		
		UV GLUE, Alkyl ester	1,00E-04			EU-28: UV-curing laminating adhesives (estimation) ts	process	1,10E-02
		UV GLUE, acrylic acid prop-2-enoic acid	1,00E-04			covered above		
		UV GLUE, 2-Propenoic acid, 2-methyl-, (1R,2R,4R)-1,7,7-trimethylbicyclo[2.2.1]hept-2-yl ester, rel-	2,00E-04			covered above		
		UV GLUE, Photoinitiator	1,00E-04			covered above		
		UV GLUE, 2-hydroxyethyl methacrylate	5,00E-04			covered above		
		Slide, ACRYLIC ADHESIVE	4,00E-03			covered above		
		Slide, Ethene, homopolymer	6,00E-03			covered above		
		COIL, Copper	8,27E-02			covered by copper above		
		COIL, Polyurethane	2,13E-03			EU-28: Crystallising Polyurethane adhesive (estimation) ts	process	2,13E-03
		COIL, 9,12-Octadecadienoic acid (9Z,12Z)-, dimer, reaction products with triethylenetetramine	2,13E-03			neglected		
		CASE LOWER, Sulfur	6,20E-05			neglected		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		CASE LOWER, Copper	2,20E-03			covered by copper above		
		CASE LOWER, Red phosphorous	5,60E-05			neglected		
		CASE LOWER, manganese	4,00E-04			covered by manganese above		
		CASE LOWER, Carbon	2,00E-04			neglected		
		CASE LOWER, Iron	1,38E-01			covered by iron above		
		CASE LOWER, Silicon	2,80E-05			DE: Silicone rubber (RTV-2, condensation) ts	process	2.8e-5 g
		CASE LOWER, Nickel (metallic)	5,20E-03			covered by nickel above		
		Lower Magnet, Iron	1,07E-01			covered by iron above		
		Lower Magnet, Nickel (metallic)	2,10E-03			covered by nickel above		
		Lower Magnet, Neodymium	4,83E-02			covered by neodymium above		
		Lower Magnet, boron	1,60E-03			covered by boron above		
		Lower Magnet, Aluminium powder	2,00E-04			covered by aluminium above		
		Lower Magnet, dysprosium	4,70E-03			neglected		
		Lower Magnet, Gallium	1,00E-04			covered by gallium above		
		Lower Magnet, Copper	1,60E-03			covered by copper above		
		Lower Magnet, Cobalt metal powder	1,50E-03			covered by cobalt above		
		F-PCB, 2-Propenenitrile, polymer with 1,3-butadiene, 3-carboxy-1-cyano-1-methylpropyl-terminated	5,00E-05		0,6	GLO: Printed Wiring Board 1-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts	process	6e-5 m2
		F-PCB, Nickel (metallic)	4,70E-05			covered above		
		F-PCB, confidential	1,18E-04			covered above		
		F-PCB, 1H,3H-Benzo[1,2-c:4,5-c']difuran-1,3,5,7-tetrone, polymer with 4,4'-oxybis[benzenamine]	6,60E-05			covered above		
		F-PCB, 3-aminophenol	1,00E-05			covered above		
		F-PCB, Gold potassium cyanide (KAu(CN) <sub>2</sub> )	3,00E-06			covered above		

Item No	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		F-PCB, 4-phenyl-5-tetradecylthiazol-2-amine	1,00E-05			covered above		
		F-PCB, Copper	6,56E-04			covered above		
		F-PCB, Epichlorohydrin-bisphenol A resin	4,00E-05			covered above		
		WEIGHT, Nickel (metallic)	8,63E-03			covered by nickel above		
		WEIGHT, Tungsten	2,79E-01			Tungsten (ProBas) <e-ep>	process	2.79e-1 g
478-890200-006	STICKER LABEL _Packing Label_8902_Global_PET_10*4mm Black_E-LIN(KUNSHAN)	Label, PET(?)	#NV	1		neglected		
415-89010-0048	GASKET_8901_BLACK_PORON_N/A_vibrator sponge_HUALONG_N/A	PORON Foam	1,10E-02	1		DE: Silicone rubber (RTV-2, condensation) ts	process	1.1e-2 g
415-89010-0047	HOLDER_8901_BLACK_RUBBER, SILICON RUBBER_N/A_mic rubber_JUSHUO_N/A	Silicon rubber	#NV	1		neglected		
415-89010-0044	SHEET_8901_NoColor_ADHESIVE_N/A_vibrator adhesive_HUALONG_N/A	Adhesive	#NV	1		neglected		
415-89010-0028	FILTER_8901_BLACK_FELT MESH_N/A_8901 mic mesh_HUALONG_N/A	Felt (Mesh)	#NV	1		neglected		



### 8.3.4 Speaker module

Table 8-8: Inventory list speaker module

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi )
313-0000-00353	SPEAKER MODULE_QT2723-F-1_26.65 * 26.6 mm_7.5 Ohm_91.5dB_CHANG ZHOU YU CHENG_N/A		3,03E+00	1		FP3 Speaker Module	plan	
		FPC-Nickel Gold Plating, Gold	1,88E-03			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	1.88e-3 g
		FPC-Nickel Gold Plating, Nickel (metallic)	7,52E-03			GLO: Nickel mix ts	process	7.52e-3 g
		Sound film-PMI, 2-Propenamide, N,N'-methylenebis[2-methyl-	1,60E-03			neglected		
		Sound film-Peek, Polyetheretherketone	6,80E-03			neglected		
		Sound absorbent cotton, Sulfurous acid, sodium salt (1:1), polymer with formaldehyde and 1,3,5-triazine-2,4,6-triamine	3,00E-04			neglected		
		Voice coil, Silver	1,92E-03			GLO: Silver mix ts	process	1.92e-3 g
		Voice coil, [Name confidential or not available]	2,41E-03			neglected		
		Voice coil, Copper	4,38E-02			GLO: Copper mix (99,999% from electrolysis) ts	process	5.28e-2 g
		Magnetic Bowl, Sulfur	3,82E-04			EU-28: Stainless steel sheet (EN15804 A1-A3) ts <t-agg>	process	1.56g
		Magnetic Bowl, manganese	6,11E-03			covered by stainless steel above		
		Magnetic Bowl, Red phosphorous	3,82E-04			covered by stainless steel above		
		Magnetic Bowl, Iron	7,55E-01			covered by stainless steel above		
		Magnetic Bowl, Carbon	1,14E-03			covered by stainless steel above		
		damping-White, Terylene	3,00E-04			neglected		

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi )
		Iron sheet, chromium	6,34E-02			covered by stainless steel above		
		Iron sheet, manganese	5,35E-04			covered by stainless steel above		
		Iron sheet, Carbon	1,62E-04			covered by stainless steel above		
		Iron sheet, Sulfur	9,73E-05			covered by stainless steel above		
		Iron sheet, Red phosphorous	1,23E-04			covered by stainless steel above		
		Iron sheet, Nickel (metallic)	3,02E-02			covered by stainless steel above		
		Iron sheet, Iron	2,27E-01			covered by stainless steel above		
		Iron sheet, Silicon	2,76E-03			covered by stainless steel above		
		Front /Back cover, Carbonic acid, diphenyl ester, polymer with 4,4'-(1-methylethylidene)bis[phenol]	9,66E-01			neglected		
		FPC-copper foil, Copper	9,03E-03			covered with copper above		
		FPC-copper foil, 1H,3H-Benzo[1,2-c:4,5-c']difuran-1,3,5,7-tetrone, polymer with 4,4'-oxybis[benzenamine]	4,37E-03			neglected		
		Gasket, Aliphatic Hydrocarbon Resin	1,40E-04			DE: Silicone rubber (RTV-2, condensation) ts	process	1.61e-2 g
		Gasket, Polyethylene Terephthalate (PET)	1,24E-02			covered above		
		Gasket, Cellulose	2,46E-03			covered above		
		Gasket, 2-Propenoic acid, 2-methyl-, methyl ester, polymer with butyl 2-propenoate	1,08E-03			covered above		
		Frame, Polyphthalamide	2,87E-02			neglected		

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi )
		Frame, 1,3,5-Triazine-2,4,6(1H,3H,5H)-trione, 1,3,5-tris[[4-(1,1-dimethylethyl)-3-hydroxy-2,6-dimethylphenyl]methyl]-	1,26E-03			neglected		
		Frame, 1-Dodecanesulfonyl chloride	1,01E-03			neglected		
		Frame, Glass wool fibers (inhalable and biopersistent)	1,66E-02			EU-28: Glass wool ts	process	1.66e-2 g
		Frame, Impact Modifier	2,77E-03			neglected		
		Plate, Sulfur	2,34E-04			covered by stainless steel above		
		Plate, Iron	4,64E-01			covered with stainless steel above		
		Plate, Red phosphorous	2,34E-04			covered with stainless steel above		
		Plate, manganese	3,75E-03			covered with stainless steel above		
		Plate, Carbon	7,03E-04			covered with stainless steel above		
		Magnetic steel, Neodymium	5,24E-02			GLO: neodymium oxide to generic market for mischmetal ecoinvent	process	5.24e-2 g
		Magnetic steel, Praseodymium	4,93E-02			CN: Praseodymium ts	process	4.93e-2 g
		Magnetic steel, dysprosium	3,40E-03			neglected		
		Magnetic steel, boron	3,74E-03			GLO: boric oxide production ecoinvent	process	3.74e-3 g
		Magnetic steel, Other	8,16E-03			neglected		
		Magnetic steel, Iron	2,23E-01			GLO: Steel hot rolled coil (ILCD) worldsteel/ELCD	process	2.23e-1 g
		FPC-Tin Ingot, Tin	1,90E-03			GLO: Tin ts	process	1.9e-3 g
		Reed, Nickel (metallic)	6,83E-04			covered by stainless steel above		
		Reed, manganese	7,30E-05			covered by stainless steel above		

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi )
		Reed, Silicon	3,65E-05			covered by stainless steel above		
		Reed, Iron	5,11E-03			covered by stainless steel above		
		Reed, Carbon	5,84E-06			covered by stainless steel above		
		Reed, Sulfur	2,19E-06			covered by stainless steel above		
		Reed, Red phosphorous	2,92E-06			covered by stainless steel above		
		Reed, chromium	1,39E-03			covered by stainless steel above		
		Sound film-Aluminum foil, Other	1,08E-02			<a href="#">EU-28: Aluminium foil (2010) European Aluminium &lt;t-agg&gt;</a>	process	1.08e-2 g
		Sound film-Aluminum foil, Cadmium	1,08E-06			covered by aluminium foil above		
		Sound film-Aluminum foil, Arsenic	1,08E-06			covered by aluminium foil above		
		Sound film-Aluminum foil, Lead	1,08E-06			covered by aluminium foil above		
		FPC-Covering film, Type paper	1,12E-03			neglected		
		FPC-Covering film, Oxirane, 2-(chloromethyl)-, homopolymer	1,60E-04			neglected		
		FPC-Covering film, 1H,3H-Benzo[1,2-c:4,5-c']difuran-1,3,5,7-tetrone, polymer with 4,4'-oxybis[benzenamine]	3,20E-04			neglected		
		damping-Black, DPP(Polyester Fibre)	3,00E-04			<a href="#">DE: Polyester Resin unsaturated (UP) ts</a>	process	3e-4 g

### 8.3.5 Display Module

Table 8-9: Inventory list display module

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
8-8902-00-0014	LCM Ass'y_8902_BLACK_DISPLAY MODULE SUB-ASS'Y		57,162	1		FP3 Display Module	plan	
401-89010-0001	Front Cabinet_8901_BLACK_PA+GF_N/A_Display Module housing ASSY_CREATOR_MG+AL+PLASTIC	fiber-reinforced PA	13,65	1		EU-28: Polyamide 6.6 fibres (PA 6.6) ts	process	3,63
336-0000-00281	Touch Panel Capacitor Type_98-03057-6598B-L_36*18 channel_5.65 inch_DJN_CG thickness 0.9mm	LCD panel	42,653	1		LCD Display - FP3	plan	8.19e-3 m2 display area
	cover glass	gorilla glass	28,45	1		GLO: glass production, for liquid crystal display ecoinvent <e-ep>	process	28.45 g
	flexible board	FPCB		1	14.94	GLO: Printed Wiring Board 1-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts	process	1.494e-3 m2
		IC on flex board (display control chip?)				IC modelling as described in section 3.1.9.3		6mm2
	electrical components on flex board	further components on flex board, MLCC, Diode, Resistor				GLO: Capacitor ceramic MLCC 0603 (6mg) D 1.6x0.8x0.8 ts GLO: Diode signal SOD123/323/523 (9.26mg) 2.4x1.6x1 with Au-Bondwire ts GLO: Resistor flat chip 0603 (1.9mg) ts	process	1 each
	connector on flex board	connector		1		Connector 40 pin (314-0000-01031) - Display Module FP3 <LZ>	process	1 piece
415-89010-0013	CASE_8901_SILVER_STAINLESS STEEL_N/A_LCM Board Shielding_CJR_N/A	Mechanical, Shielding, stainless steel	2,80E-01	1		DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	2.8e-1 g
8-8902-00-0005	Daughter Board_8902_NATURAL_LCM board	Electronics, PCBA	8,73E-01	1		PCBA Display Module FP3	plan	8.73e-1 g

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
8PCB-8901-0005	PCB_8901_NON_LCM board	Electronics, PCB		1		covered with 321-0000-00789		
301-G000-00002	Chip resistor_1.00 Kohm_± 5%_1/20 W_0201_2.0mm_N/A	Electronics, Resistor, MLCR thick film	2,07E-04	1	0201	GLO: Resistor thick film flat chip 0201 (0.15mg) ts	process	1 piece
302-0215-41055	Chip Capacitor_47.0 pF_± 5%_NPO (COG)_50 V_0201_0.3 mm_MURATA_GRM0335C1H470J_T=0.3±0.03	Electronics, Capacitor, MLCC	3,30E-04	3	0201	GLO: Capacitor ceramic MLCC 0201 (0.17mg) D 0.6x0.3x0.3 ts	process	5 pieces
302-0225-41055	Chip Capacitor_47.0 pF_± 5%_NPO (COG)_50 V_0402_0.5 mm_MURATA_GRM1555C1H470J_N/A	Electronics, Capacitor, MLCC	1,60E-03	3	0402	GLO: Capacitor ceramic MLCC 0603 (6mg) D 1.6x0.8x0.8 (Base Metals) ts	process	6 pieces
302-1000-01696	Chip Capacitor_68.0 pF_± 5%_NPO (COG)_50 V_0201_0.3 mm_2.0mm_EYANG_C0201C0G680J500NTA_N/A	Electronics, Capacitor, MLCC	2,50E-04	2	0201	covered with 302-0215-41055		
302-G000-02034	Chip Capacitor_1.00 uF_± 10%_X5R_10 V_0402_0.5 mm_2.0mm_N/A	Electronics, Capacitor, MLCC	1,60E-03	3	0402	covered with 302-0225-41055		
314-0000-01031	CON. PCB FEMALE CONNECTOR_BM20B(0.8)-40DS-0.4V(51)_0.400 mm_40 pin_4.0mm_HIROSE_H=0.8mm	Electronics, Connector	2,68E-02	1		Connector 40 pin (314-0000-01031) - Display Module FP3	plan	2.68e-2 g
		SV REINFORCED METAL FITTINGS, Gold	3,98E-06			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	4.38e-5 g
		SV REINFORCED METAL FITTINGS, Iron	2,64E-07			DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	1.04e-5 g
		SV REINFORCED METAL FITTINGS, Cadmium	3,91E-05			GLO: Cadmium ts	process	3.92e-5 g
		SV REINFORCED METAL FITTINGS, Copper	3,48E-04			GLO: Copper mix (99,999% from electrolysis) ts	process	9.64e-3 g
		SV REINFORCED METAL FITTINGS, Cobalt metal powder	2,00E-05			GLO: Cobalt, refined (metal) CDI	process	2.02e-5 g
		SV REINFORCED METAL FITTINGS, Nickel (metallic)	2,80E-05			GLO: Nickel mix ts	process	1.03e-3 g
		SV REINFORCED METAL FITTINGS, Lead	2,64E-07			EU-28: Lead primary and secondary mix IIA <t-agg>	process	2.3e-6 g

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		SV REINFORCED METAL FITTINGS, Zinc	1,79E-04			GLO: Special high grade zinc ELCD/IZA	process	1.99e-4 g
		SV CONTACT(2), Gold	3,98E-05			covered by gold above		
		SV CONTACT(2), Cadmium	1,02E-07			covered by cadmium above		
		SV CONTACT(2), Red phosphorous	1,93E-05			neglected		
		SV CONTACT(2), Copper	9,30E-03			covered by copper above		
		SV CONTACT(2), Zinc	2,03E-05			covered by zinc above		
		SV CONTACT(2), Tin	8,13E-04			GLO: Tin ts	process	8.13e-4 g
		SV CONTACT(2), Cobalt metal powder	2,00E-07			covered by cobalt above		
		SV CONTACT(2), Nickel (metallic)	1,00E-03			covered by nickel above		
		SV CONTACT(2), Lead	2,03E-06			covered by lead above		
		SV CONTACT(2), Iron	1,02E-05			covered by iron above		
		HOUSING, Calcium Stearate	1,50E-05			neglected		
		HOUSING, Wholly aromatic liquid crystal polyester(LCP)	8,77E-03			DE: Polyester Resin unsaturated (UP) ts	process	8.77e-3 g
		HOUSING, Glass wool fibers (inhalable and biopersistent)	1,50E-03			EU-28: Glass wool ts	process	1.5e-3 g
		HOUSING, Carbon black (airborne, unbound particles of respirable size)	2,25E-04			DE: Carbon black (furnace black; general purpose) ts	process	2.25e-4 g
		HOUSING, Fatty acids, montan-wax, ethylene esters	7,50E-06			neglected		
		HOUSING, Talc containing asbestiform fibers	4,50E-03			EU-28: Talcum powder (filler) ts	process	4.5e-3 g
321-0000-00789	PCB_8901_FR4-HF_49.4*12.4mm_0.500 mm_6 Layer_Selective Gold+O.S.P_GOLD CIRCUIT_8901LB-007,LCM,4in1,1-4-1	Electronics, PCB, FR4 HF 6 layers	1,75E+01	1	6.37cm2	GLO: Printed Wiring Board 8-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts	process	1.073e-3 m2

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
326-0000-00320	Filter Dual Mode_ICMF062P900MFR_100MHz_2.0mm_MODAL-INOCHIPS_Common Mode,4pin,90 Ohm,100mA,0.87x0.67x0.47mm	Electronics, Filter, Ceramic multilayer type SMD component	1,38E-03	5		GLO: Filter SAW (25mg) 3x7x1 ts	process	0,276 pieces
415-89010-0001	SPRING_8901_SILVER_STAINLESS STEEL_Plating Sn_Shielding Clip 818004173_ECT_N/A	Mechanical, Spring, Stainless steel	1,41E-02	3		DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	0.0423 g
600-0000-00038	Consumable_Solder Paste_SAC305 M8_AIMSOLDER_SAC305 M8	Solder, SAC305	2,00E-01			GLO: Solder paste SnAg3Cu0.5 (SAC-Lot) ts	process	0.2 g
600-0000-00040	Consumable_Under Fill Glue_HHD 3605BK_HENKEL LOCTITE_BLACK	PU adhesive	0,15			DE: Thermoplastic polyurethane (TPU, TPE-U) adhesive ts	process	0.15 g
478-890200-006	STICKER LABEL_Packing Label_8902_Global_PET_10*4mm Black_E-LIN(KUNSHAN)	Label, PET (?)		1		neglected		
415-89010-0022	SHEET_8901_BLUE_PET_N/A_Front camera protection film_HUALONG_N/A	PET(?)		1		neglected		



### 8.3.6 Camera Module

Table 8-10: Inventory list camera module

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
8-8902-00-0008	PCBA Ass'y_8902_BLACK_Rear Camera Module sub-assy	Module	2,89	1		FP3 Camera Module	plan	
401-89010-0009	Front Cabinet_8901_BLACK_PC_N/A_Main cameras module FC_CREATOR_N/A	Plastic, PC	6,26E-01	1	1,187	EU-28: Polycarbonate PlasticsEurope	process	1.187 g
402-89010-0003	Rear Cabinet_8901_BLACK_PLASTIC+METAL_N/A_Rear Camera Module Rear Cover ASSY_CREATOR_N/A	PC + steel	0,693	1		see below		
	Rear Cabinet plastic part	PC	0,561			covered with 401-89010-0009		
	Rear Cabinet Metal shielding	steel	5,70E-02			DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	5.7e-2 g
335-0000-00289	CAMERA MODULE CMOS_OGP1722_12M_O-FILM_N/A	Sensor? Camera itself	8,12E-01	1		Camera module CMOS (335-0000-00289) - Camera Module FP3	plan	
		VCM-F-SPRING C19900R, Copper	6,66E-02			Connectors - Camera module FP3	plan	
		VCM-F-SPRING C19900R, Titanium	2,22E-03			Connectors - Camera module FP3	plan	
		P4-M-121, Polycarbonate resin	9,40E-03			DE: Polycarbonate Granulate (PC) ts	process	0,07453 g
		镜座组件-支架, Carbon black (airborne, unbound particles of respirable size)	7,00E-04			DE: Carbon black (furnace black; general purpose) ts	process	0,00233 g
		镜座组件-支架, ponlyamide	3,08E-02			DE: Polyamide 6 Granulate (PA 6) Mix ts	process	0,0308 g
		镜座组件-支架, Potassium titanium oxide (K2Ti8O17)	3,50E-03			neglected		
		LCP 6130GM, Carbon black (airborne, unbound particles of respirable size)	4,00E-04			covered in carbon black above		

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		LCP 6130GM, Glass wool fibers (inhalable and biopersistent)	4,50E-03			EU-28: Glass wool ts	process	0,0045 g
		LCP 6130GM, Talc containing asbestiform fibers	4,40E-03			EU-28: Talcum powder (filler) ts	process	0,02907 g
		LCP 6130GM, LCP resin	1,99E-02			DE: Polyester Resin unsaturated (UP) ts	process	0,07593 g
		FPC-化学镍钯金, Palladium	1,92E-03			GLO: Palladium mix ts	process	1,92e-3 g
		FPC-化学镍钯金, Nickel (metallic)	6,72E-03			covered with nickel below		
		FPC-化学镍钯金, Gold	9,60E-04			covered with gold below		
		C5210R, Tin	3,00E-03			GLO: Tin ts	process	0,003019 9 g
		C5210R, Red phosphorous	1,00E-04			neglected		
		C5210R, Copper	3,54E-02			GLO: Copper mix (99,999% from electrolysis) ts	process	0,050908 4 g
		P4-P5 SPACER-S-030, Acrylic Resin	1,30E-04			neglected		
		P4-P5 SPACER-S-030, Polyethylene Terephthalate (PET)	3,20E-04			EU-28: Polyethylene terephthalate fibres (PET) ts	process	6,76e-3 g
		P5-M-148, Polycycloolefin Resin	1,02E-02			neglected		
		Au, Gold	4,10E-03			GLO: Gold (primary) ts	process	5,06e-3 g
		Au, Cobalt metal powder	1,00E-04			GLO: Cobalt, refined (metal) CDI	process	0,0001 g
		IC-HD8820, 2(3H)-Furanone, dihydro-	3,40E-06			neglected		
		IC-HD8820, Non regulated ingredients	2,60E-06			neglected		
		IC-HD8820, 2-methoxy-1-methylethyl acetate	6,00E-07			neglected		
		FPC-2UP, Copper	2,04E-02			covered in copper above		
		FPC-2UP, 1H,3H-Benzo[1,2-c:4,5-c']difuran-1,3,5,7-tetrone, polymer with 4,4'-oxybis[benzenamine]	3,60E-03			neglected		
		BARREL-B-115, Polycarbonate resin	5,41E-02			covered in PC above		

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		P1-M-175, Ethylene-tetracyclododecene Copolymer	1,20E-03			RER: ethylene vinyl acetate copolymer production ecoinvent 3.5	process	0,0304 g
		IC-SC40 MU, copper sulphate	1,30E-06			neglected		
		IC-SC40 MU, Sulphuric acid	1,30E-06			neglected		
		IC-SC40 MU, Water	6,10E-06			neglected		
		FPC-S-411W, Flexible board	3,50E-03		1.8cm2	GLO: Printed Wiring Board 1-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts	process	1.8e-4 m2
		P1-M-148, Polycycloolefin Resin	3,00E-03			neglected		
		Electrode ZG, Copper	6,84E-05			covered in copper above		
		Electrode ZG, Silicon dioxide	6,08E-06			neglected		
		Electrode ZG, Diboron trioxide	1,52E-06			neglected		
		P2-M-156, Polycarbonate resin	5,70E-03			covered in PC above		
		Electrode ZD, Nickel (metallic)	8,00E-06			GLO: Nickel mix ts	process	9,84e-3 g
		镜座组件-油墨, 2-Butoxyethanol	7,00E-06			neglected		
		镜座组件-油墨, Coloring agent	2,00E-05			neglected		
		镜座组件-油墨, 3,5,5-trimethylcyclohex-2-enone isophorone	5,00E-06			neglected		
		镜座组件-油墨, Bisphenol A diglycidyl ether (BADGE)	4,00E-06			neglected		
		IC-target materials, Copper	8,00E-07			IC covered with CMOS logic - FP3		
		IC-target materials, Titanium	1,00E-07			IC covered with CMOS logic - FP3		
		IC-BS25, Silicon dioxide	1,47E-05			IC covered with CMOS logic - FP3		
		IC-BS25, Acrylic Ester	5,20E-06			IC covered with CMOS logic - FP3		

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		IC-BS25, Synthetic resin	1,80E-06			IC covered with CMOS logic - FP3		
		Tin plating, Tin	1,90E-05			covered in tin above		
		Ni, Nickel (metallic)	3,10E-03			covered in nickel above		
		FPC-FH, 1H,3H-Benzo[1,2-c:4,5-c']difuran-1,3,5,7-tetrone, polymer with 4,4'-oxybis[benzenamine]	4,90E-03			neglected		
		FPC-FH, Release paper	1,31E-02			neglected		
		镜座组件-膜材, Quartz (SiO2)	2,00E-05			neglected		
		镜座组件-膜材, trititanium pentoxide	1,00E-05			neglected		
		VCM-Lens Holder Bobbin E525T LSLOCKY1, Liquid crystal polymers/LCP	2,40E-02			covered in polyester resin UP above		
		VCM-Lens Holder Bobbin E525T LSLOCKY1, Copper	1,54E-02			covered in copper above		
		VCM-Lens Holder Bobbin E525T LSLOCKY1, Talc containing asbestiform fibers	9,52E-03			covered in talc above		
		P5-P6 SPACER1-B-154, Polycarbonate resin	3,35E-03			covered in PC above		
		RETAINER-B-101, Polycarbonate resin	1,98E-03			covered in PC above		
		Nickel plating, Nickel (metallic)	7,00E-06			covered in nickel above		
		镜座组件-玻璃, aluminium oxide	5,00E-04			GLO: aluminium oxide production ecoinvent	process	0,0005 g
		镜座组件-玻璃, Magnesium fluoride (MgF2)	1,00E-03			neglected		
		镜座组件-玻璃, Aluminium fluoride	1,00E-03			RER: aluminium fluoride production ecoinvent 3.5	process	0,001 g
		镜座组件-玻璃, Calcium fluoride	1,00E-03			neglected		
		镜座组件-玻璃, Zinc Oxide (Nano)	5,00E-04			RER: zinc oxide production ecoinvent 3.5	process	0,0005 g

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		镜座组件-玻璃, barium fluoride	1,50E-03			neglected		
		镜座组件-玻璃, Copper (II) oxide	1,00E-03			RER: copper oxide production ecoinvent 3.5	process	0,001 g
		镜座组件-玻璃, phosphorus pentoxide	3,60E-03			neglected		
		IC-Nickel sulfamate, Water	4,00E-07			IC covered with CMOS logic - FP3		
		IC-Nickel sulfamate, Nickel (metallic)	1,40E-06			IC covered with CMOS logic - FP3		
		P6-M-097, Ethylene-tetracyclododecene Copolymer	2,19E-02			covered in copolymer above		
		VCMAGNET 48H, Misch metal, cerium	1,73E-02			CN: Cerium ts	process	0,017348 g
		VCMAGNET 48H, Iron	3,93E-02			neglected		
		VCM-YOKE SPB, Iron	1,60E-04			neglected		
		VCM-YOKE SPB, manganese	1,58E-01			RER: manganese production ecoinvent 3.5		0,15843 g
		VCM-YOKE SPB, Carbon	2,00E-05			covered in carbon black above		
		FPC-PP, Flexible board	4,40E-02			covered with 1 layer PCB above		
		Ceramics, Barium oxide (BaO)	1,32E-04			GLO: barium oxide production ecoinvent 3.5	process	0,000132 g
		Ceramics, Titanium dioxide (airborne, unbound particles of respirable size)	6,60E-05			RER: titanium dioxide production, chloride process ecoinvent	process	0,000066 g
		Ceramics, Misc	2,20E-05			neglected		
		P3-M-175, Ethylene-tetracyclododecene Copolymer	5,80E-03			covered in copolymer above		
		P5-P6 SPACER2-S-030, Polyethylene Terephthalate (PET)	2,00E-04			covered in PET above		
		P5-P6 SPACER2-S-030, Acrylic Resin	8,00E-05			neglected		

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		VCM-BOTTOM E525T, Carbon black (airborne, unbound particles of respirable size)	1,20E-03			covered in carbon black above		
		VCM-BOTTOM E525T, Liquid crystal polymers/LCP	3,20E-02			covered in polyester resin UP above		
		VCM-BOTTOM E525T, Talc containing asbestiform fibers	1,49E-02			covered in talc above		
		VCM-B-SPRING C19900R, Copper	6,71E-02			Connectors - Camera module FP3	plan	
		VCM-B-SPRING C19900R, Titanium	2,24E-03			Connectors - Camera module FP3	plan	
		P3-P4 SPACER-S-030, Polyethylene Terephthalate (PET)	1,00E-04			covered in PET above		
		P3-P4 SPACER-S-030, Acrylic Resin	4,00E-05			neglected		
		镜座组件-胶水, Substituted propane derivative	1,50E-03			neglected		
		镜座组件-胶水, 2,2'-[(octahydro-4,7-methano-1H-indenediyl)bis(methyleneoxymethylene)]di oxirane	7,50E-04			neglected		
		镜座组件-胶水, Carbon black (airborne, unbound particles of respirable size)	1,00E-05			covered in carbon black above		
		镜座组件-胶水, Talc containing asbestiform fibers	2,40E-04			covered in talc above		
		镜座组件-胶水, Calcium carbonate	7,50E-04			EU-28: Calcium carbonate > 63 microns IMA-Europe/ELCD	process	0,00075 g
		镜座组件-胶水, Amine adduct	7,50E-04			neglected		
		镜座组件-胶水, Substituted silane	1,00E-05			neglected		

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		镜座组件-胶水, Epoxy resin	7,50E-04			DE: Epoxy Resin (EP) Mix ts	process	0,00075 g
		镜座组件-胶水, Siloxanes and Silicones, di-Me, reaction products with silica	2,40E-04			neglected		
		FPC-SF-PC6000-U1, Silver	1,16E-03			GLO: Silver mix ts	process	1,16e-3 g
		FPC-SF-PC6000-U1, Polyethylene Terephthalate (PET)	6,04E-03			covered with PET above		
		P2-P3 SPACER-S-030, Acrylic Resin	3,00E-05			neglected		
		P2-P3 SPACER-S-030, Polyethylene Terephthalate (PET)	1,00E-04			covered in PET above		
		IC-Silicon, Silicon	9,00E-04			covered with IC above		
		IC-Silicon, Aluminium powder	1,00E-04			covered with IC above		
		Die, Arsenic	1,00E-04		0,35714	CMOS logic - FP3 <LZ>	process	3.5714e-5 m2
		Die, Silicon	9,90E-03			covered with IC above		
		P1-M-097, Ethylene-tetracyclododecene Copolymer	1,50E-03			covered in copolymer above		
		IC-Silver tin plating solution, Organic compound	1,30E-06			covered with IC above		
		IC-Silver tin plating solution, Tin	9,00E-07			covered with IC above		
		IC-Silver tin plating solution, Alkylsulphonic Acid	2,20E-06			covered with IC above		
		IC-Silver tin plating solution, Water	1,72E-05			covered with IC above		
		IC-Silver tin plating solution, Silver	2,00E-07			covered with IC above		
8-8902-00-0004	Daughter Board_8902_NATURAL_Camera board	Electronics, PCBA	3,88E-01	1		PCBA Camera Module FP3	plan	3.88e1 g
8PCB-8901-0004	PCB_8901_NON_Camera board	Electronics, PCB	#NV	1		covered with 321-0000-00788		
301-1000-00402	Chip NTC_100 Kohm_± 1%_1/10 W_0402_2.0mm_MURATA_N/A	Electronics, Resistor, MLCR thick film	1,15E-03	1	0402	GLO: Resistor thick film flat chip 0402 (0.75mg) ts	process	1 piece

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
309-0000-00326	LED Flash type_ELCH09-NB5060J8K2283910-FDX_WHITE_2pin_SMD2_1000 mA/350 lm_4.0mm_EVERLIGHT_N/A	Electronics, Diode, Flash LED (White) [Zener Diode, LED]	7,00E-03	1	2.04x1.64x0.75 (mm)	GLO: LED SMD high-efficiency with lens max 1A (60mg) Au bondwire 3.5x3.5x2.0 ts	process	1 piece
309-0000-00327	LED Flash type_ELCH08-NB2025J6J8283910-FDH(ARI)_WHITE_2pin_SMD2_1000mA/250 lm_4.0mm_EVERLIGHT_N/A	Electronics, Diode, Flash LED (White) [Zener Diode, LED]	7,59E-03	1	2.04x1.64x0.75	GLO: LED SMD high-efficiency with lens max 1A (60mg) Au bondwire 3.5x3.5x2.0 ts	process	1 piece
314-0000-00878	CON. PCB FEMALE CONNECTOR_BM20B(0.8)-30DS-0.4V(51)_0.400 mm_30 pin_8.0mm_HIROSE_8.48*2.3*0.8mm	Electronics, Connector	2,10E-02	1		Connector 30 pin (314-0000-00878) - Camera Module FP3	plan	2.1e-2 g
		Ni Plating of SV CONTACT(2), Nickel (metallic)	4,70E-04			GLO: Nickel mix ts	process	0.00052 g
		SV REINFORCED METAL FITTINGS, Zinc	3,36E-04			GLO: Special high grade zinc ELCD/IZA	process	0.000345 g
		SV REINFORCED METAL FITTINGS, Copper	6,53E-04			GLO: Copper mix (99,999% from electrolysis) ts	process	5.02e-3 g
		SV REINFORCED METAL FITTINGS, Lead	4,94E-07			EU-28: Lead primary and secondary mix ILA <t-agg>	process	#####
		SV REINFORCED METAL FITTINGS, Cadmium	7,33E-08			GLO: Cadmium ts	process	1.21e-7 g
		SV REINFORCED METAL FITTINGS, Iron	4,95E-07			DE: Stainless Steel slab (X6CrNi17) ts <t-agg>	process	0.00000527 g
		SV CONTACT(2), Lead	9,54E-07			covered by lead above		
		SV CONTACT(2), Tin	3,82E-04			GLO: Tin ts	process	0.000382 g
		SV CONTACT(2), Iron	4,77E-06			covered by iron above		
		SV CONTACT(2), Red phosphorous	9,06E-06			neglected		
		SV CONTACT(2), Zinc	9,54E-06			covered by zinc above		
		SV CONTACT(2), Copper	4,36E-03			covered by copper above		
		SV CONTACT(2), Cadmium	4,77E-08			covered by cadmium above		



Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
		Au Plating of SV REINFORCED METAL FITTINGS, Gold	9,95E-06			GLO: Gold mix (primary, copper and recycling route) ts <t-agg>	process	2.99e-5 g
		Au Plating of SV REINFORCED METAL FITTINGS, Cobalt metal powder	5,00E-08			GLO: Cobalt, refined (metal) CDI	process	#####
		Au Plating of SV CONTACT(2), Cobalt metal powder	1,00E-07			covered by cobalt above		
		Au Plating of SV CONTACT(2), Gold	1,99E-05			covered by gold above		
		HOUSING, Wholly aromatic liquid crystal polyester(LCP)	8,57E-03			DE: Polyester Resin unsaturated (UP) ts	process	8.57e-3 g
		HOUSING, Calcium Stearate	1,50E-08			neglected		
		HOUSING, Talc containing asbestiform fibers	4,40E-03			EU-28: Talcum powder (filler) ts	process	4.4e-3 g
		HOUSING, Glass wool fibers (inhalable and biopersistent)	1,47E-03			EU-28: Glass wool ts	process	1.47e-3 g
		HOUSING, Carbon black (airborne, unbound particles of respirable size)	2,20E-04			DE: Carbon black (furnace black; general purpose) ts	process	2.2e-4 g
		Ni Plating of SV REINFORCED METAL FITTINGS, Nickel (metallic)	5,00E-05			covered by nickel above		
314-0000-01200	CON. PCB FEMALE CONNECTOR_DF40GB(1.5)-48DS-0.4V(51)_0.400 mm_48 pin_8.0mm_HIROSE_N/A	Electronics, Connector	8,36E-02	1		FP3 Board-to-board connector (as modelled in the bottom module)	plan	
321-0000-00788	PCB_8901_FR4-HF_16.7*15.3mm_0.500 mm_6 Layer_Selective Gold+O.S.P_GOLD CIRCUIT_8901CB1-007,camera,4in1,1-4-1	Electronics, PCB, FR4 HF 6 layers	1,75E+01	1	2.4 cm2	GLO: Printed Wiring Board 8-layer rigid FR4 with chem-elec AuNi finish (Subtractive method) ts	process	4.04e-4 m2
600-0000-00038	Consumable_Solder Paste_SAC305 M8_AIMSOLDER_SAC305 M8	Solder, SAC305	2,00E-01			GLO: Solder paste SnAg3Cu0.5 (SAC-Lot) ts	process	0.2 g
409-00000-0275	Machine Screw_Flat_TORX_2.5mm_3.0_BLACK_Steel_Plating_H.N.M_N/A	Mechanical, Screw, Steel	4,20E-02	2		Screw 2.5mm (409-00000-0275) - FP3	plan	

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
478-890200-006	STICKER LABEL_Packing Label_8902_Global_PET_10*4mm Black_E-LIN(KUNSHAN)	Label, PET(?)		1		neglected		
415-89010-0023	ADHESIVE_8901_NoColor_ADHESIVE_N/A_8901 flash lens adhesive_HUALONG_N/A	Adhesive		1		neglected		
415-89010-0024	GASKET_8901_BLACK_PORON_N/A_Flash lens sponge_HUALONG_N/A	PORON Foam		1		neglected		
415-89010-0025	GASKET_8901_BLACK_PORON_N/A_Main camera sponge_HUALONG_N/A	PORON Foam		1		neglected		
415-89010-0026	DECORATION_8901_BLACK_ALUMINIUM_ANODIZING_Camera module deco_RUNER_N/A	Aluminium	4,07E-01	1		DE: Aluminium sheet mix ts	process	
403-89010-0002	Lens_8901_BLACK_GLASS_AR Coating_Main camera lens_KAYMAO_N/A	Glass		1				
415-89020-0001	LIGHT GUIDE_8902_TRANSPARENT_PMMA_Painting_8902 flash lens_CRERATE_N/A	PMMA	1,15E-01	1		DE: Polymethylmethacrylate granulate (PMMA) mix ts	process	0.115 g
415-89010-0040	GASKET_8901_BLACK_PORON_N/A_main camera conn spong_HUALONG_N/A	PORON Foam		1		neglected		
415-89010-0021	SHEET_8901_YELLOW_KAPTON_N/A_PCB Kapton_HUALONG_N/A	PCB (Kapton Film)		2		neglected		
415-89010-0020	SHEET_8901_YELLOW_KAPTON_N/A_North Kapton_HUALONG_N/A	Kapton Film		1		neglected		
330-0000-00476	ANTENNA EMBEDDED_8901_NFC Band ( 13.56 MHz)_BLACK_NF-C-F9-R0-006_INPAQ(SUZHOU)_N/A			1		neglected		

### 8.3.7 Packaging

Table 8-11: Inventory list packaging

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
	Packaging					FP3 Packaging	Plan	
			24,85			Bulk packaging	further input	24.85 g
481-89010-0007	Carton_8901_N/A_AB FLUTE_MASTER CARTON_RUN HAO(SUZHOU)_N/A_340*267*190(Inner)		474,00	0,034		see processes below		
		red ink	5,00			neglected		
		paper	454,00			EU-25: Graphic Paper Euro-graph/ELCD	process	15.8 g
		black ink	5,00			neglected		
		glue	10,00			neglected		
481-60110-0002	Carton_6011_N/A_B FLUTE_PAPER SPACER_RUN HAO(SUZHOU)_N/A_336x263mm	paper	5,00E+00	6,80E-02		covered with paper from 481-89010-0007		
481-89010-0008	Carton_8901_N/A_B FLUTE_HONEYCOMB BOARD_RUN HAO(SUZHOU)_N/A_336*263*175mm(85*30)	Cardboard	2,47E+02	0,034		EU-28: Corrugated board excl. paper production 2015, open paper input, average composition ts/FEFCO <t-agg>	process	8.4 g
			204,39			Sales Packaging	further input	204.39 g
479-00000-0148	Bubble Wrap_3.00mm_PE_CHANGHONG(SUZHOU)_479-00000-0148_1271-2824.2	Plastic, PE	6,80	1		RER: Polyethylene film (PE-LD) PlasticsEurope	process	6.8 g
478-890100-001	HANDSET LABEL_Packing Label_8901_Global_ART PAPER LABEL_N/A_E-LIN(KUNSHAN)			1		neglected		
7L-890100-0001	Label info HANDSET LABEL_8901_Global_LABEL			1		neglected		
478-890100-002	PROTECTIVE FILM LABEL_Packing Label_8901_Global_PET_N/A_E-LIN(KUNSHAN)	Plastic, PET	2,292	1		EU-28: Polyethylene terephthalate fibres (PET) ts	process	2.292 g
	Slide-On Sleeve Packaging	Paper/Cardboard, Cardboard	15,330	1		EU-28: Corrugated board excl. paper production 2015, open paper input, average composition ts/FEFCO <t-agg>	process	174.808 g
	Bottom Part Packaging	Paper/Cardboard, Cardboard	67,315	1		covered with Slide-On Sleeve Packaging		

Item Number	Description	Category, Type, Material	weight [g]	Quantity	size [cm <sup>2</sup> ]	GaBi Process	Level	Scale in GaBi
	Top Part packaging	Paper/Cardboard, Cardboard	62,893	1		covered with Slide-On Sleeve Packaging		
	Packaging inlay	Paper/Cardboard, Cardboard	14,756	1		covered with Slide-On Sleeve Packaging		
	Packaging of manuals	Paper/Cardboard, Cardboard	14,514	1		covered with Slide-On Sleeve Packaging		
	Manuals	Paper/Cardboard, Paper	20,494	2		EU-25: Graphic Paper Euro-graph/ELCD	process	20,494 g